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PSP 103.2

The PSP model is a joint development of Delft University of Technology and NXP Semiconductors

G.D.J. Smit, A.J. Scholten, and D.B.M. Klaassen
(NXP Semiconductors)

R. van der Toorn
(Delft University of Technology)

Unclassified Report

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PSP developers (present and past)

- At NXP Semiconductors
  - Geert D.J. Smit
  - Andries J. Scholten
  - Dirk B.M. Klaassen
- At Delft University of Technology
  - Ramses van der Toorn
- At Philips Research Europe
  - Ronald van Langevelde (until 2006)
- At Arizona State University
  - Gennady Gildenblat (until 2011)
  - Hailing Wang (until 2005)
  - Xin Li (until 2011)
  - Weimin Wu (until 2011)

Authors' address
R. van der Toorn PSP_Support@tudelft.nl
G.D.J. Smit Gert-Jan.Smit@nxp.com
A.J. Scholten Andries.Scholten@nxp.com
D.B.M. Klaassen D.B.M.Klaassen@nxp.com

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Author(s): G.D.J. Smit, A.J. Scholten, and D.B.M. Klaassen (NXP Semiconductors)
R. van der Toorn (Delft University of Technology)

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Abstract: The PSP model is a compact MOSFET model intended for analog, RF, and digital design. It is jointly developed by NXP Semiconductors and Delft University of Technology. (Until 2011, it was jointly developed by NXP Semiconductors and Arizona State University. The roots of PSP lie in both *MOS Model 11* (developed by NXP Semiconductors) and *SP* (developed at the Pennsylvania State University and later at Arizona State University). PSP is a surface-potential based MOS Model, containing all relevant physical effects (mobility reduction, velocity saturation, DIBL, gate current, lateral doping gradient effects, STI stress, etc.) to model present-day and upcoming deep-submicron bulk CMOS technologies. The source/drain junction model, c.q. the JUNCAP2 model, is fully integrated in PSP. This report contains a full description of the PSP model, including parameter sets, scaling rules, model equations, and a description of the parameter extraction procedure.
In December 2005, the Compact Model Council (CMC) has elected PSP as the new industrial standard model for compact MOSFET modeling.
Since December 2012, Delft University of Technology replaces Arizona State University as the supporting institution.

Conclusions:

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History of model and documentation

History of the model

April 2005 Release of PSP 100.0 (which includes JUNCAP2 200.0) as part of SiMKit 2.1. A Verilog-A implementation of the PSP-model is made available as well. The PSP-NQS model is released as Verilog-A code only.

August 2005 Release of PSP 100.1 (which includes JUNCAP2 200.1) as part of SiMKit 2.2. Similar to the previous version, a Verilog-A implementation of the PSP-model is made available as well and the PSP-NQS model is released as Verilog-A code only. Focus of this release was mainly on the optimization of the evaluation speed of PSP. Moreover, the PSP implementation has been extended with operating point output (SiMKit-version only).

March 2006 Release of PSP 101.0 (which includes JUNCAP2 200.1) as part of SiMKit 2.3. PSP 101.0 is *not* backward compatible with PSP 100.1. Similar to the previous version, a Verilog-A implementation of the PSP-model is made available as well and the PSP-NQS model is released as Verilog-A code only. Focus of this release was on the implementation of requirements for CMC standardization, especially those which could not preserve backward compatibility.

June 2006 Release of PSP 102.0 (which includes JUNCAP2 200.1) as part of SiMKit 2.3.2. PSP 102.0 is backward compatible with PSP 101.0 in all practical cases, provided a simple transformation to the parameter set is applied (see description below). Similar to the previous version, a Verilog-A implementation of the PSP-model is made available as well and the PSP-NQS model is released as Verilog-A code only.

Global parameter sets for PSP 101.0 can be transformed to PSP 102.0 by replacing **DPHIBL** (in 102.0 parameter set) by **DPHIBO** · **DPHIBL** (from 101.0 parameter set). After this transformation, the simulation results of PSP 102.0 are identical to those of PSP 101.0 in all practical situations.

October 2006 Release of PSP 102.1 (which includes JUNCAP2 200.2) as part of SiMKit 2.4. PSP 102.1 is backward compatible with PSP 102.0. SiMKit 2.4 includes a preliminary implementation of the PSP-NQS model. Similar to the previous version, a Verilog-A implementation of the PSP-model is available as well.

October 2007 Release of PSP 102.2 (which includes JUNCAP2 200.3). PSP 102.2 is backward compatible with PSP 102.1. This release provides an express version of JUNCAP2.

April 2008 Release of PSP 102.3 (which includes JUNCAP2 200.3) as part of SiMKit 3.1. PSP 102.3 is backward compatible with PSP 102.2. Focus of this release is on the implementation of asymmetric models for both junction and overlap regions of the drain side.

November 2008 Release of PSP 103.0 (which includes JUNCAP 200.3) as part of SiMKit 3.2. PSP 103.0 is *not* fully backward compatible with PSP 102.3. The main changes are:

- Global, local and binning models are unified. When **SWGEO** $= 1$ (default) global model is used. When **SWGEO** $= 0$ local model is selected. The binning model is invoked if **SWGEO** is set to 2.
- Added non-uniform doping (NUD) model. The model can be invoked on by setting **SWNUD** $= 1$ or 2. When **SWNUD** $= 1$, a separate surface potential calculation is carried out and the NUD model does not affect the CV results. This avoids non-reciprocal capacitances. When **SWNUD** $= 2$, the extra surface potential calculation is skipped and this may result in non-reciprocal capacitances.
  Added related model parameters **GFACNUDO**, **GFACNUDL**, **GFACNUDLEXP**, **GFACNUDW**, **GFACNUDLW**, **VSBNUDO** and **DVSBNUDO** to global, **GFACNUD**, **VSBNUD** and **DVSBNUD** to local and **POGFACNUD**,

PLGFACNUD, **PWGFACNUD**, **PLWGFACNUD**, **POVSBNUD** and **PODVSBNUD** to binning models.

- Added $V_{\rm th}$-adjustment model for CV. It can be turned on by setting **SWDELVTAC** $= 1$. Note that this requires extra computation of surface potentials. Added related model parameters **FACNEFFACO**, **FACNEFFACL**, **FACNEFFACW**, **FACNEFFACLW**, **DELVTACO**, **DELVTACL**, **DELVTACLEXP**, **DELVTACW** and **DELVTACLW** to global, **FACNEFFAC** and **DELVTAC** to local and **POFACNEFFAC**, **PLFACNEFFAC**, **PWFACNEFFAC**, **PLWFACNEFFAC**, **PODELVTAC**, **PLDELVTAC**, **PWDELVTAC** and **PLWDELVTAC** to binning model.

- Added external diffusion resistances to source and drain. Added instance parameters **NRS** and **NRD**; added model parameters **RSH** to global and binning, **RSE** and **RDE** to local model.

- Modified the geometrical scaling rules of following parameters: **VFB**, **STVFB**, **DPHIB**, **STBET** and **STTHESAT**.

- Modified the binning rule of **BETN**.

- Removed the effect of **FETA** from CV.

- Added local parameter values to OP-output.

- Some minor bug-fixes and implementation changes.

May 2009 Release of PSP 103.1 (which includes JUNCAP 200.3) as part of SiMKit 3.3. The main changes are:

- Added external sheet resistance **RSHD** for drain diffusion (used when **SWJUNASYM** $= 1$)

- Bug-fix and minor implementation change in NUD-model

- Minor bug fix in conditional for SP-calculation of overlap areas.

- Added noise source labeling (vA-code only)

December 2009 Release of PSP 103.1.1 (which includes JUNCAP 200.3) as part of SiMKit 3.4. The main changes are:

- Modified implementation of the asymmetrical junction model to improve simulation speed of verilog-A code.

- Modified implementation of the stand-alone JUNCAP2 model.

- Modified implementation of the MULT-scaling factor.

- Modified implementation of NUD model.

- Minor bug fixes.

July 2010 Release of PSP 103.1.2β as part of SiMKit 3.5. The main changes are:

- Changes in the calculation of the surface-potential in the overlap regions and the calculation of the gate-current. These modifications lead to an 7% simulation speed increase, but leads to some small changes in the overlap-capacitance, gate-current, and GIDL-current w.r.t. the previous version.

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December 2012 Release of PSP 103.2.0 (which includes JUNCAP 200.4) as part of SiMKit 4.0.1. The main changes are:

- Changes in the calculation of the surface potential in the overlap regions (see July 2010).
- Introduction of self heating. The self heating version of the model has a fifth terminal (dt) to represent the temperature increase. New parameters: **RTH**, **CTH**, **STRTH** (local model), **RTHO**, **CTHO**, **STRTHO** (global model and binning model).
- The expression for qlim2 in QM correction was modified to avoid unphysical behavior when oxide thickness is large. This modification makes the model more suitable for high-k dielectrics.
- Some minor bug-fixes in the calculation of the OP-output.
- Several improvements in the noise-model implementation
  - Fixed sign of correlation coefficient (Verilog-A only).
  - Simplified implementation and better scaled noise amplitude at internal nodes (Verilog-A only).
  - Improved behavior when crossing $V_{\rm ds} = 0$ at high-frequency.
- Scaled junction parameters added to OP-output.
- New parameter **PARAMCHK** to set level of clip warnings (SiMKit only).
- More efficient model evaluation when **MULT** $= 0$ (SiMKit only).

History of the documentation

April 2005 First release of PSP (PSP 100.0) documentation.

August 2005 Documentation updated for PSP 100.1, errors corrected and new items added.

March 2006 Documentation adapted to PSP 101.0. Added more details on noise-model implementation and a full description of the NQS-model.

June 2006 Documentation adapted to PSP 102.0 and some errors corrected.

October 2006 Documentation adapted to PSP 102.1 and some errors corrected.

October 2007 Documentation adapted to PSP 102.2 and some errors corrected.

April 2008 Documentation adapted to PSP 102.3 and some errors corrected.

November 2008 Documentation adapted to PSP 103.0 and some errors corrected.

June 2009 Documentation adapted to PSP 103.1 and some errors corrected.

December 2012 Documentation adapted to PSP 103.2.

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Section 1

Introduction

1.1 Origin and purpose

The PSP model is a compact MOSFET model intended for analog, RF, and digital design. It is jointly developed by NXP Semiconductors and Delft University of Technology. (Until 2011, it was jointly developed by NXP Semiconductors and Arizona State University. The roots of PSP lie in both *MOS Model 11* (developed by NXP Semiconductors) and *SP* (developed at the Pennsylvania State University and later at Arizona State University). PSP is a surface-potential based MOS Model, containing all relevant physical effects (mobility reduction, velocity saturation, DIBL, gate current, lateral doping gradient effects, STI stress, etc.) to model present-day and upcoming deep-submicron bulk CMOS technologies. The source/drain junction model, c.q. the JUNCAP2 model, is fully integrated in PSP.

PSP not only gives an accurate description of currents, charges, and their first order derivatives (i.e. transconductance, conductance and capacitances), but also of the higher order derivatives, resulting in an accurate description of electrical distortion behavior. The latter is especially important for analog and RF circuit design. The model furthermore gives an accurate description of the noise behavior of MOSFETs. Finally, PSP has an option for simulation of non-quasi-static (NQS) effects.

The source code of PSP and the most recent version of this documentation are available on the PSP model web site: `psp.ewi.tudelft.nl` and the NXP Semiconductors web site: `www.nxp.com/models`.

1.2 Structure of PSP

The PSP model has a hierarchical structure, similar to that of MOS Model 11 and SP. This means that there is a strict separation of the geometry scaling in the global model and the model equations in the local model.

As a consequence, PSP can be used at either one of two levels.

- **Global level** One uses a global parameter set, which describes a whole geometry range. Combined with instance parameters (such as L and W), a local parameter set is internally generated and further processed at the local level in exactly the same way as a custom-made local parameter set.

- **Local level** One uses a custom-made local parameter set to simulate a transistor with a specific geometry. Temperature scaling is included at this level.

The set of parameters which occur in the equations for the various electrical quantities is called the *local* parameter set. In PSP, temperature scaling parameters are included in the local parameter set. An overview of the local parameters in PSP is given in Section 2.5.2. Each of these parameters can be determined by purely electrical measurements. As a consequence, a local parameter set gives a complete description of the electrical properties of a device of *one* particular geometry.

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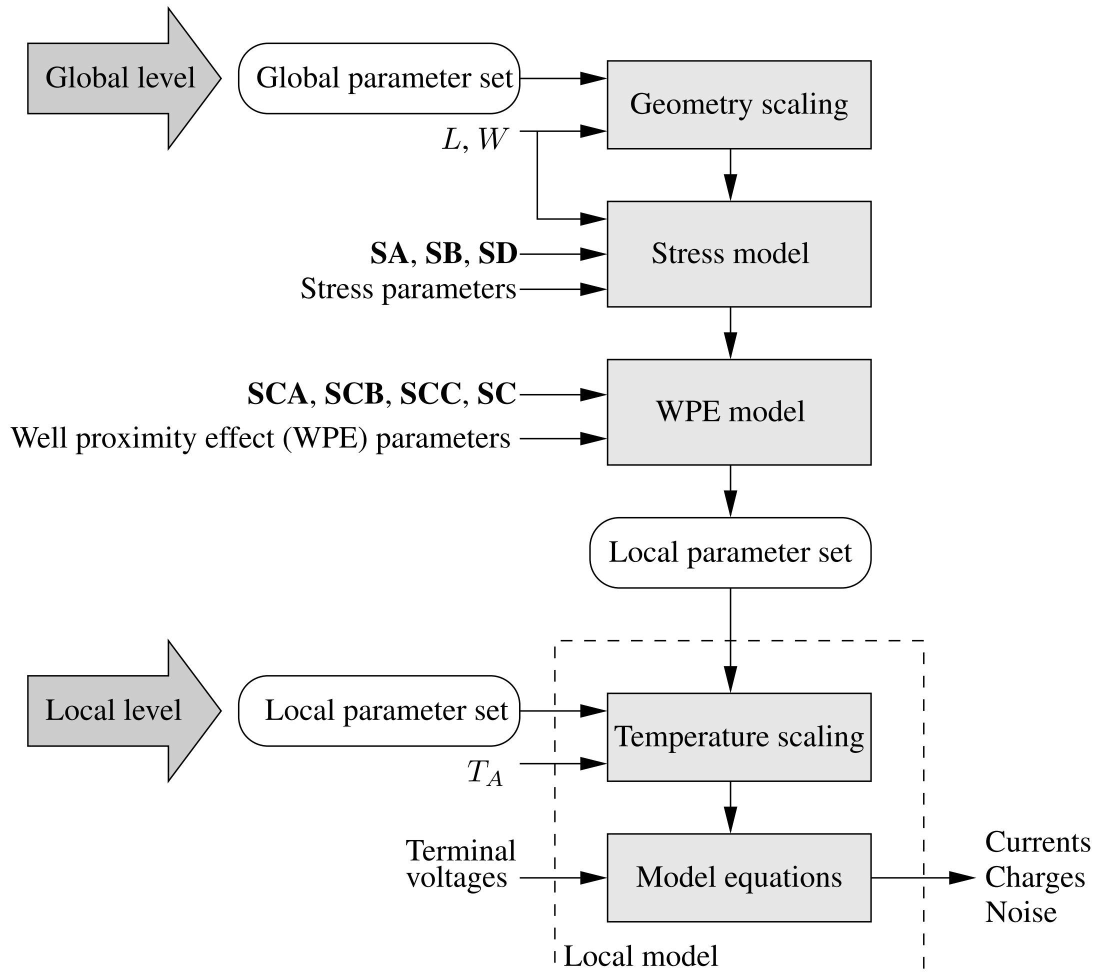

Figure 1.1: Simplified schematic overview of PSP's hierarchical structure.

Since most of these (local) parameters scale with geometry, all transistors of a particular process can be described by a (larger) set of parameters, called the *global* parameter set. An overview of the global parameters in PSP is given in Section 2.5.2. Roughly speaking, this set contains all local parameters for a long/wide device plus a number of sensitivity coefficients. From the global parameter set, one can obtain a local parameter set for a specific device by applying a set of scaling rules (see Section 3.2). The geometric properties of that specific device (such as its length and width) enter these scaling rules as *instance parameters*.

From PSP 101.0 onwards it is possible to use a set of binning rules (see Section 3.3) as an alternative to the geometrical (physics based) scaling rules. These binning rules come with their own set of parameters (see Section 2.5.2). Similar to the geometrical scaling rules, the binning rules yield a local parameter set which is used as input for the local model.

PSP is preferably used at global level when designing a circuit in a specific technology for which a global parameter set is available. On the other hand, using PSP at local level can be advantageous during parameter extraction.

As an option, it is possible to deal with the modifications of transistor properties due to stress and well proximity effect (WPE). In PSP, this is implemented by additional sets of transformation rules, which are optionally applied to the intermediate local parameter set generated at the global level. The parameters associated with the stress and WPE models are consequently part of the global parameter set (both geometrical and binning).

The model structure described above is schematically depicted in Fig. 1.1.

The JUNCAP2 model is implemented in such a way that the same set of JUNCAP2 parameters can be used at

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both the global and the local level. This is further explained in Section 6.4.

1.3 Availability

The PSP model developers (Delft University of Technology and NXP Semiconductors) distribute the PSP code in two formats:

1. Verilog-A code
2. C-code (as part of SiMKit-library)

The C-version is automatically generated from the Verilog-A version by the software package ADMS [1]. This procedure guarantees the two implementations to contain identical equations. Nevertheless—due to some specific limitations/capabilities of the two formats—there are a few minor differences, which are described in Section 6.5.

1.3.1 SiMKit

SiMKit is a simulator-independent compact transistor model library. Simulator-specific connections are handled through so-called adapters that provide the correct interfacing to the circuit simulator of choice. Currently, adapters to the following circuit simulators are provided:

1. Spectre (Cadence)
2. Pstar (NXP Semiconductors)
3. ADS (Agilent)

Some other circuit simulators vendors provide their own SiMKit adapter, such that simulations with models in SiMKit are possible.

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Section 2

Constants and Parameters

2.1 Nomenclature

The nomenclature of the quantities listed in the following sections has been chosen to express their purpose and their relation to other quantities and to preclude ambiguity and inconsistency. Throughout this document, all PSP parameter names are printed in boldface capitals. Parameters which refer to the long transistor limit and/or the reference temperature have a name containing an '**O**', while the names of scaling parameters end with the letter '**L**' and/or '**W**' for length or width scaling, respectively. Parameters for temperature scaling start with '**ST**', followed by the name of the parameter to which the temperature scaling applies. Parameters used for the binning model start with '**PO**', '**PL**', '**PW**', or '**PLW**', followed by the name of the local parameter they refer to.

2.2 Parameter clipping

For most parameters, a maximum and/or minimum value is given in the tables below. In PSP, all parameters are limited (clipped) to this pre-specified range in order to prevent difficulties in the numerical evaluation of the model, such as division by zero.

N.B. After computation of the scaling rules (either physical or binning), stress and well proximity effect equations, the resulting local parameters are subjected to the clipping values as given in Section 2.5.2.

2.3 Circuit simulator variables

External electrical variables

The definitions of the external electrical variables are illustrated in Fig. 2.1. The relationship between these external variables and the internal variables used in Chapter 4 is given in Fig. 6.1.

Symbol	Unit	Description
V_{D}^{e}	V	Potential applied to drain node
V_{G}^{e}	V	Potential applied to gate node
V_{S}^{e}	V	Potential applied to source node
V_{B}^{e}	V	Potential applied to bulk node
I_{D}^{e}	A	DC current into drain node

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. . . continued from previous page

Symbol	Unit	Description
I_{G}^{e}	A	DC current into gate node
I_{S}^{e}	A	DC current into source node
I_{B}^{e}	A	DC current into bulk node
S_{fl}^{e}	$\mathrm{A^2s}$	Spectral density of flicker noise current in the channel
S_{id}^{e}	$\mathrm{A^2s}$	Spectral density of thermal noise current in the channel
$S_{\mathrm{ig,S}}^{e}$	$\mathrm{A^2s}$	Spectral density of induced gate noise at source side
$S_{\mathrm{ig,D}}^{e}$	$\mathrm{A^2s}$	Spectral density of induced gate noise at drain side
S_{igs}^{e}	$\mathrm{A^2s}$	Spectral density of gate current shot noise at source side
S_{igd}^{e}	$\mathrm{A^2s}$	Spectral density of gate current shot noise at drain side
$S_{\mathrm{j,S}}^{e}$	$\mathrm{A^2s}$	Spectral density of source junction shot noise
$S_{\mathrm{j,D}}^{e}$	$\mathrm{A^2s}$	Spectral density of drain junction shot noise
S_{igid}^{e}	$\mathrm{A^2s}$	Cross spectral density between S_{id}^{e} and (S_{igS}^{e} or S_{igD}^{e})

Other circuit simulator variables

Next to the electrical variables described above, the quantities in the table below are also provided to the model by the circuit simulator.

Symbol	Unit	Description
T_{A}	°C	Ambient circuit temperature
f_{op}	Hz	Operation frequency

2.4 Model constants

In the following table the symbolic representation, the value and the description of the various physical constants used in the PSP model are given.

No.	Symbol	Unit	Value	Description
1	T_0	K	273.15	Offset between Celsius and Kelvin temperature scale
2	k_{B}	J/K	$1.3806505 \cdot 10^{-23}$	Boltzmann constant
3	$\hbar$	J s	$1.05457168 \cdot 10^{-34}$	Reduced Planck constant
4	q	C	$1.6021918 \cdot 10^{-19}$	Elementary unit charge
5	m_0	kg	$9.1093826 \cdot 10^{-31}$	Electron rest mass
6	ϵ_0	F/m	$8.8541878176 \cdot 10^{-12}$	Permittivity of free space
7	$\epsilon_{\mathrm{r,Si}}$	–	11.8	Relative permittivity of silicon
8	QM_{N}	$\mathrm{V\,m^{\frac{4}{3}}C^{-\frac{2}{3}}}$	5.951993	Constant of quantum-mechanical behavior of electrons
9	QM_{P}	$\mathrm{V\,m^{\frac{4}{3}}C^{-\frac{2}{3}}}$	7.448711	Constant of quantum-mechanical behavior of holes

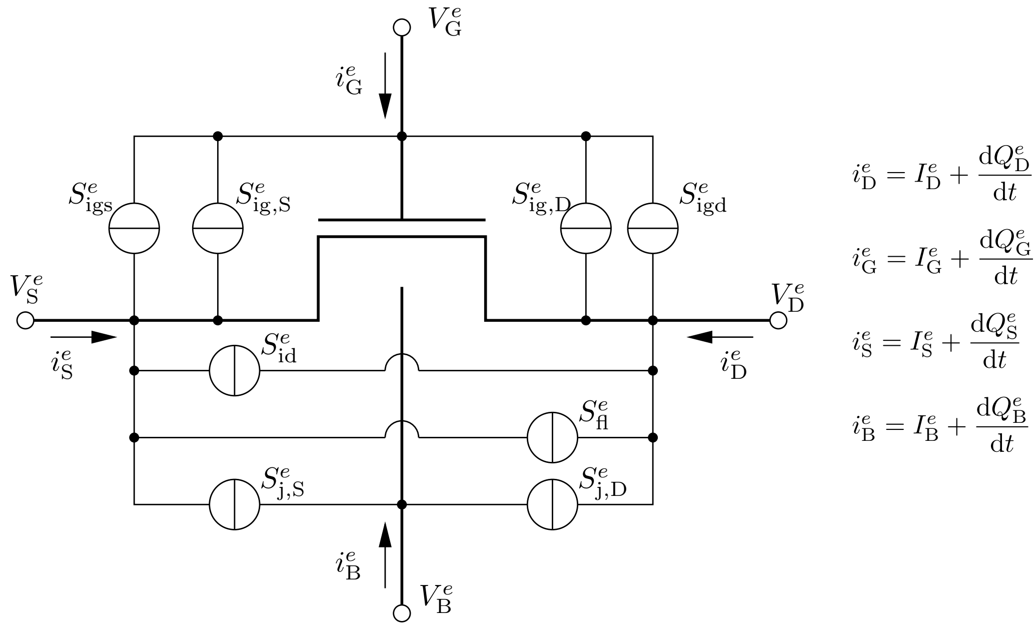

Figure 2.1: Definition of external electrical quantities.

2.5 Model parameters

In this section all parameters of the PSP-model are described. The parameters for the intrinsic MOS model, the stress and well proximity effect models and the junction model are given in separate tables. The complete parameter list for each of the model entry levels is composed of several parts, as indicated in the table below.

Entry level	**Sections**
Global (geometrical scaling)	2.5.1 (instance parameters)
	2.5.2 (intrinsic MOS)
	2.5.3 (stress)
	2.5.4 (well proximity effect)
	2.5.5 (junctions)
	2.5.6 (parasitic resistances)
Binning	2.5.1 (instance parameters)
	2.5.2 (intrinsic MOS)
	2.5.3 (stress)
	2.5.4 (well proximity effect)
	2.5.5 (junctions)
	2.5.6 (parasitic resistances)
Local	2.5.1 (instance parameters)
	2.5.2 (intrinsic MOS)
	2.5.5 (junctions)
	2.5.6 (parasitic resistances)

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2.5.1 Instance parameters

The instant parameters for global, local and binning models are listed in the table below. The last column of **Geo.** shows for which value of **SWGEO** the listed parameter is used. Note that, as explained in Section 6.4, the instance parameters for the JUNCAP2 model are used at the local level as well.

No.	Name	Unit	Default	Min.	Max.	Description	Geo.
0	L	m	10^{-6}	10^{-9}	–	Drawn channel length	1, 2
1	W	m	10^{-6}	10^{-9}	–	Drawn channel width (total width)	1, 2
2	**ABSOURCE**	m^2	10^{-12}	0	–	Source junction area	0, 1, 2
3	**LSSOURCE**	m	10^{-6}	0	–	STI-edge part of source junction perimeter	0, 1, 2
4	**LGSOURCE**	m	10^{-6}	0	–	Gate-edge part of source junction perimeter	0, 1, 2
5	**ABDRAIN**	m^2	10^{-12}	0	–	Drain junction area	0, 1, 2
6	**LSDRAIN**	m	10^{-6}	0	–	STI-edge part of drain junction perimeter	0, 1, 2
7	**LGDRAIN**	m	10^{-6}	0	–	Gate-edge part of drain junction perimeter	0, 1, 2
8	**AS**	m^2	10^{-12}	0	–	Source junction area (alternative spec.)	0, 1, 2
9	**PS**	m	10^{-6}	0	–	Source STI-edge perimeter (alternative spec.)	0, 1, 2
10	**AD**	m^2	10^{-12}	0	–	Drain junction area (alternative spec.)	0, 1, 2
11	**PD**	m	10^{-6}	0	–	Drain STI-edge perimeter (alternative spec.)	0, 1, 2
12	**JW**	m	$1 \cdot 10^{-6}$	0	–	Junction width	0
13	**DELVTO**	V	0	–	–	Threshold voltage shift parameter	0, 1, 2
14	**FACTUO**	–	1	0	–	Zero-field mobility pre-factor	0, 1, 2
15	**SA**	m	0	–	–	Distance between OD-edge and poly at source side	1, 2
16	**SB**	m	0	–	–	Distance between OD-edge and poly at drain side	1, 2
17	**SD**	m	0	–	–	Distance between neighboring fingers	1, 2
18	**SCA**	–	0	0	–	Integral of the first distribution function for scattered well dopant	1, 2
19	**SCB**	–	0	0	–	Integral of the second distribution function for scattered well dopant	1, 2
20	**SCC**	–	0	0	–	Integral of the third distribution function for scattered well dopant	1, 2
21	**SC**	m	0	–	–	Distance between OD edge and nearest well edge	1, 2
22	**NRS**	–	0	–	–	Number of squares of source diffusion	1, 2
23	**NRD**	–	0	–	–	Number of squares of drain diffusion	1, 2
24	**NGCON**	–	1	1	2	Number of gate contacts	1, 2

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No.	Name	Unit	Default	Min.	Max.	Description	Geo.
25	**XGW**	m	10^{-7}	–	–	Distance from the gate contact to the channel edge	1, 2
26	**NF**	–	1	1	–	Number of fingers; internally rounded to the nearest integer	1, 2
27	**MULT**	–	1	0	–	Number of devices in parallel	0, 1, 2

Note that if both **SA** and **SB** are set to 0 the stress-equations are not computed. If **SCA**, **SCB**, **SCC** and **SC** are all set to 0 the well proximity effect equations are not computed.

The switching parameter **SWJUNCAP** is used to determine the meaning and usage of the junction instance parameters, where **AB** (junction area), **LS** (STI-edge part of junction perimeter), and **LG** (gate-edge part of junction perimeter) are the instance parameters of a single instance (source or drain) of the JUNCAP2 model.

	source			drain		
SWJUNCAP	**AB**	**LS**	**LG**	**AB**	**LS**	**LG**
0	0	0	0	0	0	0
1	**ABSOURCE**	**LSSOURCE**	**LGSOURCE**	**ABDRAIN**	**LSDRAIN**	**LGDRAIN**
2	**AS**	**PS**	W_E	**AD**	**PD**	W_E
3	**AS**	**PS** $- W_\mathrm{E}$	W_E	**AD**	**PD** $- W_\mathrm{E}$	W_E

At the local level, the switching parameter **SWJUNCAP** is used to determine the meaning and usage of the junction instance parameters, where **AB** (junction area), **LS** (STI-edge part of junction perimeter), and **LG** (gate-edge part of junction perimeter) are the instance parameters of a single instance (source or drain) of the JUNCAP2 model. Because the transistor width W is not available at the local level, an additional instance parameter **JW** (junction width) is required when **SWJUNCAP** $= 2$ or 3.

	source			drain		
SWJUNCAP	**AB**	**LS**	**LG**	**AB**	**LS**	**LG**
0	0	0	0	0	0	0
1	**ABSOURCE**	**LSSOURCE**	**LGSOURCE**	**ABDRAIN**	**LSDRAIN**	**LGDRAIN**
2	**AS**	**PS**	**JW**	**AD**	**PD**	**JW**
3	**AS**	**PS** – **JW**	**JW**	**AD**	**PD** – **JW**	**JW**

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2.5.2 Intrinsic model

The model parameters for the intrinsic part of the MOSFET are listed in the table below. The last column—labeled '**Geo.**'—shows for which value of **SWGEO** the parameter is used. The convention used in this table is that, if a scaling rule exists for a local parameter its scaling (global and/or binning) parameters are grouped underneath. Note also some parameters do not have their local counterparts.

No.	Name	Unit	Default	Min.	Max.	Description	Geo.
0	**LEVEL**	–	103	–	–	Model selection parameter; see Sec. 6.1	0, 1, 2
1	**TYPE**	–	1	−1	1	Channel type parameter; 1 ↔ NMOS, −1 ↔ PMOS[1]	0, 1, 2
2	**TR**	°C	21	−273	–	Reference temperature	0, 1, 2
3	**DTA**	K	0	–	–	Temperature offset w.r.t. ambient circuit temperature	0, 1, 2
				Switches			
4	**PARAMCHK**	–	0	–	–	Level of clip-warning info[2]	0, 1, 2
5	**SWGEO**	–	1	0	2	Flag for geometrical model (0 ↔ local, 1 ↔ global, 2 ↔ binning)	0, 1, 2
6	**SWIGATE**	–	0	0	1	Flag for gate current (0 ↔ "off")	0, 1, 2
7	**SWIMPACT**	–	0	0	1	Flag for impact ionization current (0 ↔ "off")	0, 1, 2
8	**SWGIDL**	–	0	0	1	Flag for GIDL/GISL current (0 ↔ "off")	0, 1, 2
9	**SWJUNCAP**	–	0	0	3	Flag for JUNCAP (0 ↔ "off")	0, 1, 2
10	**SWJUNASYM**	–	0	–	–	Flag for asymmetric junctions (0 ↔ "off")	0, 1, 2
11	**SWNUD**	–	0	0	2	Flag for NUD-effect (0 ↔ "off")	0, 1, 2
12	**SWDELVTAC**	–	0	0	1	Flag for separate charge calculation (0 ↔ "off")	0, 1, 2
13	**QMC**	–	1	0	–	Quantum-mechanical correction factor	0, 1, 2
				Labels for binning set			
14	**LMIN**	m	0	–	–	Dummy parameter to label binning set	2
15	**LMAX**	m	1	–	–	Dummy parameter to label binning set	2
16	**WMIN**	m	0	–	–	Dummy parameter to label binning set	2
17	**WMAX**	m	1	–	–	Dummy parameter to label binning set	2
				Process Parameters			
18	**LVARO**	m	0	–	–	Geometry independent difference between actual and programmed poly-silicon gate length	1, 2

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[1]See Section 6.3.1 for more information on usage of **TYPE** in various simulators.
[2]Only in SiMKit-version of PSP. See Section 6.5.4 for more information.

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No.	Name	Unit	Default	Min.	Max.	Description	Geo.
19	**LVARL**	–	0	–	–	Length dependence of ΔL_{PS}	1, 2
20	**LVARW**	–	0	–	–	Width dependence of ΔL_{PS}	1, 2
21	**LAP**	m	0	–	–	Effective channel length reduction per side due to lateral diffusion of source/drain dopant ions	1, 2
22	**WVARO**	m	0	–	–	Geometry independent difference between actual and programmed field-oxide opening	1, 2
23	**WVARL**	–	0	–	–	Length dependence of ΔW_{OD}	1, 2
24	**WVARW**	–	0	–	–	Width dependence of ΔW_{OD}	1, 2
25	**WOT**	m	0	–	–	Effective reduction of channel width per side due to lateral diffusion of channel-stop dopant ions	1, 2
26	**DLQ**	m	0	–	–	Effective channel length offset for CV	1, 2
27	**DWQ**	m	0	–	–	Effective channel width offset for CV	1, 2
28	**VFB**	V	-1	–	–	Flat-band voltage at **TR**	0
29	**VFBO**	V	-1	–	–	Geometry-independent part	1
30	**VFBL**	V	0	–	–	Length dependence	1
31	**VFBW**	V	0	–	–	Width dependence	1
32	**VFBLW**	V	0	–	–	Area dependence	1
33	**POVFB**	V	-1	–	–	Geometry independent part	2
34	**PLVFB**	V	0	–	–	Length dependence	2
35	**PWVFB**	V	0	–	–	Width dependence	2
36	**PLWVFB**	V	0	–	–	Length times width dependence	2
37	**STVFB**	V/K	$5 \cdot 10^{-4}$	–	–	Temperature dependence of **VFB**	0
38	**STVFBO**	V/K	$5 \cdot 10^{-4}$	–	–	Geometry-independent part	1
39	**STVFBL**	V/K	0	–	–	Length dependence	1
40	**STVFBW**	V/K	0	–	–	Width dependence	1
41	**STVFBLW**	V/K	0	–	–	Area dependence	1
42	**POSTVFB**	V/K	$5 \cdot 10^{-4}$	–	–	Geometry independent part	2
43	**PLSTVFB**	V/K	0	–	–	Length dependence	2
44	**PWSTVFB**	V/K	0	–	–	Width dependence	2
45	**PLWSTVFB**	V/K	0	–	–	Length times width dependence	2
46	**TOX**	m	$2 \cdot 10^{-9}$	10^{-10}	–	Gate oxide thickness	0
47	**TOXO**	m	$2 \cdot 10^{-9}$	10^{-10}	–	Gate oxide thickness	1
48	**POTOX**	m	$2 \cdot 10^{-9}$	–	–	Geometry independent part	2
49	**EPSROX**	–	3.9	1	–	Relative permittivity of gate dielectric	0

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No.	Name	Unit	Default	Min.	Max.	Description	Geo.
50	**EPSROXO**	–	3.9	1	–	Geometry independent part	1
51	**POEPSROX**	–	3.9	1	–	Geometry independent part	2
52	**NEFF**	m^{-3}	$5 \cdot 10^{23}$	10^{20}	10^{26}	Substrate doping	0
53	**NSUBO**	m^{-3}	$3 \cdot 10^{23}$	10^{20}	–	Geometry independent substrate doping	1
54	**NSUBW**	–	0	–	–	Width dependence of substrate doping due to segregation	1
55	**WSEG**	m	10^{-8}	10^{-10}	–	Characteristic length for segregation of substrate doping	1
56	**NPCK**	m^{-3}	10^{24}	0	–	Pocket doping level	1
57	**NPCKW**	–	0	–	–	Width dependence of **NPCK** due to segregation	1
58	**WSEGP**	m	10^{-8}	10^{-10}	–	Characteristic length for segregation of pocket doping	1
59	**LPCK**	m	10^{-8}	10^{-10}	–	Characteristic length for lateral doping profile	1
60	**LPCKW**	–	0	–	–	Width dependence of **LPCK** due to segregation	1
61	**FOL1**	–	0	–	–	First order length dependence of short channel body-effect	1
62	**FOL2**	–	0	–	–	Second order length dependence of short channel body-effect	1
63	**PONEFF**	m^{-3}	$5 \cdot 10^{23}$	–	–	Geometry independent part	2
64	**PLNEFF**	m^{-3}	0	–	–	Length dependence	2
65	**PWNEFF**	m^{-3}	0	–	–	Width dependence	2
66	**PLWNEFF**	m^{-3}	0	–	–	Length times width dependence	2
67	**FACNEFFAC**	–	1	0	–	Pre-factor for effective substrate doping in separate charge calculation when **SWDELVTAC** $= 1$	0
68	**FACNEFFACO**	–	1	0	–	Geometry independent part	1
69	**FACNEFFACL**	–	0	–	–	Length dependence	1
70	**FACNEFFACW**	–	0	–	–	Width dependence	1
71	**FACNEFFACLW**	–	0	–	–	Area dependence	1
72	**POFACNEFFAC**	–	1	–	–	Geometry independent part	2
73	**PLFACNEFFAC**	–	0	–	–	Length dependence	2
74	**PWFACNEFFAC**	–	0	–	–	Width dependence	2
75	**PLWFACNEFFAC**	–	0	–	–	Area dependence	2
76	**GFACNUD**	–	1	0.01	–	Bodyfactor change due to NUD-effect	0
77	**GFACNUDO**	–	1	–	–	Geometry independent part	1
78	**GFACNUDL**	–	0	–	–	Length dependence	1

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No.	Name	Unit	Default	Min.	Max.	Description	Geo.
79	**GFACNUDLEXP**	–	1	–	–	Exponent for length dependence	1
80	**GFACNUDW**	–	0	–	–	Width dependence	1
81	**GFACNUDLW**	–	0	–	–	Area dependence	1
82	**POGFACNUD**	–	1	–	–	Geometry independent part	2
83	**PLGFACNUD**	–	0	–	–	Length dependence	2
84	**PWGFACNUD**	–	0	–	–	Width dependence	2
85	**PLWGFACNUD**	–	0	–	–	Area dependence	2
86	**VSBNUD**	V	0	0	–	Lower $V_{\rm SB}$-value for NUD-effect	0
87	**VSBNUDO**	V	0	–	–	Geometry independent part	1
88	**POVSBNUD**	V	0	–	–	Geometry independent part	2
89	**DVSBNUD**	V	1	0.1	–	$V_{\rm SB}$-range for NUD-effect	0
90	**DVSBNUDO**	V	1	–	–	Geometry independent part	1
91	**PODVSBNUD**	V	1	–	–	Geometry independent part	2
92	**VNSUB**	V	0	–	–	Effective doping bias-dependence parameter	0
93	**VNSUBO**	V	0	–	–	Geometry independent part	1
94	**POVNSUB**	V	0	–	–	Geometry independent part	2
95	**NSLP**	V	0.05	10^{-3}	–	Effective doping bias-dependence parameter	0
96	**NSLPO**	V	0.05	–	–	Geometry independent part	1
97	**PONSLP**	V	0.05	–	–	Geometry independent part	2
98	**DNSUB**	$\rm V^{-1}$	0	0	1	Effective doping bias-dependence parameter	0
99	**DNSUBO**	$\rm V^{-1}$	0	–	–	Geometry independent part	1
100	**PODNSUB**	$\rm V^{-1}$	0	–	–	Geometry independent part	2
101	**DPHIB**	V	0	–	–	Offset of $\varphi_{\rm B}$	0
102	**DPHIBO**	V	0	–	–	Geometry independent part	1
103	**DPHIBL**	V	0	–	–	Length dependence	1
104	**DPHIBLEXP**	–	1	–	–	Exponent for length dependence	1
105	**DPHIBW**	V	0	–	–	Width dependence	1
106	**DPHIBLW**	V	0	–	–	Area dependence	1
107	**PODPHIB**	V	0	–	–	Geometry independent part	2
108	**PLDPHIB**	V	0	–	–	Length dependence	2
109	**PWDPHIB**	V	0	–	–	Width dependence	2
110	**PLWDPHIB**	V	0	–	–	Length times width dependence	2

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No.	Name	Unit	Default	Min.	Max.	Description	Geo.
111	**DELVTAC**	V	0	–	–	Offset of φ_{B} in separate charge calculation when **SWDELVTAC** $= 1$	0
112	**DELVTACO**	V	0	–	–	Geometry independent part	1
113	**DELVTACL**	V	0	–	–	Length dependence	1
114	**DELVTACLEXP**	–	1	–	–	Exponent for length dependence	1
115	**DELVTACW**	V	0	–	–	Width dependence	1
116	**DELVTACLW**	V	0	–	–	Area dependence	1
117	**PODELVTAC**	V	0	–	–	Geometry independent part	2
118	**PLDELVTAC**	V	0	–	–	Length dependence	2
119	**PWDELVTAC**	V	0	–	–	Width dependence	2
120	**PLWDELVTAC**	V	0	–	–	Length times width dependence	2
121	**NP**	m^{-3}	10^{26}	0	–	Gate poly-silicon doping	0
122	**NPO**	m^{-3}	10^{26}	–	–	Geometry-independent part	1
123	**NPL**	–	0	–	–	Length dependence	1
124	**PONP**	m^{-3}	10^{26}	–	–	Geometry independent part	2
125	**PLNP**	m^{-3}	0	–	–	Length dependence	2
126	**PWNP**	m^{-3}	0	–	–	Width dependence	2
127	**PLWNP**	m^{-3}	0	–	–	Length times width dependence	2
128	**CT**	–	0	0	–	Interface states factor	0
129	**CTO**	–	0	–	–	Geometry-independent part	1
130	**CTL**	–	0	–	–	Length dependence	1
131	**CTLEXP**	–	1	–	–	Exponent for length dependence	1
132	**CTW**	–	0	–	–	Width dependence	1
133	**CTLW**	–	0	–	–	Area dependence	1
134	**POCT**	–	0	–	–	Geometry independent part	2
135	**PLCT**	–	0	–	–	Length dependence	2
136	**PWCT**	–	0	–	–	Width dependence	2
137	**PLWCT**	–	0	–	–	Length times width dependence	2
138	**TOXOV**	m	$2 \cdot 10^{-9}$	10^{-10}	–	Overlap oxide thickness	0
139	**TOXOVO**	m	$2 \cdot 10^{-9}$	10^{-10}	–	Geometry independent part	1
140	**POTOXOV**	m	$2 \cdot 10^{-9}$	–	–	Geometry independent part	2
141	**TOXOVD**	m	$2 \cdot 10^{-9}$	10^{-10}	–	Overlap oxide thickness for drain side	0
142	**TOXOVDO**	m	$2 \cdot 10^{-9}$	10^{-10}	–	Geometry independent part	1
143	**POTOXOVD**	m	$2 \cdot 10^{-9}$	–	–	Geometry independent part	2
144	**LOV**	m	0	0	–	Overlap length for overlap capacitance	1

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No.	Name	Unit	Default	Min.	Max.	Description	Geo.
145	**LOVD**	m	0	0	–	Overlap length for gate/drain overlap capacitance	1
146	**NOV**	m^{-3}	$5 \cdot 10^{25}$	10^{20}	10^{27}	Effective doping of overlap region	0
147	**NOVO**	m^{-3}	$5 \cdot 10^{25}$	–	–	Geometry independent part	1
148	**PONOV**	m^{-3}	$5 \cdot 10^{25}$	–	–	Geometry independent part	2
149	**PLNOV**	m^{-3}	0	–	–	Length dependence	2
150	**PWNOV**	m^{-3}	0	–	–	Width dependence	2
151	**PLWNOV**	m^{-3}	0	–	–	Length times width dependence	2
152	**NOVD**	m^{-3}	$5 \cdot 10^{25}$	10^{20}	10^{27}	Effective doping of overlap region for drain side	0
153	**NOVDO**	m^{-3}	$5 \cdot 10^{25}$	–	–	Geometry independent part	1
154	**PONOVD**	m^{-3}	$5 \cdot 10^{25}$	–	–	Geometry independent part	2
155	**PLNOVD**	m^{-3}	0	–	–	Length dependence	2
156	**PWNOVD**	m^{-3}	0	–	–	Width dependence	2
157	**PLWNOVD**	m^{-3}	0	–	–	Length times width dependence	2
				DIBL Parameters			
158	**CF**	–	0	0	–	DIBL parameter	0
159	**CFL**	–	0	–	–	Length dependence	1
160	**CFLEXP**	–	2	–	–	Exponent for length dependence	1
161	**CFW**	–	0	–	–	Width dependence	1
162	**POCF**	–	0	–	–	Geometry independent part	2
163	**PLCF**	–	0	–	–	Length dependence	2
164	**PWCF**	–	0	–	–	Width dependence	2
165	**PLWCF**	–	0	–	–	Length times width dependence	2
166	**CFB**	V^{-1}	0	0	1	Back-bias dependence of **CF**	0
167	**CFBO**	V^{-1}	0	–	–	Geometry independent part	1
168	**POCFB**	V^{-1}	0	–	–	Geometry independent part	2
				Mobility Parameters			
169	**BETN**	$m^2/V/s$	$7 \cdot 10^{-2}$	0	–	Product of channel aspect ratio and zero-field mobility at **TR**	0
170	**UO**	$m^2/V/s$	$5 \cdot 10^{-2}$	–	–	Zero-field mobility at **TR**	1
171	**FBET1**	–	0	–	–	Relative mobility decrease due to first lateral profile	1
172	**FBET1W**	–	0	–	–	Width dependence of **FBET1**	1
173	**LP1**	m	10^{-8}	10^{-10}	–	Mobility-related characteristic length of first lateral profile	1
174	**LP1W**	–	0	–	–	Width dependence of **LP1**	1

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No.	Name	Unit	Default	Min.	Max.	Description	Geo.
175	**FBET2**	–	0	–	–	Relative mobility decrease due to second lateral profile	1
176	**LP2**	m	10^{-8}	10^{-10}	–	Mobility-related characteristic length of second lateral profile	1
177	**BETW1**	–	0	–	–	First higher-order width scaling coefficient of **BETN**	1
178	**BETW2**	–	0	–	–	Second higher-order width scaling coefficient of **BETN**	1
179	**WBET**	m	10^{-9}	10^{-10}	–	Characteristic width for width scaling of **BETN**	1
180	**POBETN**	$m^2/V/s$	$7 \cdot 10^{-2}$	–	–	Geometry independent part	2
181	**PLBETN**	$m^2/V/s$	0	–	–	Length dependence	2
182	**PWBETN**	$m^2/V/s$	0	–	–	Width dependence	2
183	**PLWBETN**	$m^2/V/s$	0	–	–	Length times width dependence	2
184	**STBET**	–	1	–	–	Temperature dependence of **BETN**	0
185	**STBETO**	–	1	–	–	Geometry independent part	1
186	**STBETL**	–	0	–	–	Length dependence	1
187	**STBETW**	–	0	–	–	Width dependence	1
188	**STBETLW**	–	0	–	–	Area dependence	1
189	**POSTBET**	–	1	–	–	Geometry independent part	2
190	**PLSTBET**	–	0	–	–	Length dependence	2
191	**PWSTBET**	–	0	–	–	Width dependence	2
192	**PLWSTBET**	–	0	–	–	Length times width dependence	2
193	**MUE**	m/V	0.5	0	–	Mobility reduction coefficient at **TR**	0
194	**MUEO**	m/V	0.5	–	–	Geometry independent part	1
195	**MUEW**	–	0	–	–	Width dependence	1
196	**POMUE**	m/V	0.5	–	–	Geometry independent part	2
197	**PLMUE**	m/V	0	–	–	Length dependence	2
198	**PWMUE**	m/V	0	–	–	Width dependence	2
199	**PLWMUE**	m/V	0	–	–	Length times width dependence	2
200	**STMUE**	–	0	–	–	Temperature dependence of **MUE**	0
201	**STMUEO**	–	0	–	–	Geometry independent part	1
202	**POSTMUE**	–	0	–	–	Geometry independent part	2
203	**THEMU**	–	1.5	0	–	Mobility reduction exponent at **TR**	0
204	**THEMUO**	–	1.5	0	–	Geometry independent part	1
205	**POTHEMU**	–	1.5	–	–	Geometry independent part	2
206	**STTHEMU**	–	1.5	–	–	Temperature dependence of **THEMU**	0

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No.	Name	Unit	Default	Min.	Max.	Description	Geo.
207	**STTHEMUO**	–	1.5	–	–	Geometry independent part	1
208	**POSTTHEMU**	–	1.5	–	–	Geometry independent part	2
209	**CS**	–	0	0	–	Coulomb scattering parameter at **TR**	0
210	**CSO**	–	0	–	–	Geometry independent part	1
211	**CSL**	–	0	–	–	Length dependence	1
212	**CSLEXP**	–	1	–	–	Exponent for length dependence	1
213	**CSW**	–	0	–	–	Width dependence	1
214	**CSLW**	–	0	–	–	Area dependence	1
215	**POCS**	–	0	–	–	Geometry independent part	2
216	**PLCS**	–	0	–	–	Length dependence	2
217	**PWCS**	–	0	–	–	Width dependence	2
218	**PLWCS**	–	0	–	–	Length times width dependence	2
219	**STCS**	–	0	–	–	Temperature dependence of **CS**	0
220	**STCSO**	–	0	–	–	Geometry independent part	1
221	**POSTCS**	–	0	–	–	Geometry independent part	2
222	**XCOR**	V^{-1}	0	0	–	Non-universality parameter	0
223	**XCORO**	V^{-1}	0	–	–	Geometry independent part	1
224	**XCORL**	–	0	–	–	Length dependence	1
225	**XCORW**	–	0	–	–	Width dependence	1
226	**XCORLW**	–	0	–	–	Area dependence	1
227	**POXCOR**	V^{-1}	0	–	–	Geometry independent part	2
228	**PLXCOR**	V^{-1}	0	–	–	Length dependence	2
229	**PWXCOR**	V^{-1}	0	–	–	Width dependence	2
230	**PLWXCOR**	V^{-1}	0	–	–	Length times width dependence	2
231	**STXCOR**	–	0	–	–	Temperature dependence of **XCOR**	0
232	**STXCORO**	–	0	–	–	Geometry independent part	1
233	**POSTXCOR**	–	0	–	–	Geometry independent part	2
234	**FETA**	–	1	0	–	Effective field parameter	0
235	**FETAO**	–	1	–	–	Geometry independent part	1
236	**POFETA**	–	1	–	–	Geometry independent part	2
			Series Resistance Parameters				
237	**RS**	Ω	30	0	–	Source/drain series resistance at **TR**	0
238	**RSW1**	Ω	50	–	–	Source/drain series resistance for a channel width $W_{\rm EN}$	1

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No.	Name	Unit	Default	Min.	Max.	Description	Geo.
239	**RSW2**	–	0	–	–	Higher-order width scaling	1
240	**PORS**	Ω	30	–	–	Geometry independent part	2
241	**PLRS**	Ω	0	–	–	Length dependence	2
242	**PWRS**	Ω	0	–	–	Width dependence	2
243	**PLWRS**	Ω	0	–	–	Length times width dependence	2
244	**STRS**	–	1	–	–	Temperature dependence of **RS**	0
245	**STRSO**	–	1	–	–	Geometry dependent part	1
246	**POSTRS**	–	1	–	–	Geometry independent part	2
247	**RSB**	V^{-1}	0	−0.5	1	Back-bias dependence of **RS**	0
248	**RSBO**	V^{-1}	0	–	–	Geometry independent part	1
249	**PORSB**	V^{-1}	0	–	–	Geometry independent part	2
250	**RSG**	V^{-1}	0	−0.5	–	Gate-bias dependence of **RS**	0
251	**RSGO**	V^{-1}	0	–	–	Geometry independent part	1
252	**PORSG**	V^{-1}	0	–	–	Geometry independent part	2
				Velocity Saturation Parameters			
253	**THESAT**	V^{-1}	1	0	–	Velocity saturation parameter at **TR**	0
254	**THESATO**	V^{-1}	0	–	–	Geometry independent part	1
255	**THESATL**	V^{-1}	0.05	–	–	Length dependence	1
256	**THESATLEXP**	–	1	–	–	Exponent for length dependence	1
257	**THESATW**	–	0	–	–	Width dependence	1
258	**THESATLW**	–	0	–	–	Area dependence	1
259	**POTHESAT**	V^{-1}	1	–	–	Geometry independent part	2
260	**PLTHESAT**	V^{-1}	0	–	–	Length dependence	2
261	**PWTHESAT**	V^{-1}	0	–	–	Width dependence	2
262	**PLWTHESAT**	V^{-1}	0	–	–	Length times width dependence	2
263	**STTHESAT**	–	1	–	–	Temperature dependence of **THESAT**	0
264	**STTHESATO**	–	1	–	–	Geometry independent temperature dependence	1
265	**STTHESATL**	–	0	–	–	Length dependence	1
266	**STTHESATW**	–	0	–	–	Width dependence	1
267	**STTHESATLW**	–	0	–	–	Area dependence	1
268	**POSTTHESAT**	–	1	–	–	Geometry independent part	2
269	**PLSTTHESAT**	–	0	–	–	Length dependence	2
270	**PWSTTHESAT**	–	0	–	–	Width dependence	2
271	**PLWSTTHESAT**	–	0	–	–	Length times width dependence of temperature dependence	2

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No.	Name	Unit	Default	Min.	Max.	Description	Geo.
272	**THESATB**	V^{-1}	0	-0.5	1	Back-bias dependence of velocity saturation	0
273	**THESATBO**	V^{-1}	0	–	–	Geometry independent part	1
274	**POTHESATB**	V^{-1}	0	–	–	Geometry independent part	2
275	**PLTHESATB**	V^{-1}	0	–	–	Length dependence	2
276	**PWTHESATB**	V^{-1}	0	–	–	Width dependence	2
277	**PLWTHESATB**	V^{-1}	0	–	–	Length times width dependence	2
278	**THESATG**	V^{-1}	0	-0.5	–	Gate-bias dependence of velocity saturation	0
279	**THESATGO**	V^{-1}	0	–	–	Geometry independent part	1
280	**POTHESATG**	V^{-1}	0	–	–	Geometry independent part	2
281	**PLTHESATG**	V^{-1}	0	–	–	Length dependence	2
282	**PWTHESATG**	V^{-1}	0	–	–	Width dependence	2
283	**PLWTHESATG**	V^{-1}	0	–	–	Length times width dependence	2
				Saturation Voltage Parameter			
284	**AX**	-	3	2	–	Linear/saturation transition factor	0
285	**AXO**	–	18	–	–	Geometry independent	1
286	**AXL**	–	0.4	0	–	Length dependence	1
287	**POAX**	–	3	–	–	Geometry independent part	2
288	**PLAX**	–	0	–	–	Length dependence	2
289	**PWAX**	–	0	–	–	Width dependence	2
290	**PLWAX**	–	0	–	–	Length times width dependence	2
				Channel Length Modulation (CLM) Parameters			
291	**ALP**	–	0.01	0	–	CLM pre-factor	0
292	**ALPL**	–	$5 \cdot 10^{-4}$	–	–	Length dependence	1
293	**ALPLEXP**	–	1	–	–	Exponent for length dependence	1
294	**ALPW**	–	0	–	–	Width dependence	1
295	**POALP**	–	0.01	–	–	Geometry independent part	2
296	**PLALP**	–	0	–	–	Length dependence	2
297	**PWALP**	–	0	–	–	Width dependence	2
298	**PLWALP**	–	0	–	–	Length times width dependence	2
299	**ALP1**	V	0	0	–	CLM enhancement factor above threshold	0
300	**ALP1L1**	V	0	–	–	Length dependence	1
301	**ALP1LEXP**	–	0.5	–	–	Exponent for length dependence	1
302	**ALP1L2**	–	0	0	–	Second order length dependence	1
303	**ALP1W**	–	0	–	–	Width dependence	1
304	**POALP1**	V	0	–	–	Geometry independent part	2

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No.	Name	Unit	Default	Min.	Max.	Description	Geo.
305	**PLALP1**	V	0	–	–	Length dependence	2
306	**PWALP1**	V	0	–	–	Width dependence	2
307	**PLWALP1**	V	0	–	–	Length times width dependence	2
308	**ALP2**	V^{-1}	0	0	–	CLM enhancement factor below threshold	0
309	**ALP2L1**	V	0	–	–	Length dependence	1
310	**ALP2LEXP**	–	0.5	–	–	Exponent for length dependence	1
311	**ALP2L2**	–	0	0	–	Second order length dependence	1
312	**ALP2W**	–	0	–	–	Width dependence	1
313	**POALP2**	V^{-1}	0	–	–	Geometry independent part	2
314	**PLALP2**	V^{-1}	0	–	–	Length dependence	2
315	**PWALP2**	V^{-1}	0	–	–	Width dependence	2
316	**PLWALP2**	V^{-1}	0	–	–	Length times width dependence	2
317	**VP**	V	0.05	10^{-10}	–	CLM logarithmic dependence parameter	0
318	**VPO**	V	0.05	–	–	Geometry independent part	1
319	**POVP**	V	0.05	–	–	Geometry independent part	2
				Impact Ionization (II) Parameters			
320	**A1**	–	1	0	–	Impact-ionization pre-factor	0
321	**A1O**	–	1	–	–	Geometry independent part	1
322	**A1L**	–	0	–	–	Length dependence	1
323	**A1W**	–	0	–	–	Width dependence	1
324	**POA1**	–	1	–	–	Geometry independent part	2
325	**PLA1**	–	0	–	–	Length dependence	2
326	**PWA1**	–	0	–	–	Width dependence	2
327	**PLWA1**	–	0	–	–	Length times width dependence	2
328	**A2**	V	10	0	–	Impact-ionization exponent at **TR**	0
329	**A2O**	V	10	–	–	Geometry independent part	1
330	**POA2**	V	10	–	–	Geometry independent part	2
331	**STA2**	V	0	–	–	Temperature dependence of **A2**	0
332	**STA2O**	V	0	–	–	Geometry independent part	1
333	**POSTA2**	V	0	–	–	Geometry independent part	2
334	**A3**	–	1	0	–	Saturation-voltage dependence of II	0
335	**A3O**	–	1	–	–	Geometry independent part	1
336	**A3L**	–	0	–	–	Length dependence	1
337	**A3W**	–	0	–	–	Width dependence	1

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No.	Name	Unit	Default	Min.	Max.	Description	Geo.
338	**POA3**	–	1	–	–	Geometry independent part	2
339	**PLA3**	–	0	–	–	Length dependence	2
340	**PWA3**	–	0	–	–	Width dependence	2
341	**PLWA3**	–	0	–	–	Length times width dependence	2
342	**A4**	$V^{-\frac{1}{2}}$	0	0	–	Back-bias dependence of II	0
343	**A4O**	$V^{-\frac{1}{2}}$	0	–	–	Geometry independent part	1
344	**A4L**	–	0	–	–	Length dependence	1
345	**A4W**	–	0	–	–	Width dependence	1
346	**POA4**	$V^{-\frac{1}{2}}$	0	–	–	Geometry independent part	2
347	**PLA4**	$V^{-\frac{1}{2}}$	0	–	–	Length dependence	2
348	**PWA4**	$V^{-\frac{1}{2}}$	0	–	–	Width dependence	2
349	**PLWA4**	$V^{-\frac{1}{2}}$	0	–	–	Length times width dependence	2
						Gate Current Parameters	
350	**GCO**	–	0	−10	10	Gate tunnelling energy adjustment	0
351	**GCOO**	–	0	–	–	Geometry independent part	1
352	**POGCO**	–	0	–	–	Geometry independent part	2
353	**IGINV**	A	0	0	–	Gate channel current pre-factor	0
354	**IGINVLW**	A	0	–	–	Gate channel current pre-factor for a channel area of $W_{\mathrm{EN}} \cdot L_{\mathrm{EN}}$	1
355	**POIGINV**	A	0	–	–	Geometry independent part	2
356	**PLIGINV**	A	0	–	–	Length dependence	2
357	**PWIGINV**	A	0	–	–	Width dependence	2
358	**PLWIGINV**	A	0	–	–	Length times width dependence	2
359	**IGOV**	A	0	0	–	Gate overlap current pre-factor	0
360	**IGOVW**	A	0	–	–	Gate overlap current pre-factor for a channel width of W_{EN}	1
361	**POIGOV**	A	0	–	–	Geometry independent part	2
362	**PLIGOV**	A	0	–	–	Length dependence	2
363	**PWIGOV**	A	0	–	–	Width dependence	2
364	**PLWIGOV**	A	0	–	–	Length times width dependence	2
365	**IGOVD**	A	0	0	–	Gate overlap current pre-factor for drain side	0
366	**IGOVDW**	A	0	–	–	Gate overlap current pre-factor for a channel width of W_{EN} for drain side	1
367	**POIGOVD**	A	0	–	–	Geometry independent part	2
368	**PLIGOVD**	A	0	–	–	Length dependence	2
369	**PWIGOVD**	A	0	–	–	Width dependence	2

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No.	Name	Unit	Default	Min.	Max.	Description	Geo.
370	**PLWIGOVD**	A	0	–	–	Length times width dependence	2
371	**STIG**	–	2	–	–	Temperature dependence of gate current	0
372	**STIGO**	–	2	–	–	Geometry independent part	1
373	**POSTIG**	–	2	–	–	Geometry independent part	2
374	**GC2**	–	0.375	0	10	Gate current slope factor	0
375	**GC2O**	–	0.375	–	–	Geometry independent part	1
376	**POGC2**	–	$3.75 \cdot 10^{-1}$	–	–	Geometry independent part	2
377	**GC3**	–	0.063	-2	2	Gate current curvature factor	0
378	**GC3O**	–	0.063	–	–	Geometry independent part	1
379	**POGC3**	–	$6.3 \cdot 10^{-2}$	–	–	Geometry independent part	2
380	**CHIB**	V	3.1	1	–	Tunnelling barrier height	0
381	**CHIBO**	V	3.1	–	–	Geometry independent part	1
382	**POCHIB**	V	3.1	–	–	Geometry independent part	2
						Gate-Induced Drain Leakage (GIDL) Parameters	
383	**AGIDL**	A/V^3	0	0	–	GIDL pre-factor	0
384	**AGIDLW**	A/V^3	0	–	–	Width dependence	1
385	**POAGIDL**	A/V^3	0	–	–	Geometry independent part	2
386	**PLAGIDL**	A/V^3	0	–	–	Length dependence	2
387	**PWAGIDL**	A/V^3	0	–	–	Width dependence	2
388	**PLWAGIDL**	A/V^3	0	–	–	Length times width dependence	2
389	**AGIDLD**	A/V^3	0	0	–	GIDL pre-factor for drain side	0
390	**AGIDLDW**	A/V^3	0	–	–	Width dependence	1
391	**POAGIDLD**	A/V^3	0	–	–	Geometry independent part	2
392	**PLAGIDLD**	A/V^3	0	–	–	Length dependenceof	2
393	**PWAGIDLD**	A/V^3	0	–	–	Width dependenceof	2
394	**PLWAGIDLD**	A/V^3	0	–	–	Length times width dependence	2
395	**BGIDL**	V	41	0	–	GIDL probability factor at **TR**	0
396	**BGIDLO**	V	41	–	–	Geometry independent part	1
397	**POBGIDL**	V	41	–	–	Geometry independent part	2
398	**BGIDLD**	V	41	0	–	GIDL probability factor at **TR** for drain side	0
399	**BGIDLDO**	V	41	–	–	Geometry independent part	1
400	**POBGIDLD**	V	41	–	–	Geometry independent part	2

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No.	Name	Unit	Default	Min.	Max.	Description	Geo.
401	**STBGIDL**	V/K	0	–	–	Temperature dependence of **BGIDL**	0
402	**STBGIDLO**	V/K	0	–	–	Geometry independent part	1
403	**POSTBGIDL**	V/K	0	–	–	Geometry independent part	2
404	**STBGIDLD**	V/K	0	–	–	Temperature dependence of **BGIDL** for drain side	0
405	**STBGIDLDO**	V/K	0	–	–	Geometry independent part	1
406	**POSTBGIDLD**	V/K	0	–	–	Geometry independent part	2
407	**CGIDL**	–	0	–	–	Back-bias dependence of GIDL	0
408	**CGIDLO**	–	0	–	–	Geometry independent part	1
409	**POCGIDL**	–	0	–	–	Geometry independent part	2
410	**CGIDLD**	–	0	–	–	Back-bias dependence of GIDL for drain side	0
411	**CGIDLDO**	–	0	–	–	Geometry independent part	1
412	**POCGIDLD**	–	0	–	–	Geometry independent part	2
			Charge Model Parameters				
413	**COX**	F	10^{-14}	0	–	Oxide capacitance for intrinsic channel	0
414	**POCOX**	F	10^{-14}	–	–	Geometry independent part	2
415	**PLCOX**	F	0	–	–	Length dependence	2
416	**PWCOX**	F	0	–	–	Width dependence	2
417	**PLWCOX**	F	0	–	–	Length times width dependence	2
418	**CGOV**	F	10^{-15}	0	–	Oxide capacitance for gate–drain/source overlap	0
419	**POCGOV**	F	10^{-15}	–	–	Geometry independent part	2
420	**PLCGOV**	F	0	–	–	Length dependence	2
421	**PWCGOV**	F	0	–	–	Width dependence	2
422	**PLWCGOV**	F	0	–	–	Length times width dependence	2
423	**CGOVD**	F	10^{-15}	0	–	Oxide capacitance for gate–drain/source overlap for drain side	0
424	**POCGOVD**	F	10^{-15}	–	–	Geometry independent part	2
425	**PLCGOVD**	F	0	–	–	Length dependence	2
426	**PWCGOVD**	F	0	–	–	Width dependence	2
427	**PLWCGOVD**	F	0	–	–	Length times width dependence	2
428	**CGBOV**	F	0	0	–	Oxide capacitance for gate–bulk overlap	0

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No.	Name	Unit	Default	Min.	Max.	Description	Geo.
429	**CGBOVL**	F	0	–	–	Oxide capacitance for gate–bulk overlap for a channel length of L_{EN}	1
430	**POCGBOV**	F	0	–	–	Geometry independent part	2
431	**PLCGBOV**	F	0	–	–	Length dependence	2
432	**PWCGBOV**	F	0	–	–	Width dependence	2
433	**PLWCGBOV**	F	0	–	–	Length times width dependence	2
434	**CFR**	F	0	0	–	Outer fringe capacitance	0
435	**CFRW**	F	0	–	–	Outer fringe capacitance for a channel width of W_{EN}	1
436	**POCFR**	F	0	–	–	Geometry independent part	2
437	**PLCFR**	F	0	–	–	Length dependence	2
438	**PWCFR**	F	0	–	–	Width dependence	2
439	**PLWCFR**	F	0	–	–	Length times width dependence	2
440	**CFRD**	F	0	0	–	Outer fringe capacitance for drain side	0
441	**CFRDW**	F	0	–	–	Outer fringe capacitance for a channel width of W_{EN} for drain side	1
442	**POCFRD**	F	0	–	–	Geometry independent part	2
443	**PLCFRD**	F	0	–	–	Length dependence	2
444	**PWCFRD**	F	0	–	–	Width dependence	2
445	**PLWCFRD**	F	0	–	–	Length times width dependence	2
				Noise Model Parameters			
446	**FNT**	–	1	0	–	Thermal noise coefficient	0
447	**FNTO**	–	1	–	–	Geometry independent part	1
448	**POFNT**	–	1	–	–	Geometry independent part	2
449	**NFA**	$\mathrm{V}^{-1}/\mathrm{m}^4$	$8 \cdot 10^{22}$	0	–	First coefficient of flicker noise	0
450	**NFALW**	$\mathrm{V}^{-1}/\mathrm{m}^4$	$8 \cdot 10^{22}$	–	–	First coefficient of flicker noise for a channel area of $W_{\mathrm{EN}} \cdot L_{\mathrm{EN}}$	1
451	**PONFA**	$\mathrm{V}^{-1}/\mathrm{m}^4$	$8 \cdot 10^{22}$	–	–	Geometry independent part	2
452	**PLNFA**	$\mathrm{V}^{-1}/\mathrm{m}^4$	0	–	–	Length dependence	2
453	**PWNFA**	$\mathrm{V}^{-1}/\mathrm{m}^4$	0	–	–	Width dependence	2
454	**PLWNFA**	$\mathrm{V}^{-1}/\mathrm{m}^4$	0	–	–	Length times width dependence	2
455	**NFB**	$\mathrm{V}^{-1}/\mathrm{m}^2$	$3 \cdot 10^{7}$	0	–	Second coefficient of flicker noise	0
456	**NFBLW**	$\mathrm{V}^{-1}/\mathrm{m}^2$	$3 \cdot 10^{7}$	–	–	Second coefficient of flicker noise for a channel area of $W_{\mathrm{EN}} \cdot L_{\mathrm{EN}}$	1
457	**PONFB**	$\mathrm{V}^{-1}/\mathrm{m}^2$	$3 \cdot 10^{7}$	–	–	Geometry independent part	2

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No.	Name	Unit	Default	Min.	Max.	Description	Geo.
458	**PLNFB**	V^{-1}/m^2	0	–	–	Length dependence	2
459	**PWNFB**	V^{-1}/m^2	0	–	–	Width dependence	2
460	**PLWNFB**	V^{-1}/m^2	0	–	–	Length times width dependence	2
461	**NFC**	V^{-1}	0	0	–	Third coefficient of flicker noise	0
462	**NFCLW**	V^{-1}	0	–	–	Third coefficient of flicker noise for a channel area of $W_{\mathrm{EN}} \cdot L_{\mathrm{EN}}$	1
463	**PONFC**	V^{-1}	0	–	–	Geometry independent part	2
464	**PLNFC**	V^{-1}	0	–	–	Length dependence	2
465	**PWNFC**	V^{-1}	0	–	–	Width dependence	2
466	**PLWNFC**	V^{-1}	0	–	–	Length times width dependence	2
467	**EF**	–	1	0	–	Flicker noise frequency exponent	0
468	**EFO**	–	1	–	–	Geometry independent part	1
469	**POEF**	–	1	–	–	Geometry independent part	2
470	**LINTNOI**	m	0	–	–	Length offset for flicker noise	1
471	**ALPNOI**	–	2	–	–	Exponent for length offset	1

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2.5.3 Parameters for stress model

The stress model of BSIM4.4.0 has been adopted in PSP with as little modifications as possible. Parameter names have been copied, but they have been subjected to PSP conventions by replacing every zero by an '**O**'. Moreover, the parameters **STK2** and **LODK2** are not available in PSP. Except for these changes, stress parameters determined for BSIM can be directly applied in PSP. Some trivial conversion of parameters BSIM→PSP is still necessary, see [2].

The parameters in this section are part of PSP's global parameter set (both geometrical and binning).

No.	Name	Unit	Default	Min.	Max.	Description	Geo.
0	**SAREF**	m	10^{-6}	10^{-9}	–	Reference distance between OD edge to Poly from one side	1, 2
1	**SBREF**	m	10^{-6}	10^{-9}	–	Reference distance between OD edge to Poly from other side	1, 2
2	**WLOD**	m	0	–	–	Width parameter	1, 2
3	**KUO**	m	0	–	–	Mobility degradation/enhancement coefficient	1, 2
4	**KVSAT**	m	0	-1	1	Saturation velocity degradation/enhancement parameter	1, 2
5	**TKUO**	–	0	–	–	Temperature coefficient of **KUO**	1, 2
6	**LKUO**	$\mathrm{m}^{\mathbf{LLODKUO}}$	0	–	–	Length dependence of **KUO**	1, 2
7	**WKUO**	$\mathrm{m}^{\mathbf{WLODKUO}}$	0	–	–	Width dependence of **KUO**	1, 2
8	**PKUO**	$\mathrm{m}^{\mathbf{LLODKUO+WLODKUO}}$	0	–	–	Cross-term dependence of **KUO**	1, 2
9	**LLODKUO**	–	0	0	–	Length parameter for mobility stress effect	1, 2
10	**WLODKUO**	–	0	0	–	Width parameter for mobility stress effect	1, 2
11	**KVTHO**	Vm	0	–	–	Threshold shift parameter	1, 2
12	**LKVTHO**	$\mathrm{m}^{\mathbf{LLODVTH}}$	0	–	–	Length dependence of **KVTHO**	1, 2
13	**WKVTHO**	$\mathrm{m}^{\mathbf{WLODVTH}}$	0	–	–	Width dependence of **KVTHO**	1, 2
14	**PKVTHO**	$\mathrm{m}^{\mathbf{LLODVTH+WLODVTH}}$	0	–	–	Cross-term dependence of **KVTHO**	1, 2
15	**LLODVTH**	–	0	0	–	Length parameter for threshold voltage stress effect	1, 2
16	**WLODVTH**	–	0	0	–	Width parameter for threshold voltage stress effect	1, 2
17	**STETAO**	m	0	–	–	ETAO shift factor related to threshold voltage change	1, 2
18	**LODETAO**	–	1	0	–	ETAO shift modification factor	1, 2

2.5.4 Parameters for well proximity effect model

The WPE model of BSIM4.5.0 has been adopted in PSP with as little modifications as possible. Parameter names have been copied, but they have been subjected to PSP conventions by replacing every zero by an '**O**'. Moreover, the parameter **K2WE** is not available in PSP. Except for some trivial conversion of parameters BSIM→PSP [2], WPE parameters from BSIM can be used directly in PSP. The WPE parameters have both geometrical and binning rules included as explained in Section 3.6.2. The last column—labeled '**Geo.**'—shows for which value of **SWGEO** the parameter is used.

No.	Name	Unit	Default	Min.	Max.	Description	Geo.
0	**SCREF**	m	$1 \cdot 10^{-6}$	0	–	Distance between OD-edge and well edge of a reference device	1, 2
1	**WEB**	–	0	–	–	Coefficient for **SCB**	1, 2
2	**WEC**	–	0	–	–	Coefficient for **SCC**	1, 2
3	**KVTHOWEO**	–	0	–	–	Geometry independent threshold shift parameter	1
4	**KVTHOWEL**	–	0	–	–	Length dependence	1
5	**KVTHOWEW**	–	0	–	–	Width dependence	1
6	**KVTHOWELW**	–	0	–	–	Area dependence	1
7	**POKVTHOWE**	–	0	–	–	Geometry independent part of threshold shift parameter	2
8	**PLKVTHOWE**	–	0	–	–	Length dependence	2
9	**PWKVTHOWE**	–	0	–	–	Width dependence	2
10	**PLWKVTHOWE**	–	0	–	–	Length times width dependence	2
11	**KUOWEO**	–	0	–	–	Geometry independent mobility degradation factor	1
12	**KUOWEL**	–	0	–	–	Length dependence	1
13	**KUOWEW**	–	0	–	–	Width dependence	1
14	**KUOWELW**	–	0	–	–	Area dependence	1
15	**POKUOWE**	–	0	–	–	Geometry independent part of mobility degradation factor	2
16	**PLKUOWE**	–	0	–	–	Length dependence	2
17	**PWKUOWE**	–	0	–	–	Width dependence	2
18	**PLWKUOWE**	–	0	–	–	Length times width dependence	2

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2.5.5 Parameters for source-bulk and drain-bulk junction model

The JUNCAP2 parameters are part of both the global and the local parameter sets. The last column of **Asym.** shows for which value of **SWJUNASYM** the listed parameter is enabled: i.e., when **SWJUNASYM** $= 0$, parameters No. 3-45 are used for both source-bulk and drain-bulk junctions and parameters No. 46-88 are ignored; when **SWJUNASYM** $= 1$, parameters No. 3-45 are used for source-bulk junction and No. 46-88 are used for drain-bulk junction; parameters No. 0-2 are used in both situations.

No.	Name	Unit	Default	Min.	Max.	Description	Asym.
0	**TRJ**	°C	21	$T_{\min}$	–	Reference temperature	0, 1
1	**SWJUNEXP**	–	0	0	1	Flag for JUNCAP2 Express; 0 $\leftrightarrow$ full JUNCAP2 model, 1 $\leftrightarrow$ Express model	0, 1
2	**IMAX**	A	1000	10^{-12}	–	Maximum current up to which forward current behaves exponentially	0, 1
				Capacitance Parameters			
3	**CJORBOT**	F/m^2	10^{-3}	10^{-12}	–	Zero-bias capacitance per unit-of-area of bottom component for source-bulk junction	0, 1
4	**CJORSTI**	F/m	10^{-9}	10^{-18}	–	Zero-bias capacitance per unit-of-length of STI-edge component for source-bulk junction	0, 1
5	**CJORGAT**	F/m	10^{-9}	10^{-18}	–	Zero-bias capacitance per unit-of-length of gate-edge component for source-bulk junction	0, 1
6	**VBIRBOT**	V	1	$V_{\mathrm{bi,low}}$	–	Built-in voltage at the reference temperature of bottom component for source-bulk junction	0, 1
7	**VBIRSTI**	V	1	$V_{\mathrm{bi,low}}$	–	Built-in voltage at the reference temperature of STI-edge component for source-bulk junction	0, 1
8	**VBIRGAT**	V	1	$V_{\mathrm{bi,low}}$	–	Built-in voltage at the reference temperature of gate-edge component for source-bulk junction	0, 1
9	**PBOT**	–	0.5	0.05	0.95	Grading coefficient of bottom component for source-bulk junction	0, 1
10	**PSTI**	–	0.5	0.05	0.95	Grading coefficient of STI-edge component for source-bulk junction	0, 1
11	**PGAT**	–	0.5	0.05	0.95	Grading coefficient of gate-edge component for source-bulk junction	0, 1
				Ideal-current Parameters			

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No.	Name	Unit	Default	Min.	Max.	Description	Asym.
12	**PHIGBOT**	V	1.16	–	–	Zero-temperature bandgap voltage of bottom component for source-bulk junction	0, 1
13	**PHIGSTI**	V	1.16	–	–	Zero-temperature bandgap voltage of STI-edge component for source-bulk junction	0, 1
14	**PHIGGAT**	V	1.16	–	–	Zero-temperature bandgap voltage of gate-edge component for source-bulk junction	0, 1
15	**IDSATRBOT**	A/m^2	10^{-12}	0	–	Saturation current density at the reference temperature of bottom component for source-bulk junction	0, 1
16	**IDSATRSTI**	A/m	10^{-18}	0	–	Saturation current density at the reference temperature of STI-edge component for source-bulk junction	0, 1
17	**IDSATRGAT**	A/m	10^{-18}	0	–	Saturation current density at the reference temperature of gate-edge component for source-bulk junction	0, 1
				Shockley-Read-Hall Parameters			
18	**CSRHBOT**	A/m^3	10^2	0	–	Shockley-Read-Hall prefactor of bottom component for source-bulk junction	0, 1
19	**CSRHSTI**	A/m^2	10^{-4}	0	–	Shockley-Read-Hall prefactor of STI-edge component for source-bulk junction	0, 1
20	**CSRHGAT**	A/m^2	10^{-4}	0	–	Shockley-Read-Hall prefactor of gate-edge component for source-bulk junction	0, 1
21	**XJUNSTI**	m	10^{-7}	10^{-9}	–	Junction depth of STI-edge component for source-bulk junction	0, 1
22	**XJUNGAT**	m	10^{-7}	10^{-9}	–	Junction depth of gate-edge component for source-bulk junction	0, 1
				Trap-assisted Tunneling Parameters			
23	**CTATBOT**	A/m^3	10^2	0	–	Trap-assisted tunneling prefactor of bottom component for source-bulk junction	0, 1
24	**CTATSTI**	A/m^2	10^{-4}	0	–	Trap-assisted tunneling prefactor of STI-edge component for source-bulk junction	0, 1
25	**CTATGAT**	A/m^2	10^{-4}	0	–	Trap-assisted tunneling prefactor of gate-edge component for source-bulk junction	0, 1

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No.	Name	Unit	Default	Min.	Max.	Description	Asym.
26	**MEFFTATBOT**	–	0.25	.01	–	Effective mass (in units of m_0) for trap-assisted tunneling of bottom component for source-bulk junction	0, 1
27	**MEFFTATSTI**	–	0.25	.01	–	Effective mass (in units of m_0) for trap-assisted tunneling of STI-edge component for source-bulk junction	0, 1
28	**MEFFTATGAT**	–	0.25	.01	–	Effective mass (in units of m_0) for trap-assisted tunneling of gate-edge component for source-bulk junction	0, 1
				Band-to-band Tunneling Parameters			
29	**CBBTBOT**	AV^{-3}	10^{-12}	0	–	Band-to-band tunneling prefactor of bottom component for source-bulk junction	0, 1
30	**CBBTSTI**	$\mathrm{AV}^{-3}\mathrm{m}$	10^{-18}	0	–	Band-to-band tunneling prefactor of STI-edge component for source-bulk junction	0, 1
31	**CBBTGAT**	$\mathrm{AV}^{-3}\mathrm{m}$	10^{-18}	0	–	Band-to-band tunneling prefactor of gate-edge component for source-bulk junction	0, 1
32	**FBBTRBOT**	Vm^{-1}	10^{9}	–	–	Normalization field at the reference temperature for band-to-band tunneling of bottom component for source-bulk junction	0, 1
33	**FBBTRSTI**	Vm^{-1}	10^{9}	–	–	Normalization field at the reference temperature for band-to-band tunneling of STI-edge component for source-bulk junction	0, 1
34	**FBBTRGAT**	Vm^{-1}	10^{9}	–	–	Normalization field at the reference temperature for band-to-band tunneling of gate-edge component for source-bulk junction	0, 1
35	**STFBBTBOT**	K^{-1}	-10^{-3}	–	–	Temperature scaling parameter for band-to-band tunneling of bottom component for source-bulk junction	0, 1
36	**STFBBTSTI**	K^{-1}	-10^{-3}	–	–	Temperature scaling parameter for band-to-band tunneling of STI-edge component for source-bulk junction	0, 1
37	**STFBBTGAT**	K^{-1}	-10^{-3}	–	–	Temperature scaling parameter for band-to-band tunneling of gate-edge component for source-bulk junction	0, 1
				Avalanche and Breakdown Parameters			

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No.	Name	Unit	Default	Min.	Max.	Description	Asym.
38	**VBRBOT**	V	10	0.1	–	Breakdown voltage of bottom component for source-bulk junction	0, 1
39	**VBRSTI**	V	10	0.1	–	Breakdown voltage of STI-edge component for source-bulk junction	0, 1
40	**VBRGAT**	V	10	0.1	–	Breakdown voltage of gate-edge component for source-bulk junction	0, 1
41	**PBRBOT**	V	4	0.1	–	Breakdown onset tuning parameter of bottom component for source-bulk junction	0, 1
42	**PBRSTI**	V	4	0.1	–	Breakdown onset tuning parameter of STI-edge component for source-bulk junction	0, 1
43	**PBRGAT**	V	4	0.1	–	Breakdown onset tuning parameter of gate-edge component for source-bulk junction	0, 1
				JUNCAP Express Parameters			
44	**VJUNREF**	V	2.5	0.5	–	Typical maximum source-bulk junction voltage; usually about $2 \cdot V_{\mathrm{sup}}$	0, 1
45	**FJUNQ**	V	0.03	0	–	Fraction below which source-bulk junction capacitance components are neglected	0, 1
				Capacitance Parameters			
46	**CJORBOTD**	F/m^2	10^{-3}	10^{-12}	–	Zero-bias capacitance per unit-of-area of bottom component for drain-bulk junction	1
47	**CJORSTID**	F/m	10^{-9}	10^{-18}	–	Zero-bias capacitance per unit-of-length of STI-edge component for drain-bulk junction	1
48	**CJORGATD**	F/m	10^{-9}	10^{-18}	–	Zero-bias capacitance per unit-of-length of gate-edge component for drain-bulk junction	1
49	**VBIRBOTD**	V	1	$V_{\mathrm{bi,low}}$	–	Built-in voltage at the reference temperature of bottom component for drain-bulk junction	1
50	**VBIRSTID**	V	1	$V_{\mathrm{bi,low}}$	–	Built-in voltage at the reference temperature of STI-edge component for drain-bulk junction	1
51	**VBIRGATD**	V	1	$V_{\mathrm{bi,low}}$	–	Built-in voltage at the reference temperature of gate-edge component for drain-bulk junction	1
52	**PBOTD**	–	0.5	0.05	0.95	Grading coefficient of bottom component for drain-bulk junction	1

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No.	Name	Unit	Default	Min.	Max.	Description	Asym.
53	**PSTID**	–	0.5	0.05	0.95	Grading coefficient of STI-edge component for drain-bulk junction	1
54	**PGATD**	–	0.5	0.05	0.95	Grading coefficient of gate-edge component for drain-bulk junction	1
						Ideal-current Parameters	
55	**PHIGBOTD**	V	1.16	–	–	Zero-temperature bandgap voltage of bottom component for drain-bulk junction	1
56	**PHIGSTID**	V	1.16	–	–	Zero-temperature bandgap voltage of STI-edge component for drain-bulk junction	1
57	**PHIGGATD**	V	1.16	–	–	Zero-temperature bandgap voltage of gate-edge component for drain-bulk junction	1
58	**IDSATRBOTD**	A/m^2	10^{-12}	0	–	Saturation current density at the reference temperature of bottom component for drain-bulk junction	1
59	**IDSATRSTID**	A/m	10^{-18}	0	–	Saturation current density at the reference temperature of STI-edge component for drain-bulk junction	1
60	**IDSATRGATD**	A/m	10^{-18}	0	–	Saturation current density at the reference temperature of gate-edge component for drain-bulk junction	1
						Shockley-Read-Hall Parameters	
61	**CSRHBOTD**	A/m^3	10^2	0	–	Shockley-Read-Hall prefactor of bottom component for drain-bulk junction	1
62	**CSRHSTID**	A/m^2	10^{-4}	0	–	Shockley-Read-Hall prefactor of STI-edge component for drain-bulk junction	1
63	**CSRHGATD**	A/m^2	10^{-4}	0	–	Shockley-Read-Hall prefactor of gate-edge component for drain-bulk junction	1
64	**XJUNSTID**	m	10^{-7}	10^{-9}	–	Junction depth of STI-edge component for drain-bulk junction	1
65	**XJUNGATD**	m	10^{-7}	10^{-9}	–	Junction depth of gate-edge component for drain-bulk junction	1
						Trap-assisted Tunneling Parameters	
66	**CTATBOTD**	A/m^3	10^2	0	–	Trap-assisted tunneling prefactor of bottom component for drain-bulk junction	1
67	**CTATSTID**	A/m^2	10^{-4}	0	–	Trap-assisted tunneling prefactor of STI-edge component for drain-bulk junction	1

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No.	Name	Unit	Default	Min.	Max.	Description	Asym.
68	**CTATGATD**	A/m^2	10^{-4}	0	–	Trap-assisted tunneling prefactor of gate-edge component for drain-bulk junction	1
69	**MEFFTATBOTD**	–	0.25	.01	–	Effective mass (in units of m_0) for trap-assisted tunneling of bottom component for drain-bulk junction	1
70	**MEFFTATSTID**	–	0.25	.01	–	Effective mass (in units of m_0) for trap-assisted tunneling of STI-edge component for drain-bulk junction	1
71	**MEFFTATGATD**	–	0.25	.01	–	Effective mass (in units of m_0) for trap-assisted tunneling of gate-edge component for drain-bulk junction	1
						Band-to-band Tunneling Parameters	
72	**CBBTBOTD**	AV^{-3}	10^{-12}	0	–	Band-to-band tunneling prefactor of bottom component for drain-bulk junction	1
73	**CBBTSTID**	AV^{-3}m	10^{-18}	0	–	Band-to-band tunneling prefactor of STI-edge component for drain-bulk junction	1
74	**CBBTGATD**	AV^{-3}m	10^{-18}	0	–	Band-to-band tunneling prefactor of gate-edge component for drain-bulk junction	1
75	**FBBTRBOTD**	Vm^{-1}	10^9	–	–	Normalization field at the reference temperature for band-to-band tunneling of bottom component for drain-bulk junction	1
76	**FBBTRSTID**	Vm^{-1}	10^9	–	–	Normalization field at the reference temperature for band-to-band tunneling of STI-edge component for drain-bulk junction	1
77	**FBBTRGATD**	Vm^{-1}	10^9	–	–	Normalization field at the reference temperature for band-to-band tunneling of gate-edge component for drain-bulk junction	1
78	**STFBBTBOTD**	K^{-1}	-10^{-3}	–	–	Temperature scaling parameter for band-to-band tunneling of bottom component for drain-bulk junction	1
79	**STFBBTSTID**	K^{-1}	-10^{-3}	–	–	Temperature scaling parameter for band-to-band tunneling of STI-edge component for drain-bulk junction	1
80	**STFBBTGATD**	K^{-1}	-10^{-3}	–	–	Temperature scaling parameter for band-to-band tunneling of gate-edge component for drain-bulk junction	1
						Avalanche and Breakdown Parameters	

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No.	Name	Unit	Default	Min.	Max.	Description	Asym.
81	**VBRBOTD**	V	10	0.1	–	Breakdown voltage of bottom component for drain-bulk junction	1
82	**VBRSTID**	V	10	0.1	–	Breakdown voltage of STI-edge component for drain-bulk junction	1
83	**VBRGATD**	V	10	0.1	–	Breakdown voltage of gate-edge component for drain-bulk junction	1
84	**PBRBOTD**	V	4	0.1	–	Breakdown onset tuning parameter of bottom component for drain-bulk junction	1
85	**PBRSTID**	V	4	0.1	–	Breakdown onset tuning parameter of STI-edge component for drain-bulk junction	1
86	**PBRGATD**	V	4	0.1	–	Breakdown onset tuning parameter of gate-edge component for drain-bulk junction	1
				JUNCAP Express Parameters			
87	**VJUNREFD**	V	2.5	0.5	–	Typical maximum drain-bulk junction voltage; usually about $2 \cdot V_{\rm sup}$	1
88	**FJUNQD**	V	0.03	0	–	Fraction below which drain-bulk junction capacitance components are neglected	1

2.5.6 Parameters for parasitic resistances

The parameters for parasitic resistances are listed in the table below. The last column—labeled '**Geo.**'—shows for which value of **SWGEO** the parameter is used.

No.	Name	Unit	Default	Min.	Max.	Description	Geo.
0	**RG**	Ω	0	0	–	Gate resistance R_{gate}	0
1	**RGO**	Ω	0	–	–	Gate resistance R_{gate}	1, 2
2	**RINT**	Ω·m^2	0	0	–	Contact resistance between silicide and ploy	1, 2
3	**RVPOLY**	Ω·m^2	0	0	–	Vertical poly resistance	1, 2
4	**RSHG**	Ω/□	0	0	–	Gate electrode diffusion sheet resistance	1, 2
5	**DLSIL**	m	0	–	–	Silicide extension over the physical gate length	1, 2
6	**RSE**	Ω	0	0	–	External source resistance	0
7	**RDE**	Ω	0	0	–	External drain resistance	0
8	**RSH**	Ω/□	0	–	–	Sheet resistance of source diffusion	1, 2
9	**RSHD**	Ω/□	0	–	–	Sheet resistance of drain diffusion	1, 2
10	**RBULK**	Ω	0	0	–	Bulk resistance R_{bulk}	0
11	**RBULKO**	Ω	0	–	–	Bulk resistance R_{bulk}	1, 2
12	**RWELL**	Ω	0	0	–	Well resistance R_{well}	0
13	**RWELLO**	Ω	0	–	–	Well resistance R_{well}	1, 2
14	**RJUNS**	Ω	0	0	–	Source-side bulk resistance R_{juns}	0
15	**RJUNSO**	Ω	0	–	–	Source-side bulk resistance R_{juns}	1, 2
16	**RJUND**	Ω	0	0	–	Drain-side bulk resistance R_{jund}	0
17	**RJUNDO**	Ω	0	–	–	Drain-side bulk resistance R_{jund}	1, 2

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2.5.7 Parameters for self heating

The parameters for self heating are listed below. They are only available in the self heating version of the model. The last column—labeled '**Geo.**'—shows for which value of **SWGEO** the parameter is used.

No.	Name	Unit	Default	Min.	Max.	Description	Geo.
0	**RTH**	K/W	0	0	–	Thermal resistance	0
1	**RTHO**	K/W	0	–	–	Geometry independent part	1, 2
2	**RTHW1**	K/W	0	–	–	Width dependence	1, 2
3	**RTHW2**	–	0	–	–	Offset in width dependence	1, 2
4	**RTHLW**	–	0	–	–	Length-correction to width dependence	1, 2
5	**CTH**	J/K	0	0	–	Thermal capacitance	0
6	**CTHO**	J/K	0	–	–	Geometry independent part	1, 2
7	**CTHW1**	J/K	0	–	–	Width dependence	1, 2
8	**CTHW2**	–	0	–	–	Offset in width dependence	1, 2
9	**CTHLW**	–	0	–	–	Length-correction to width dependence	1, 2
10	**STRTH**	–	0	–	–	Temperature sensitivity of **RTH**	0
11	**STRTHO**	–	0	–	–	Geometry independent part	1, 2

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2.5.8 Parameters for NQS

The parameters for non-quasi-static effects are listed below. They are only available in the NQS-version of the model. The last column—labeled '**Geo.**'—shows for which value of **SWGEO** the parameter is used.

No.	Name	Unit	Default	Min.	Max.	Description	Geo.
0	**SWNQS**	–	0	0	9	Switch for NQS effects / number of collocation points	0, 1, 2
1	**MUNQS**	–	1	0	–	Relative mobility for NQS modeling	0
2	**MUNQSO**	–	1	–	–	Relative mobility for NQS modeling	1, 2

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Section 3

Geometry dependence and Other effects

3.1 Introduction

The physical geometry scaling rules of PSP (Section 3.2) have been developed to give a good description over the whole geometry range of CMOS technologies. As an alternative, the binning-rules can be used (Section 3.3) to allow for a more phenomenological geometry dependency. (Note that the user has to choose between the two options; the geometrical scaling rules and the binning scaling rules cannot be used at the same time.) In both cases, the result is a local parameter set (for a transistor of the specified L and W), which is fed into the local model.

Stress and well proximity effects are included in PSP. Use of the stress model (Section 3.5) and/or well proximity effect model (Section 3.6) leads to modification of some of the local parameters calculated from the geometrical or binning scaling rules.

3.2 Geometrical scaling rules

The physical scaling rules to calculate the local parameters from a global parameter set are given in this section.

Note:

- After calculation of the local parameters (and possible application of the stress equations in Section 3.5), clipping is applied according to Section 2.5.2.
- The geometrical scaling equations are *only* calculated when **SWGEO** $= 1$.

Effective length and width

$$W_{\rm f} = \frac{W}{\textbf{NF}} \tag{3.1}$$

$$L_{\rm EN} = 10^{-6} \tag{3.2}$$

$$W_{\rm EN} = 10^{-6} \tag{3.3}$$

$$\Delta L_{\rm PS} = \textbf{LVARO} \cdot \left(1 + \textbf{LVARL} \cdot \frac{L_{\rm EN}}{L}\right) \cdot \left(1 + \textbf{LVARW} \cdot \frac{W_{\rm EN}}{W_{\rm f}}\right) \tag{3.4}$$

$$\Delta W_{\rm OD} = \textbf{WVARO} \cdot \left(1 + \textbf{WVARL} \cdot \frac{L_{\rm EN}}{L}\right) \cdot \left(1 + \textbf{WVARW} \cdot \frac{W_{\rm EN}}{W_{\rm f}}\right) \tag{3.5}$$

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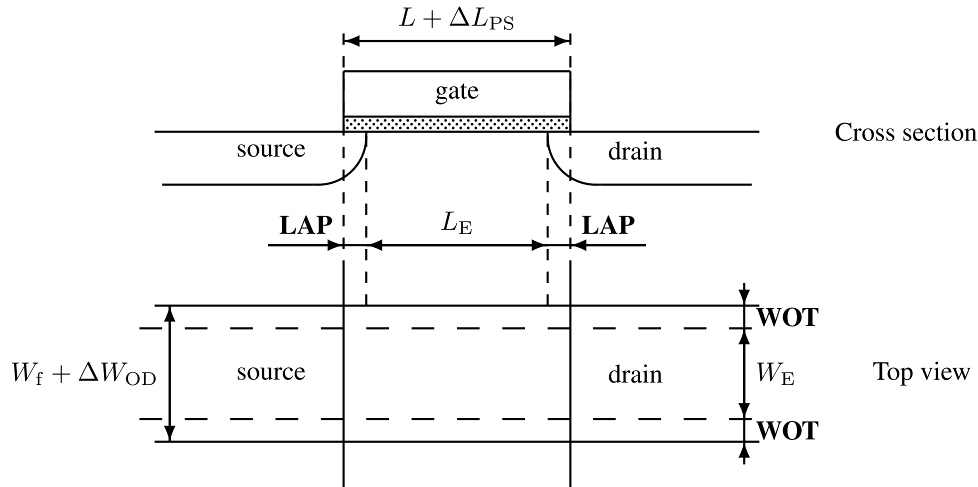

Figure 3.1: Specification of the dimensions of a MOS transistor

$$L_{\rm E} = L - \Delta L = L + \Delta L_{\rm PS} - 2 \cdot \textbf{LAP} \tag{3.6}$$

$$W_{\rm E} = W_{\rm f} - \Delta W = W_{\rm f} + \Delta W_{\rm OD} - 2 \cdot \textbf{WOT} \tag{3.7}$$

$$L_{\rm E,CV} = L + \Delta L_{\rm PS} - 2 \cdot \textbf{LAP} + \textbf{DLQ} \tag{3.8}$$

$$W_{\rm E,CV} = W_{\rm f} + \Delta W_{\rm OD} - 2 \cdot \textbf{WOT} + \textbf{DWQ} \tag{3.9}$$

$$L_{\rm G,CV} = L + \Delta L_{\rm PS} + \textbf{DLQ} \tag{3.10}$$

$$W_{\rm G,CV} = W_{\rm f} + \Delta W_{\rm OD} + \textbf{DWQ} \tag{3.11}$$

Note: If the calculated $L_{\rm E}$, $W_{\rm E}$, $L_{\rm E,CV}$, $W_{\rm E,CV}$, $L_{\rm G,CV}$, or $W_{\rm G,CV}$ is smaller than 1 nm (10^{-9} m), the value is clipped to this lower bound of 1 nm.

Process Parameters

$$\textbf{VFB} = \textbf{VFBO} + \textbf{VFBL} \cdot \frac{L_{\rm EN}}{L_{\rm E}} + \textbf{VFBW} \cdot \frac{W_{\rm EN}}{W_{\rm E}} + \textbf{VFBLW} \cdot \frac{W_{\rm EN} \cdot L_{\rm EN}}{W_{\rm E} \cdot L_{\rm E}} \tag{3.12}$$

$$\textbf{STVFB} = \textbf{STVFBO} + \textbf{STVFBL} \cdot \frac{L_{\rm EN}}{L_{\rm E}} + \textbf{STVFBW} \cdot \frac{W_{\rm EN}}{W_{\rm E}} + \textbf{STVFBLW} \cdot \frac{W_{\rm EN} \cdot L_{\rm EN}}{W_{\rm E} \cdot L_{\rm E}} \tag{3.13}$$

$$\textbf{TOX} = \textbf{TOXO} \tag{3.14}$$

$$\textbf{EPSROX} = \textbf{EPSROXO} \tag{3.15}$$

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$$N_{\text{sub0,eff}} = \textbf{NSUBO} \cdot \text{MAX}\left(\left[1 + \textbf{NSUBW} \cdot \frac{W_{\text{EN}}}{W_{\text{E}}} \cdot \ln\left(1 + \frac{W_{\text{E}}}{\textbf{WSEG}}\right)\right], 10^{-3}\right) \tag{3.16}$$

$$N_{\text{pck,eff}} = \textbf{NPCK} \cdot \text{MAX}\left(\left[1 + \textbf{NPCKW} \cdot \frac{W_{\text{EN}}}{W_{\text{E}}} \cdot \ln\left(1 + \frac{W_{\text{E}}}{\textbf{WSEGP}}\right)\right], 10^{-3}\right) \tag{3.17}$$

$$L_{\text{pck,eff}} = \textbf{LPCK} \cdot \text{MAX}\left(\left[1 + \textbf{LPCKW} \cdot \frac{W_{\text{EN}}}{W_{\text{E}}} \cdot \ln\left(1 + \frac{W_{\text{E}}}{\textbf{WSEGP}}\right)\right], 10^{-3}\right) \tag{3.18}$$

$$a = 7.5 \cdot 10^{10} \tag{3.19}$$

$$b = \sqrt{N_{\text{sub0,eff}} + 0.5 \cdot N_{\text{pck,eff}}} - \sqrt{N_{\text{sub0,eff}}} \tag{3.20}$$

$$N_{\text{sub}} = \begin{cases} N_{\text{sub0,eff}} + N_{\text{pck,eff}} \cdot \left[2 - \dfrac{L_{\text{E}}}{L_{\text{pck,eff}}}\right] & \text{for } L_{\text{E}} < L_{\text{pck,eff}} \\ N_{\text{sub0,eff}} + N_{\text{pck,eff}} \cdot \dfrac{L_{\text{pck,eff}}}{L_{\text{E}}} & \text{for } L_{\text{pck,eff}} \le L_{\text{E}} \le 2 \cdot L_{\text{pck,eff}} \\ \Bigg[\sqrt{N_{\text{sub0,eff}}} + \\ \quad a \cdot \ln\left(1 + 2 \cdot \dfrac{L_{\text{pck,eff}}}{L_{\text{E}}} \cdot \left[\exp\left(\dfrac{b}{a}\right) - 1\right]\right)\Bigg]^2 & \text{for } L_{\text{E}} > 2 \cdot L_{\text{pck,eff}} \end{cases} \tag{3.21}$$

$$\textbf{NEFF} = N_{\text{sub}} \cdot \left(1 - \textbf{FOL1} \cdot \frac{L_{\text{EN}}}{L_{\text{E}}} - \textbf{FOL2} \cdot \left[\frac{L_{\text{EN}}}{L_{\text{E}}}\right]^2\right) \tag{3.22}$$

$$\begin{aligned} \textbf{FACNEFFAC} = {} & \textbf{FACNEFFACO} + \textbf{FACNEFFACL} \cdot \frac{L_{\text{EN}}}{L_{\text{E}}} \\ & + \textbf{FACNEFFACW} \cdot \frac{W_{\text{EN}}}{W_{\text{E}}} + \textbf{FACNEFFACLW} \cdot \frac{L_{\text{EN}} \cdot W_{\text{EN}}}{L_{\text{E}} \cdot W_{\text{E}}} \end{aligned} \tag{3.23}$$

$$\begin{aligned} \textbf{GFACNUD} = {} & \textbf{GFACNUDO} + \textbf{GFACNUDL} \cdot \left[\frac{L_{\text{EN}}}{L_{\text{E}}}\right]^{\textbf{GFACNUDLEXP}} \\ & + \textbf{GFACNUDW} \cdot \frac{W_{\text{EN}}}{W_{\text{E}}} + \textbf{GFACNUDLW} \cdot \frac{L_{\text{EN}} \cdot W_{\text{EN}}}{L_{\text{E}} \cdot W_{\text{E}}} \end{aligned} \tag{3.24}$$

$$\textbf{VSBNUD} = \textbf{VSBNUDO} \tag{3.25}$$

$$\textbf{DVSBNUD} = \textbf{DVSBNUDO} \tag{3.26}$$

$$\textbf{VNSUB} = \textbf{VNSUBO} \tag{3.27}$$

$$\textbf{NSLP} = \textbf{NSLPO} \tag{3.28}$$

$$\mathbf{DNSUB} = \mathbf{DNSUBO} \tag{3.29}$$

$$\mathbf{DPHIB} = \mathbf{DPHIBO} + \mathbf{DPHIBL} \cdot \left[\frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}}\right]^{\mathbf{DPHIBLEXP}} + \mathbf{DPHIBW} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{DPHIBLW} \cdot \frac{W_{\mathrm{EN}} \cdot L_{\mathrm{EN}}}{W_{\mathrm{E}} \cdot L_{\mathrm{E}}} \tag{3.30}$$

$$\mathbf{DELVTAC} = \mathbf{DELVTACO} + \mathbf{DELVTACL} \cdot \left[\frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}}\right]^{\mathbf{DELVTACLEXP}} + \mathbf{DELVTACW} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{DELVTACLW} \cdot \frac{W_{\mathrm{EN}} \cdot L_{\mathrm{EN}}}{W_{\mathrm{E}} \cdot L_{\mathrm{E}}} \tag{3.31}$$

$$\mathbf{NP} = \mathbf{NPO} \cdot \mathrm{MAX}\left(10^{-6}, 1 + \mathbf{NPL} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}}\right) \tag{3.32}$$

$$\mathbf{CT} = \left(\mathbf{CTO} + \mathbf{CTL} \cdot \left[\frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}}\right]^{\mathbf{CTLEXP}}\right) \cdot \left(1 + \mathbf{CTW} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}}\right) \cdot \left(1 + \mathbf{CTLW} \cdot \frac{W_{\mathrm{EN}} \cdot L_{\mathrm{EN}}}{W_{\mathrm{E}} \cdot L_{\mathrm{E}}}\right) \tag{3.33}$$

$$\mathbf{TOXOV} = \mathbf{TOXOVO} \tag{3.34}$$

$$\mathbf{TOXOVD} = \mathbf{TOXOVDO} \tag{3.35}$$

$$\mathbf{NOV} = \mathbf{NOVO} \tag{3.36}$$

$$\mathbf{NOVD} = \mathbf{NOVDO} \tag{3.37}$$

DIBL Parameters

$$\mathbf{CF} = \mathbf{CFL} \cdot \left[\frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}}\right]^{\mathbf{CFLEXP}} \cdot \left(1 + \mathbf{CFW} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}}\right) \tag{3.38}$$

$$\mathbf{CFB} = \mathbf{CFBO} \tag{3.39}$$

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Mobility Parameters

$$F_{\beta 1,\text{eff}} = \mathbf{FBET1} \cdot \left(1 + \mathbf{FBET1W} \cdot \frac{W_\text{EN}}{W_\text{E}}\right) \tag{3.40}$$

$$L_{\text{P1,eff}} = \mathbf{LP1} \cdot \text{MAX}\left(\left[1 + \mathbf{LP1W} \cdot \frac{W_\text{EN}}{W_\text{E}}\right], 10^{-3}\right) \tag{3.41}$$

$$\begin{aligned} G_{\text{P,E}} = 1 + F_{\beta 1,\text{eff}} \cdot \frac{L_{\text{P1,eff}}}{L_\text{E}} \cdot \left[1 - \exp\left(-\frac{L_\text{E}}{L_{\text{P1,eff}}}\right)\right] \\ + \mathbf{FBET2} \cdot \frac{\mathbf{LP2}}{L_\text{E}} \cdot \left[1 - \exp\left(-\frac{L_\text{E}}{\mathbf{LP2}}\right)\right] \end{aligned} \tag{3.42}$$

$$G_{\text{W,E}} = 1 + \mathbf{BETW1} \cdot \frac{W_\text{EN}}{W_\text{E}} + \mathbf{BETW2} \cdot \frac{W_\text{EN}}{W_\text{E}} \cdot \ln\left(1 + \frac{W_\text{E}}{\mathbf{WBET}}\right) \tag{3.43}$$

$$\mathbf{BETN} = \frac{\mathbf{UO}}{G_{\text{P,E}}} \cdot \frac{W_\text{E}}{L_\text{E}} \cdot G_{\text{W,E}} \tag{3.44}$$

$$\mathbf{STBET} = \mathbf{STBETO} + \mathbf{STBETL} \cdot \frac{L_\text{EN}}{L_\text{E}} + \mathbf{STBETW} \cdot \frac{W_\text{EN}}{W_\text{E}} + \mathbf{STBETLW} \cdot \frac{W_\text{EN} \cdot L_\text{EN}}{W_\text{E} \cdot L_\text{E}} \tag{3.45}$$

$$\mathbf{MUE} = \mathbf{MUEO} \cdot \left[1 + \mathbf{MUEW} \cdot \frac{W_\text{EN}}{W_\text{E}}\right] \tag{3.46}$$

$$\mathbf{STMUE} = \mathbf{STMUEO} \tag{3.47}$$

$$\mathbf{THEMU} = \mathbf{THEMUO} \tag{3.48}$$

$$\mathbf{STTHEMU} = \mathbf{STTHEMUO} \tag{3.49}$$

$$\begin{aligned} \mathbf{CS} = \left(\mathbf{CSO} + \mathbf{CSL} \cdot \left[\frac{L_\text{EN}}{L_\text{E}}\right]^{\mathbf{CSLEXP}}\right) \cdot \left(1 + \mathbf{CSW} \cdot \frac{W_\text{EN}}{W_\text{E}}\right) \\ \cdot \left(1 + \mathbf{CSLW} \cdot \frac{W_\text{EN} \cdot L_\text{EN}}{W_\text{E} \cdot L_\text{E}}\right) \end{aligned} \tag{3.50}$$

$$\mathbf{STCS} = \mathbf{STCSO} \tag{3.51}$$

$$\begin{aligned} \mathbf{XCOR} = \mathbf{XCORO} \cdot \left(1 + \mathbf{XCORL} \cdot \frac{L_\text{EN}}{L_\text{E}}\right) \cdot \left(1 + \mathbf{XCORW} \cdot \frac{W_\text{EN}}{W_\text{E}}\right) \\ \cdot \left(1 + \mathbf{XCORLW} \cdot \frac{W_\text{EN} \cdot L_\text{EN}}{W_\text{E} \cdot L_\text{E}}\right) \end{aligned} \tag{3.52}$$

$$\mathbf{STXCOR} = \mathbf{STXCORO} \tag{3.53}$$

$$\mathbf{FETA} = \mathbf{FETAO} \tag{3.54}$$

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Series Resistance Parameters

$$\mathbf{RS} = \mathbf{RSW1} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} \cdot \left[1 + \mathbf{RSW2} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}}\right] \tag{3.55}$$

$$\mathbf{STRS} = \mathbf{STRSO} \tag{3.56}$$

$$\mathbf{RSB} = \mathbf{RSBO} \tag{3.57}$$

$$\mathbf{RSG} = \mathbf{RSGO} \tag{3.58}$$

Velocity Saturation Parameters

$$\mathbf{THESAT} = \left(\mathbf{THESATO} + \mathbf{THESATL} \cdot \frac{G_{\mathrm{W,E}}}{G_{\mathrm{P,E}}} \cdot \left[\frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}}\right]^{\mathbf{THESATLEXP}}\right) \cdot \left(1 + \mathbf{THESATW} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}}\right) \cdot \left(1 + \mathbf{THESATLW} \cdot \frac{W_{\mathrm{EN}} \cdot L_{\mathrm{EN}}}{W_{\mathrm{E}} \cdot L_{\mathrm{E}}}\right) \tag{3.59}$$

$$\mathbf{STTHESAT} = \mathbf{STTHESATO} + \mathbf{STTHESATL} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{STTHESATW} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{STTHESATLW} \cdot \frac{W_{\mathrm{EN}} \cdot L_{\mathrm{EN}}}{W_{\mathrm{E}} \cdot L_{\mathrm{E}}} \tag{3.60}$$

$$\mathbf{THESATB} = \mathbf{THESATBO} \tag{3.61}$$

$$\mathbf{THESATG} = \mathbf{THESATGO} \tag{3.62}$$

Saturation Voltage Parameter

$$\mathbf{AX} = \frac{\mathbf{AXO}}{1 + \mathbf{AXL} \cdot \dfrac{L_{\mathrm{EN}}}{L_{\mathrm{E}}}} \tag{3.63}$$

Channel Length Modulation (CLM) Parameters

$$\mathbf{ALP} = \mathbf{ALPL} \cdot \left[\frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}}\right]^{\mathbf{ALPLEXP}} \cdot \left(1 + \mathbf{ALPW} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}}\right) \tag{3.64}$$

$$\mathbf{ALP1} = \frac{\mathbf{ALP1L1} \cdot \left[\dfrac{L_{\mathrm{EN}}}{L_{\mathrm{E}}}\right]^{\mathbf{ALP1LEXP}}}{1 + \mathbf{ALP1L2} \cdot \left[\dfrac{L_{\mathrm{EN}}}{L_{\mathrm{E}}}\right]^{\mathbf{ALP1LEXP}+1}} \cdot \left(1 + \mathbf{ALP1W} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}}\right) \tag{3.65}$$

$$\mathbf{ALP2} = \frac{\mathbf{ALP2L1} \cdot \left[\dfrac{L_{\mathrm{EN}}}{L_{\mathrm{E}}}\right]^{\mathbf{ALP2LEXP}}}{1 + \mathbf{ALP2L2} \cdot \left[\dfrac{L_{\mathrm{EN}}}{L_{\mathrm{E}}}\right]^{\mathbf{ALP2LEXP}+1}} \cdot \left(1 + \mathbf{ALP2W} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}}\right) \tag{3.66}$$

$$\mathbf{VP} = \mathbf{VPO} \tag{3.67}$$

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Impact Ionization (II) Parameters

$$\mathbf{A1} = \mathbf{A1O} \cdot \left(1 + \mathbf{A1L} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}}\right) \cdot \left(1 + \mathbf{A1W} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}}\right) \tag{3.68}$$

$$\mathbf{A2} = \mathbf{A2O} \tag{3.69}$$

$$\mathbf{STA2} = \mathbf{STA2O} \tag{3.70}$$

$$\mathbf{A3} = \mathbf{A3O} \cdot \left(1 + \mathbf{A3L} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}}\right) \cdot \left(1 + \mathbf{A3W} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}}\right) \tag{3.71}$$

$$\mathbf{A4} = \mathbf{A4O} \cdot \left(1 + \mathbf{A4L} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}}\right) \cdot \left(1 + \mathbf{A4W} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}}\right) \tag{3.72}$$

Gate Current Parameters

$$\mathbf{GCO} = \mathbf{GCOO} \tag{3.73}$$

$$\mathbf{IGINV} = \mathbf{IGINVLW} \cdot \frac{W_{\mathrm{E}} \cdot L_{\mathrm{E}}}{W_{\mathrm{EN}} \cdot L_{\mathrm{EN}}} \tag{3.74}$$

$$\mathbf{IGOV} = \mathbf{IGOVW} \cdot \frac{W_{\mathrm{E}} \cdot \mathbf{LOV}}{W_{\mathrm{EN}} \cdot L_{\mathrm{EN}}} \tag{3.75}$$

$$\mathbf{IGOVD} = \mathbf{IGOVDW} \cdot \frac{W_{\mathrm{E}} \cdot \mathbf{LOVD}}{W_{\mathrm{EN}} \cdot L_{\mathrm{EN}}} \tag{3.76}$$

$$\mathbf{STIG} = \mathbf{STIGO} \tag{3.77}$$

$$\mathbf{GC2} = \mathbf{GC2O} \tag{3.78}$$

$$\mathbf{GC3} = \mathbf{GC3O} \tag{3.79}$$

$$\mathbf{CHIB} = \mathbf{CHIBO} \tag{3.80}$$

Gate-Induced Drain Leakage (GIDL) Parameters

$$\mathbf{AGIDL} = \mathbf{AGIDLW} \cdot \frac{W_{\mathrm{E}} \cdot \mathbf{LOV}}{W_{\mathrm{EN}} \cdot L_{\mathrm{EN}}} \tag{3.81}$$

$$\mathbf{AGIDLD} = \mathbf{AGIDLDW} \cdot \frac{W_{\mathrm{E}} \cdot \mathbf{LOVD}}{W_{\mathrm{EN}} \cdot L_{\mathrm{EN}}} \tag{3.82}$$

$$\mathbf{BGIDL} = \mathbf{BGIDLO} \tag{3.83}$$

$$\mathbf{BGIDLD} = \mathbf{BGIDLDO} \tag{3.84}$$

$$\mathbf{STBGIDL} = \mathbf{STBGIDLO} \tag{3.85}$$

$$\mathbf{STBGIDLD} = \mathbf{STBGIDLDO} \tag{3.86}$$

$$\mathbf{CGIDL} = \mathbf{CGIDLO} \tag{3.87}$$

$$\mathbf{CGIDLD} = \mathbf{CGIDLDO} \tag{3.88}$$

Charge Model Parameters

$$\epsilon_{\mathrm{ox}} = \epsilon_0 \cdot \mathbf{EPSROX} \tag{3.89}$$

$$\mathbf{COX} = \epsilon_{\mathrm{ox}} \cdot \frac{W_{\mathrm{E,CV}} \cdot L_{\mathrm{E,CV}}}{\mathbf{TOX}} \tag{3.90}$$

$$\mathbf{CGOV} = \epsilon_{\mathrm{ox}} \cdot \frac{W_{\mathrm{E,CV}} \cdot \mathbf{LOV}}{\mathbf{TOXOV}} \tag{3.91}$$

$$\mathbf{CGOVD} = \epsilon_{\mathrm{ox}} \cdot \frac{W_{\mathrm{E,CV}} \cdot \mathbf{LOVD}}{\mathbf{TOXOVD}} \tag{3.92}$$

$$\mathbf{CGBOV} = \mathbf{CGBOVL} \cdot \frac{L_{\mathrm{G,CV}}}{L_{\mathrm{EN}}} \tag{3.93}$$

$$\mathbf{CFR} = \mathbf{CFRW} \cdot \frac{W_{\mathrm{G,CV}}}{W_{\mathrm{EN}}} \tag{3.94}$$

$$\mathbf{CFRD} = \mathbf{CFRDW} \cdot \frac{W_{\mathrm{G,CV}}}{W_{\mathrm{EN}}} \tag{3.95}$$

Noise Model Parameters

$$L_{\mathrm{noi}} = \mathrm{MAX}\left(1 - \frac{2 \cdot \mathbf{LINTNOI}}{L_{\mathrm{E}}}, 10^{-3}\right) \tag{3.96}$$

$$L_{\mathrm{red}} = \frac{1}{L_{\mathrm{noi}}^{\mathbf{ALPNOI}}} \tag{3.97}$$

$$\mathbf{NFA} = L_{\mathrm{red}} \cdot \mathbf{NFALW} \cdot \frac{W_{\mathrm{EN}} \cdot L_{\mathrm{EN}}}{W_{\mathrm{E}} \cdot L_{\mathrm{E}}} \tag{3.98}$$

$$\mathbf{NFB} = L_{\mathrm{red}} \cdot \mathbf{NFBLW} \cdot \frac{W_{\mathrm{EN}} \cdot L_{\mathrm{EN}}}{W_{\mathrm{E}} \cdot L_{\mathrm{E}}} \tag{3.99}$$

$$\mathbf{NFC} = L_{\mathrm{red}} \cdot \mathbf{NFCLW} \cdot \frac{W_{\mathrm{EN}} \cdot L_{\mathrm{EN}}}{W_{\mathrm{E}} \cdot L_{\mathrm{E}}} \tag{3.100}$$

$$\mathbf{EF} = \mathbf{EFO} \tag{3.101}$$

WPE parameters

$$K_{\mathrm{vthowe}} = \mathbf{KVTHOWEO} + \mathbf{KVTHOWEL} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{KVTHOWEW} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{KVTHOWELW} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.102}$$

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$$K_{\mathrm{uowe}} = \mathbf{KUOWEO} + \mathbf{KUOWEL} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{KUOWEW} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{KUOWELW} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.103}$$

Self heating parameters

$$\mathbf{RTH} = \mathbf{RTHO} + \frac{\mathbf{RTHW1}}{\mathbf{RTHW2} + \frac{W_{\mathrm{E}}}{W_{\mathrm{EN}}} \cdot \left[1 + \mathbf{RTHLW} \cdot \frac{L_{\mathrm{E}}}{L_{\mathrm{EN}}}\right]} \tag{3.104}$$

$$\mathbf{CTH} = \mathbf{CTHO} + \mathbf{CTHW1} \cdot \left\{\mathbf{CTHW2} + \frac{W_{\mathrm{E}}}{W_{\mathrm{EN}}} \cdot \left[1 + \mathbf{CTHLW} \cdot \frac{L_{\mathrm{E}}}{L_{\mathrm{EN}}}\right]\right\} \tag{3.105}$$

$$\mathbf{STRTH} = \mathbf{STRTHO} \tag{3.106}$$

NQS parameters

$$\mathbf{MUNQS} = \mathbf{MUNQSO} \tag{3.107}$$

3.3 Binning equations

The binning equations are provided as a (phenomenological) alternative to the physical scaling equations for computing local parameters. The physical geometrical scaling rules have been developed to give a good description over the whole geometry range of CMOS technologies. For processes under development, however, it is sometimes useful to have more flexible scaling relations. In that case on could opt for a binning strategy, where the accuracy with geometry is mostly determined by the number of bins used. The physical scaling rules of Section 3.2 are generally not suitable for binning strategies, since they may result in discontinuities in local parameter values at the bin boundaries. Consequently, special binning geometrical scaling relations have been developed, which guarantee continuity of the resulting local model parameters at the bin boundaries.

Note: The binning equations are *only* calculated when **SWGEO** $= 2$.

Only four different types of binning scaling rules are used, which are based on first order developments of the geometrical scaling rules in terms of $L_{\rm E}$, $1/L_{\rm E}$, $W_{\rm E}$, and $1/W_{\rm E}$ (examples below are for a fictitious parameter **YYY**):

1. Type I

$$\mathbf{YYY} = \mathbf{POYYY} + \mathbf{PLYYY} \cdot \frac{L_{\rm EN}}{L_{\rm E}} + \mathbf{PWYYY} \cdot \frac{W_{\rm EN}}{W_{\rm E}} + \mathbf{PLWYYY} \cdot \frac{L_{\rm EN} \cdot W_{\rm EN}}{L_{\rm E} \cdot W_{\rm E}} \tag{3.108}$$

2. Type II

$$\mathbf{YYY} = \mathbf{POYYY} + \mathbf{PLYYY} \cdot \frac{L_{\rm E}}{L_{\rm EN}} + \mathbf{PWYYY} \cdot \frac{W_{\rm E}}{W_{\rm EN}} + \mathbf{PLWYYY} \cdot \frac{L_{\rm E} \cdot W_{\rm E}}{L_{\rm EN} \cdot W_{\rm EN}} \tag{3.109}$$

3. Type III

$$\mathbf{YYY} = \mathbf{POYYY} + \mathbf{PLYYY} \cdot \frac{L_{\rm EN}}{L_{\rm E}} + \mathbf{PWYYY} \cdot \frac{W_{\rm E}}{W_{\rm EN}} + \mathbf{PLWYYY} \cdot \frac{W_{\rm E} \cdot L_{\rm EN}}{W_{\rm EN} \cdot L_{\rm E}} \tag{3.110}$$

4. Type IV (no binning)

$$\mathbf{YYY} = \mathbf{POYYY} \tag{3.111}$$

In Table 3.1 a survey of the binning type used for each local parameter is given. In some cases where the geometrical scaling rule is constant, the binning rule is chosen to be more flexible.

When using the binning rules above, the binning parameters for one bin can be directly calculated from the local parameter sets of the four corner devices of the bin (see Sec. 7.6). This results in a *separate parameter set for each bin*. The binning scheme ensures that the local parameters are exactly reproduced at the bin corners and that no humps occur in the local parameter values across bin boundaries.

Note: After calculation of the local parameters from the binning rules (and possible applications of the stress equations in Section 3.5 and well proximity equations in Section 3.6), clipping is applied according to Section 2.5.2.

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Table 3.1: Overview of local parameters and binning type. The third column indicates whether there is a physical geometrical scaling rule for the local parameters.

#	parameter	physical scaling	binning	#	parameter	physical scaling	binning
0	**VFB**	yes	type I	40	**THESATG**	no	type I
1	**STVFB**	yes	type I	41	**AX**	yes	type I
2	**TOX**	no	no	42	**ALP**	yes	type I
3	**EPSROX**	no	no	43	**ALP1**	yes	type I
4	**NEFF**	yes	type I	44	**ALP2**	yes	type I
5	**FACNEFFAC**	yes	type I	45	**VP**	no	no
6	**GFACNUD**	yes	type I	46	**A1**	yes	type I
7	**VSBNUD**	no	no	47	**A2**	no	no
8	**DVSBNUD**	no	no	48	**STA2**	no	no
9	**VNSUB**	no	no	49	**A3**	yes	type I
10	**NSLP**	no	no	50	**A4**	yes	type I
11	**DNSUB**	no	no	51	**GCO**	no	no
12	**DPHIB**	yes	type I	52	**IGINV**	yes	type II
13	**DELVTAC**	yes	type I	53	**IGOV**	yes	type III
14	**NP**	yes	type I	54	**IGOVD**	yes	type III
15	**CT**	yes	type I	55	**STIG**	no	no
16	**TOXOV**	no	no	56	**GC2**	no	no
17	**TOXOVD**	no	no	57	**GC3**	no	no
18	**NOV**	no	type I	58	**CHIB**	no	no
19	**NOVD**	no	Type I	59	**AGIDL**	yes	type III
20	**CF**	yes	type I	60	**AGIDLD**	yes	type III
21	**CFB**	no	no	61	**BGIDL**	no	no
22	**BETN**	yes	type III	62	**BGIDLD**	no	no
23	**STBET**	yes	type I	63	**STBGIDL**	no	no
24	**MUE**	yes	type I	64	**STBGIDLD**	no	no
25	**STMUE**	no	no	65	**CGIDL**	no	no
26	**THEMU**	no	no	66	**CGIDLD**	no	no
27	**STTHEMU**	no	no	67	**COX**	yes	type II
28	**CS**	yes	type I	68	**CGOV**	yes	type III
29	**STCS**	no	no	69	**CGOVD**	yes	type III
30	**XCOR**	yes	type I	70	**CGBOV**	yes	type II
31	**STXCOR**	no	no	71	**CFR**	yes	type III
32	**FETA**	no	no	72	**CFRD**	yes	type III
33	**RS**	yes	type I	73	**FNT**	no	no
34	**STRS**	no	no	74	**NFA**	yes	type I
35	**RSB**	no	no	75	**NFB**	yes	type I
36	**RSG**	no	no	76	**NFC**	yes	type I
37	**THESAT**	yes	type I	77	**EF**	no	no
38	**STTHESAT**	yes	type I	78	**DTA**	no	no
39	**THESATB**	no	type I				

Effective length and width

$$L_{\mathrm{EN}} = 10^{-6} \tag{3.112}$$

$$W_{\mathrm{EN}} = 10^{-6} \tag{3.113}$$

$$\Delta L_{\mathrm{PS}} = \mathbf{LVARO} \cdot \left(1 + \mathbf{LVARL} \cdot \frac{L_{\mathrm{EN}}}{L}\right) \tag{3.114}$$

$$\Delta W_{\mathrm{OD}} = \mathbf{WVARO} \cdot \left(1 + \mathbf{WVARW} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{f}}}\right) \tag{3.115}$$

$$L_{\mathrm{E}} = L - \Delta L = L + \Delta L_{\mathrm{PS}} - 2 \cdot \mathbf{LAP} \tag{3.116}$$

$$W_{\mathrm{E}} = W_{\mathrm{f}} - \Delta W = W_{\mathrm{f}} + \Delta W_{\mathrm{OD}} - 2 \cdot \mathbf{WOT} \tag{3.117}$$

$$L_{\mathrm{E,CV}} = L + \Delta L_{\mathrm{PS}} - 2 \cdot \mathbf{LAP} + \mathbf{DLQ} \tag{3.118}$$

$$W_{\mathrm{E,CV}} = W_{\mathrm{f}} + \Delta W_{\mathrm{OD}} - 2 \cdot \mathbf{WOT} + \mathbf{DWQ} \tag{3.119}$$

$$L_{\mathrm{G,CV}} = L + \Delta L_{\mathrm{PS}} + \mathbf{DLQ} \tag{3.120}$$

$$W_{\mathrm{G,CV}} = W_{\mathrm{f}} + \Delta W_{\mathrm{OD}} + \mathbf{DWQ} \tag{3.121}$$

Note: If the calculated L_{E}, W_{E}, $L_{\mathrm{E,CV}}$, $W_{\mathrm{E,CV}}$, $L_{\mathrm{G,CV}}$, or $W_{\mathrm{G,CV}}$ is smaller than 1 nm (10^{-9} m), the value is clipped to this lower bound of 1 nm.

Process Parameters

$$\mathbf{VFB} = \mathbf{POVFB} + \mathbf{PLVFB} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWVFB} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWVFB} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.122}$$

$$\mathbf{STVFB} = \mathbf{POSTVFB} + \mathbf{PLSTVFB} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWSTVFB} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWSTVFB} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.123}$$

$$\mathbf{TOX} = \mathbf{POTOX} \tag{3.124}$$

$$\mathbf{EPSROX} = \mathbf{POEPSROX} \tag{3.125}$$

$$\mathbf{NEFF} = \mathbf{PONEFF} + \mathbf{PLNEFF} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWNEFF} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWNEFF} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.126}$$

$$\mathbf{FACNEFFAC} = \mathbf{POFACNEFFAC} + \mathbf{PLFACNEFFAC} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWFACNEFFAC} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWFACNEFFAC} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.127}$$

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$$\mathbf{GFACNUD} = \mathbf{POGFACNUD} + \mathbf{PLGFACNUD} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWGFACNUD} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWGFACNUD} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \quad (3.128)$$

$$\mathbf{VSBNUD} = \mathbf{POVSBNUD} \quad (3.129)$$

$$\mathbf{DVSBNUD} = \mathbf{PODVSBNUD} \quad (3.130)$$

$$\mathbf{VNSUB} = \mathbf{POVNSUB} \quad (3.131)$$

$$\mathbf{NSLP} = \mathbf{PONSLP} \quad (3.132)$$

$$\mathbf{DNSUB} = \mathbf{PODNSUB} \quad (3.133)$$

$$\mathbf{DPHIB} = \mathbf{PODPHIB} + \mathbf{PLDPHIB} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWDPHIB} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWDPHIB} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \quad (3.134)$$

$$\mathbf{DELVTAC} = \mathbf{PODELVTAC} + \mathbf{PLDELVTAC} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWDELVTAC} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWDELVTAC} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \quad (3.135)$$

$$\mathbf{NP} = \mathbf{PONP} + \mathbf{PLNP} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWNP} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWNP} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \quad (3.136)$$

$$\mathbf{CT} = \mathbf{POCT} + \mathbf{PLCT} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWCT} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWCT} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \quad (3.137)$$

$$\mathbf{TOXOV} = \mathbf{POTOXOV} \quad (3.138)$$

$$\mathbf{TOXOVD} = \mathbf{POTOXOVD} \quad (3.139)$$

$$\mathbf{NOV} = \mathbf{PONOV} + \mathbf{PLNOV} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWNOV} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWNOV} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \quad (3.140)$$

$$\mathbf{NOVD} = \mathbf{PONOVD} + \mathbf{PLNOVD} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWNOVD} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWNOVD} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \quad (3.141)$$

DIBL Parameters

$$\mathbf{CF} = \mathbf{POCF} + \mathbf{PLCF} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWCF} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWCF} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \quad (3.142)$$

$$\mathbf{CFB} = \mathbf{POCFB} \quad (3.143)$$

Mobility Parameters

$$\mathbf{BETN} = \frac{W_\mathrm{E}}{L_\mathrm{E}} \cdot \left(\mathbf{POBETN} + \mathbf{PLBETN} \cdot \frac{L_\mathrm{EN}}{L_\mathrm{E}} + \mathbf{PWBETN} \cdot \frac{W_\mathrm{EN}}{W_\mathrm{E}} + \mathbf{PLWBETN} \cdot \frac{L_\mathrm{EN} \cdot W_\mathrm{EN}}{L_\mathrm{E} \cdot W_\mathrm{E}} \right) \tag{3.144}$$

(See Section 7.6.1 for an explanation of this binning rule.)

$$\mathbf{STBET} = \mathbf{POSTBET} + \mathbf{PLSTBET} \cdot \frac{L_\mathrm{EN}}{L_\mathrm{E}} + \mathbf{PWSTBET} \cdot \frac{W_\mathrm{EN}}{W_\mathrm{E}} + \mathbf{PLWSTBET} \cdot \frac{L_\mathrm{EN} \cdot W_\mathrm{EN}}{L_\mathrm{E} \cdot W_\mathrm{E}} \tag{3.145}$$

$$\mathbf{MUE} = \mathbf{POMUE} + \mathbf{PLMUE} \cdot \frac{L_\mathrm{EN}}{L_\mathrm{E}} + \mathbf{PWMUE} \cdot \frac{W_\mathrm{EN}}{W_\mathrm{E}} + \mathbf{PLWMUE} \cdot \frac{L_\mathrm{EN} \cdot W_\mathrm{EN}}{L_\mathrm{E} \cdot W_\mathrm{E}} \tag{3.146}$$

$$\mathbf{STMUE} = \mathbf{POSTMUE} \tag{3.147}$$

$$\mathbf{THEMU} = \mathbf{POTHEMU} \tag{3.148}$$

$$\mathbf{STTHEMU} = \mathbf{POSTTHEMU} \tag{3.149}$$

$$\mathbf{CS} = \mathbf{POCS} + \mathbf{PLCS} \cdot \frac{L_\mathrm{EN}}{L_\mathrm{E}} + \mathbf{PWCS} \cdot \frac{W_\mathrm{EN}}{W_\mathrm{E}} + \mathbf{PLWCS} \cdot \frac{L_\mathrm{EN} \cdot W_\mathrm{EN}}{L_\mathrm{E} \cdot W_\mathrm{E}} \tag{3.150}$$

$$\mathbf{STCS} = \mathbf{POSTCS} \tag{3.151}$$

$$\mathbf{XCOR} = \mathbf{POXCOR} + \mathbf{PLXCOR} \cdot \frac{L_\mathrm{EN}}{L_\mathrm{E}} + \mathbf{PWXCOR} \cdot \frac{W_\mathrm{EN}}{W_\mathrm{E}} + \mathbf{PLWXCOR} \cdot \frac{L_\mathrm{EN} \cdot W_\mathrm{EN}}{L_\mathrm{E} \cdot W_\mathrm{E}} \tag{3.152}$$

$$\mathbf{STXCOR} = \mathbf{POSTXCOR} \tag{3.153}$$

$$\mathbf{FETA} = \mathbf{POFETA} \tag{3.154}$$

Series Resistance Parameters

$$\mathbf{RS} = \mathbf{PORS} + \mathbf{PLRS} \cdot \frac{L_\mathrm{EN}}{L_\mathrm{E}} + \mathbf{PWRS} \cdot \frac{W_\mathrm{EN}}{W_\mathrm{E}} + \mathbf{PLWRS} \cdot \frac{L_\mathrm{EN} \cdot W_\mathrm{EN}}{L_\mathrm{E} \cdot W_\mathrm{E}} \tag{3.155}$$

$$\mathbf{STRS} = \mathbf{POSTRS} \tag{3.156}$$

$$\mathbf{RSB} = \mathbf{PORSB} \tag{3.157}$$

$$\mathbf{RSG} = \mathbf{PORSG} \tag{3.158}$$

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Velocity Saturation Parameters

$$\mathbf{THESAT} = \mathbf{POTHESAT} + \mathbf{PLTHESAT} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWTHESAT} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWTHESAT} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.159}$$

$$\mathbf{STTHESAT} = \mathbf{POSTTHESAT} + \mathbf{PLSTTHESAT} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWSTTHESAT} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWSTTHESAT} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.160}$$

$$\mathbf{THESATB} = \mathbf{POTHESATB} + \mathbf{PLTHESATB} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWTHESATB} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWTHESATB} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.161}$$

$$\mathbf{THESATG} = \mathbf{POTHESATG} + \mathbf{PLTHESATG} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWTHESATG} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWTHESATG} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.162}$$

Saturation Voltage Parameters

$$\mathbf{AX} = \mathbf{POAX} + \mathbf{PLAX} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWAX} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWAX} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.163}$$

Channel Length Modulation (CLM) Parameters

$$\mathbf{ALP} = \mathbf{POALP} + \mathbf{PLALP} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWALP} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWALP} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.164}$$

$$\mathbf{ALP1} = \mathbf{POALP1} + \mathbf{PLALP1} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWALP1} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWALP1} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.165}$$

$$\mathbf{ALP2} = \mathbf{POALP2} + \mathbf{PLALP2} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWALP2} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWALP2} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.166}$$

$$\mathbf{VP} = \mathbf{POVP} \tag{3.167}$$

Impact Ionization (II) Parameters

$$\mathbf{A1} = \mathbf{POA1} + \mathbf{PLA1} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWA1} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWA1} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.168}$$

$$\mathbf{A2} = \mathbf{POA2} \tag{3.169}$$

$$\mathbf{STA2} = \mathbf{POSTA2} \tag{3.170}$$

$$\mathbf{A3} = \mathbf{POA3} + \mathbf{PLA3} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWA3} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWA3} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \quad (3.171)$$

$$\mathbf{A4} = \mathbf{POA4} + \mathbf{PLA4} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWA4} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWA4} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \quad (3.172)$$

Gate Current Parameters

$$\mathbf{GCO} = \mathbf{POGCO} \quad (3.173)$$

$$\mathbf{IGINV} = \mathbf{POIGINV} + \mathbf{PLIGINV} \cdot \frac{L_{\mathrm{E}}}{L_{\mathrm{EN}}} + \mathbf{PWIGINV} \cdot \frac{W_{\mathrm{E}}}{W_{\mathrm{EN}}} + \mathbf{PLWIGINV} \cdot \frac{L_{\mathrm{E}} \cdot W_{\mathrm{E}}}{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}} \quad (3.174)$$

$$\mathbf{IGOV} = \mathbf{POIGOV} + \mathbf{PLIGOV} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWIGOV} \cdot \frac{W_{\mathrm{E}}}{W_{\mathrm{EN}}} + \mathbf{PLWIGOV} \cdot \frac{W_{\mathrm{E}} \cdot L_{\mathrm{EN}}}{W_{\mathrm{EN}} \cdot L_{\mathrm{E}}} \quad (3.175)$$

$$\mathbf{IGOVD} = \mathbf{POIGOVD} + \mathbf{PLIGOVD} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWIGOVD} \cdot \frac{W_{\mathrm{E}}}{W_{\mathrm{EN}}} + \mathbf{PLWIGOVD} \cdot \frac{W_{\mathrm{E}} \cdot L_{\mathrm{EN}}}{W_{\mathrm{EN}} \cdot L_{\mathrm{E}}} \quad (3.176)$$

$$\mathbf{STIG} = \mathbf{POSTIG} \quad (3.177)$$

$$\mathbf{GC2} = \mathbf{POGC2} \quad (3.178)$$

$$\mathbf{GC3} = \mathbf{POGC3} \quad (3.179)$$

$$\mathbf{CHIB} = \mathbf{POCHIB} \quad (3.180)$$

Gate-Induced Drain Leakage (GIDL) Parameters

$$\mathbf{AGIDL} = \mathbf{POAGIDL} + \mathbf{PLAGIDL} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWAGIDL} \cdot \frac{W_{\mathrm{E}}}{W_{\mathrm{EN}}} + \mathbf{PLWAGIDL} \cdot \frac{W_{\mathrm{E}} \cdot L_{\mathrm{EN}}}{W_{\mathrm{EN}} \cdot L_{\mathrm{E}}} \quad (3.181)$$

$$\mathbf{AGIDLD} = \mathbf{POAGIDLD} + \mathbf{PLAGIDLD} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWAGIDLD} \cdot \frac{W_{\mathrm{E}}}{W_{\mathrm{EN}}} + \mathbf{PLWAGIDLD} \cdot \frac{W_{\mathrm{E}} \cdot L_{\mathrm{EN}}}{W_{\mathrm{EN}} \cdot L_{\mathrm{E}}} \quad (3.182)$$

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$$\mathbf{BGIDL} = \mathbf{POBGIDL} \tag{3.183}$$

$$\mathbf{BGIDLD} = \mathbf{POBGIDLD} \tag{3.184}$$

$$\mathbf{STBGIDL} = \mathbf{POSTBGIDL} \tag{3.185}$$

$$\mathbf{STBGIDLD} = \mathbf{POSTBGIDLD} \tag{3.186}$$

$$\mathbf{CGIDL} = \mathbf{POCGIDL} \tag{3.187}$$

$$\mathbf{CGIDLD} = \mathbf{POCGIDLD} \tag{3.188}$$

Charge Model Parameters

$$\mathbf{COX} = \mathbf{POCOX} + \mathbf{PLCOX} \cdot \frac{L_{\mathrm{E,CV}}}{L_{\mathrm{EN}}} + \mathbf{PWCOX} \cdot \frac{W_{\mathrm{E,CV}}}{W_{\mathrm{EN}}} + \mathbf{PLWCOX} \cdot \frac{L_{\mathrm{E,CV}} \cdot W_{\mathrm{E,CV}}}{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}} \tag{3.189}$$

$$\mathbf{CGOV} = \mathbf{POCGOV} + \mathbf{PLCGOV} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E,CV}}} + \mathbf{PWCGOV} \cdot \frac{W_{\mathrm{E,CV}}}{W_{\mathrm{EN}}} + \mathbf{PLWCGOV} \cdot \frac{W_{\mathrm{E,CV}} \cdot L_{\mathrm{EN}}}{W_{\mathrm{EN}} \cdot L_{\mathrm{E,CV}}} \tag{3.190}$$

$$\mathbf{CGOVD} = \mathbf{POCGOVD} + \mathbf{PLCGOVD} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E,CV}}} + \mathbf{PWCGOVD} \cdot \frac{W_{\mathrm{E,CV}}}{W_{\mathrm{EN}}} + \mathbf{PLWCGOVD} \cdot \frac{W_{\mathrm{E,CV}} \cdot L_{\mathrm{EN}}}{W_{\mathrm{EN}} \cdot L_{\mathrm{E,CV}}} \tag{3.191}$$

$$\mathbf{CGBOV} = \mathbf{POCGBOV} + \mathbf{PLCGBOV} \cdot \frac{L_{\mathrm{G,CV}}}{L_{\mathrm{EN}}} + \mathbf{PWCGBOV} \cdot \frac{W_{\mathrm{G,CV}}}{W_{\mathrm{EN}}} + \mathbf{PLWCGBOV} \cdot \frac{L_{\mathrm{G,CV}} \cdot W_{\mathrm{G,CV}}}{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}} \tag{3.192}$$

$$\mathbf{CFR} = \mathbf{POCFR} + \mathbf{PLCFR} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{G,CV}}} + \mathbf{PWCFR} \cdot \frac{W_{\mathrm{G,CV}}}{W_{\mathrm{EN}}} + \mathbf{PLWCFR} \cdot \frac{W_{\mathrm{G,CV}} \cdot L_{\mathrm{EN}}}{W_{\mathrm{EN}} \cdot L_{\mathrm{G,CV}}} \tag{3.193}$$

$$\mathbf{CFRD} = \mathbf{POCFRD} + \mathbf{PLCFRD} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{G,CV}}} + \mathbf{PWCFRD} \cdot \frac{W_{\mathrm{G,CV}}}{W_{\mathrm{EN}}} + \mathbf{PLWCFRD} \cdot \frac{W_{\mathrm{G,CV}} \cdot L_{\mathrm{EN}}}{W_{\mathrm{EN}} \cdot L_{\mathrm{G,CV}}} \tag{3.194}$$

Noise Model Parameters

$$\mathbf{FNT} = \mathbf{POFNT} \tag{3.195}$$

$$\mathbf{NFA} = \mathbf{PONFA} + \mathbf{PLNFA} \cdot \frac{L_{\mathrm{EN}}}{L_{\mathrm{E}}} + \mathbf{PWNFA} \cdot \frac{W_{\mathrm{EN}}}{W_{\mathrm{E}}} + \mathbf{PLWNFA} \cdot \frac{L_{\mathrm{EN}} \cdot W_{\mathrm{EN}}}{L_{\mathrm{E}} \cdot W_{\mathrm{E}}} \tag{3.196}$$

$$\textbf{NFB} = \textbf{PONFB} + \textbf{PLNFB} \cdot \frac{L_{\rm EN}}{L_{\rm E}} + \textbf{PWNFB} \cdot \frac{W_{\rm EN}}{W_{\rm E}} + \textbf{PLWNFB} \cdot \frac{L_{\rm EN} \cdot W_{\rm EN}}{L_{\rm E} \cdot W_{\rm E}} \tag{3.197}$$

$$\textbf{NFC} = \textbf{PONFC} + \textbf{PLNFC} \cdot \frac{L_{\rm EN}}{L_{\rm E}} + \textbf{PWNFC} \cdot \frac{W_{\rm EN}}{W_{\rm E}} + \textbf{PLWNFC} \cdot \frac{L_{\rm EN} \cdot W_{\rm EN}}{L_{\rm E} \cdot W_{\rm E}} \tag{3.198}$$

$$\textbf{EF} = \textbf{POEF} \tag{3.199}$$

WPE parameters

$$K_{\rm vthowe} = \textbf{POKVTHOWE} + \textbf{PLKVTHOWE} \cdot \frac{L_{\rm EN}}{L_{\rm E}} + \textbf{PWKVTHOWE} \cdot \frac{W_{\rm EN}}{W_{\rm E}} + \textbf{PLWKVTHOWE} \cdot \frac{L_{\rm EN} \cdot W_{\rm EN}}{L_{\rm E} \cdot W_{\rm E}} \tag{3.200}$$

$$K_{\rm uowe} = \textbf{POKUOWE} + \textbf{PLKUOWE} \cdot \frac{L_{\rm EN}}{L_{\rm E}} + \textbf{PWKUOWE} \cdot \frac{W_{\rm EN}}{W_{\rm E}} + \textbf{PLWKUOWE} \cdot \frac{L_{\rm EN} \cdot W_{\rm EN}}{L_{\rm E} \cdot W_{\rm E}} \tag{3.201}$$

Self heating parameters

(Also for **SWGEO** $= 2$, the geometrical scaling rules are used.)

$$\textbf{RTH} = \textbf{RTHO} + \frac{\textbf{RTHW1}}{\textbf{RTHW2} + \frac{W_{\rm E}}{W_{\rm EN}} \cdot \left[1 + \textbf{RTHLW} \cdot \frac{L_{\rm E}}{L_{\rm EN}}\right]} \tag{3.202}$$

$$\textbf{CTH} = \textbf{CTHO} + \textbf{CTHW1} \cdot \left\{\textbf{CTHW2} + \frac{W_{\rm E}}{W_{\rm EN}} \cdot \left[1 + \textbf{CTHLW} \cdot \frac{L_{\rm E}}{L_{\rm EN}}\right]\right\} \tag{3.203}$$

$$\textbf{STRTH} = \textbf{STRTHO} \tag{3.204}$$

NQS parameters

(Also for **SWGEO** $= 2$, the geometrical scaling rules are used.)

$$\textbf{MUNQS} = \textbf{MUNQSO} \tag{3.205}$$

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3.4 Parasitic resistances

PSP model contains a network of parasitic elements: a gate resistance, two diffusion resistances for source and drain, and four bulk resistances. Note that the junction diodes are no longer directly connected to the bulk terminal of the intrinsic MOS-transistor. The complete circuit is shown in Fig. 3.2. At this moment, only the gate resistance is scaled with geometry (facilitating the implementation of multi-finger devices).

Note: The resistance equations are calculated when **SWGEO** $= 1$ or 2.

$$L_\mathrm{f} = L + \Delta L_\mathrm{PS} \tag{3.206}$$

$$L_\mathrm{sil,f} = L_\mathrm{f} + \mathbf{DLSIL} \tag{3.207}$$

$$W_\mathrm{E,f} = W_\mathrm{f} + \Delta W_\mathrm{OD} \tag{3.208}$$

$$X_\mathrm{GWE} = \mathbf{XGW} - 0.5 \cdot \Delta W_\mathrm{OD} \tag{3.209}$$

$$\mathbf{RG} = \mathbf{RGO} + \frac{1}{\mathbf{NF}} \cdot \left[\frac{\mathbf{RSHG} \cdot \left(\frac{W_\mathrm{E,f}}{3 \cdot \mathbf{NGCON}} + X_\mathrm{GWE} \right)}{\mathbf{NGCON} \cdot L_\mathrm{sil,f}} + \frac{\mathbf{RINT} + \mathbf{RVPOLY}}{W_\mathrm{E,f} \cdot L_\mathrm{f}} \right] \tag{3.210}$$

$$\mathbf{RSE} = \mathbf{NRS} \cdot \mathbf{RSH} \tag{3.211}$$

$$\mathbf{RDE} = \mathbf{NRD} \cdot \mathbf{RSHD} \tag{3.212}$$

$$\mathbf{RBULK} = \mathbf{RBULKO} \tag{3.213}$$

$$\mathbf{RWELL} = \mathbf{RWELLO} \tag{3.214}$$

$$\mathbf{RJUNS} = \mathbf{RJUNSO} \tag{3.215}$$

$$\mathbf{RJUND} = \mathbf{RJUNDO} \tag{3.216}$$

Note: The values of L_f, $L_\mathrm{sil,f}$, $W_\mathrm{E,f}$ and X_GWE are clipped to a minimum value of 1 nm. The calculated local parameters are subject to the boundaries specified in Section 2.5.6.

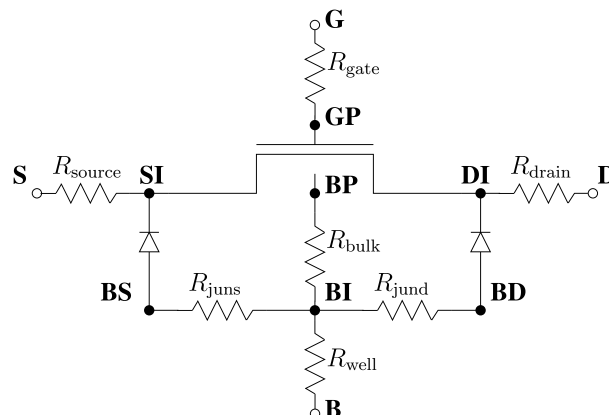

Figure 3.2: Parasitics circuit

3.5 Stress effects

The stress model of BSIM4.4.0 [3] has been adopted in PSP without any modifications, except for two changes: (1) in the original BSIM parameter names all zeros have been replaced by "O"s, in order to comply with PSP conventions and (2) the BSIM parameters *STK2* and *LODK2* are not available in PSP. Some trivial conversion of parameters BSIM→PSP is still necessary, see [2].

The local PSP parameters affected by the stress equations are **BETN**, **THESAT**, **VFB**, and **CF**.

Calculation of **SA** and **SB** for irregular layouts is given in Section B.1.

Note:

- After modification of the local parameters by the stress equations, clipping is applied according to Section 2.5.2.
- If both **SA** and **SB** are set to 0, the stress-equations are *not* computed.
- The stress equations are calculated when **SWGEO** $= 1$ or 2.

3.5.1 Layout effects for multi-finger devices

For multi-finger devices, effective values $\mathbf{SA}_{\mathrm{eff}}$ and $\mathbf{SB}_{\mathrm{eff}}$ for the instance parameters are calculated (see Fig. 3.3).

$$\frac{1}{\mathbf{SA}_{\mathrm{eff}} + 0.5 \cdot L} = \frac{1}{\mathbf{NF}} \cdot \sum_{i=0}^{\mathbf{NF}-1} \frac{1}{\mathbf{SA} + 0.5 \cdot L + i \cdot (\mathbf{SD} + L)} \tag{3.217}$$

$$\frac{1}{\mathbf{SB}_{\mathrm{eff}} + 0.5 \cdot L} = \frac{1}{\mathbf{NF}} \cdot \sum_{i=0}^{\mathbf{NF}-1} \frac{1}{\mathbf{SB} + 0.5 \cdot L + i \cdot (\mathbf{SD} + L)} \tag{3.218}$$

3.5.2 Layout effects for regular shapes

$$R_{\mathrm{A}} = \frac{1}{\mathbf{SA}_{\mathrm{eff}} + 0.5 \cdot L} \tag{3.219}$$

$$R_{\mathrm{B}} = \frac{1}{\mathbf{SB}_{\mathrm{eff}} + 0.5 \cdot L} \tag{3.220}$$

$$R_{\mathrm{A,ref}} = \frac{1}{\mathbf{SAREF} + 0.5 \cdot L} \tag{3.221}$$

$$R_{\mathrm{B,ref}} = \frac{1}{\mathbf{SBREF} + 0.5 \cdot L} \tag{3.222}$$

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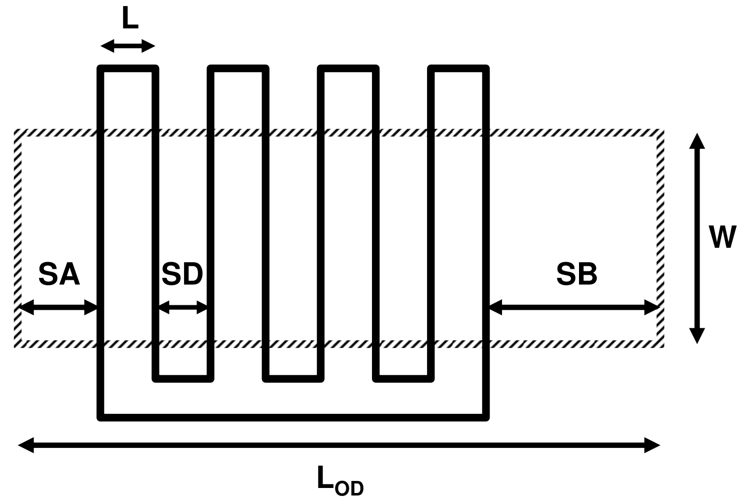

Figure 3.3: A typical layout of multi-finger devices with an additional instance parameters **SD**.

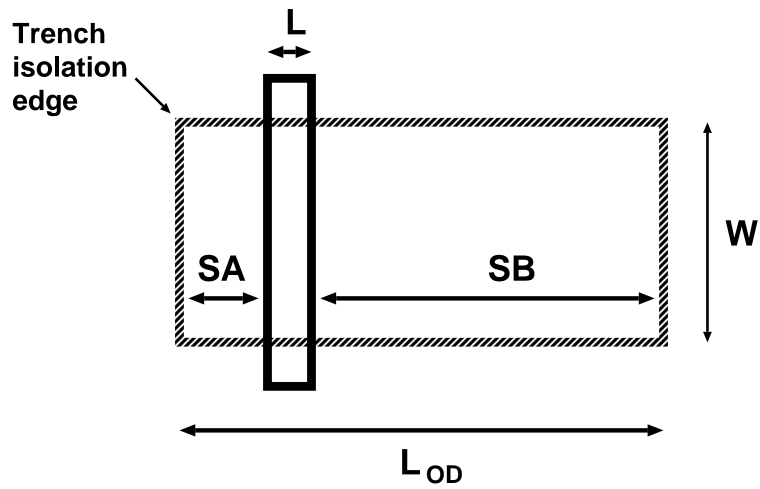

Figure 3.4: Typical layout of a MOSFET. Note that $L_{\mathrm{OD}} = \mathbf{SA} + \mathbf{SB} + L$, where OD is the active region definition.

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3.5.3 Parameter modifications

Mobility-related equations

$$K_{\mathrm{u0}} = \left(1 + \frac{\mathbf{LKUO}}{(L + \Delta L_{\mathrm{PS}})^{\mathbf{LLODKUO}}} + \frac{\mathbf{WKUO}}{(W_{\mathrm{f}} + \Delta W_{\mathrm{OD}} + \mathbf{WLOD})^{\mathbf{WLODKUO}}} + \frac{\mathbf{PKUO}}{(L + \Delta L_{\mathrm{PS}})^{\mathbf{LLODKUO}} \cdot (W_{\mathrm{f}} + \Delta W_{\mathrm{OD}} + \mathbf{WLOD})^{\mathbf{WLODKUO}}}\right) \cdot \left[1 + \mathbf{TKUO} \cdot \left(\frac{T_{\mathrm{KA}}}{T_{\mathrm{KR}}} - 1\right)\right] \quad (3.223)$$

$$\rho_\beta = \frac{\mathbf{KUO}}{K_{\mathrm{u0}}} \cdot (R_{\mathrm{A}} + R_{\mathrm{B}}) \quad (3.224)$$

$$\rho_{\beta,\mathrm{ref}} = \frac{\mathbf{KUO}}{K_{\mathrm{u0}}} \cdot (R_{\mathrm{A,ref}} + R_{\mathrm{B,ref}}) \quad (3.225)$$

$$\mathbf{BETN} = \frac{1 + \rho_\beta}{1 + \rho_{\beta,\mathrm{ref}}} \cdot \mathbf{BETN}_{\mathrm{ref}} \quad (3.226)$$

$$\mathbf{THESAT} = \frac{1 + \rho_\beta}{1 + \rho_{\beta,\mathrm{ref}}} \cdot \frac{1 + \mathbf{KVSAT} \cdot \rho_{\beta,\mathrm{ref}}}{1 + \mathbf{KVSAT} \cdot \rho_\beta} \cdot \mathbf{THESAT}_{\mathrm{ref}} \quad (3.227)$$

Threshold-voltage-related equations

$$K_{\mathrm{vth0}} = 1 + \frac{\mathbf{LKVTHO}}{(L + \Delta L_{\mathrm{PS}})^{\mathbf{LLODVTH}}} + \frac{\mathbf{WKVTHO}}{(W_{\mathrm{f}} + \Delta W_{\mathrm{OD}} + \mathbf{WLOD})^{\mathbf{WLODVTH}}} + \frac{\mathbf{PKVTHO}}{(L + \Delta L_{\mathrm{PS}})^{\mathbf{LLODVTH}} \cdot (W_{\mathrm{f}} + \Delta W_{\mathrm{OD}} + \mathbf{WLOD})^{\mathbf{WLODVTH}}} \quad (3.228)$$

$$\Delta R = R_{\mathrm{A}} + R_{\mathrm{B}} - R_{\mathrm{A,ref}} - R_{\mathrm{B,ref}} \quad (3.229)$$

$$\mathbf{VFB} = \mathbf{VFB}_{\mathrm{ref}} + \mathbf{KVTHO} \cdot \frac{\Delta R}{K_{\mathrm{vth0}}} \quad (3.230)$$

$$\mathbf{CF} = \mathbf{CF}_{\mathrm{ref}} + \mathbf{STETAO} \cdot \frac{\Delta R}{K_{\mathrm{vth0}}^{\mathbf{LODETAO}}} \quad (3.231)$$

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3.6 Well proximity effects

The well proximity effect (WPE) model from BSIM4.5.0 [4, 5, 6] has been adopted in PSP with two changes relative to BSIM4.5.0: (1) in the original BSIM parameter names all zeros have been replaced by 'O's in order to comply with PSP naming convention and (2) the BSIM parameter *K2WE* is not available in PSP. Except for some trivial conversion of parameters BSIM→PSP [2], WPE parameters from BSIM can be used directly in PSP.

The local PSP parameters affected by the WPE equations are **VFB** and **BETN**.

How to calculate **SCA**, **SCB**, and **SCC** is shown in Section B.2.

Note:

- After modification of the local parameters by the WPE equations, clipping is applied according to Section 2.5.2.
- If **SCA**, **SCB**, **SCC** and **SC** are all set to 0, the WPE equations are *not* computed.
- The WPE equations are calculated when **SWGEO** $= 1$ or 2.

3.6.1 Parameters for pre-layout simulation

If **SCA** $=$ **SCB** $=$ **SCC** $= 0$ and **SC** > 0, **SCA**, **SCB**, and **SCC** will be computed from **SC** according to Eqs. (B.9)–(B.11), as shown below. Here, **SC** should be taken as the distance to the nearest well edge (see Fig. 3.5). If any of the parameters **SCA**, **SCB**, or **SCC** is positive, all three values as supplied will be used and **SC** will be ignored.

If **SCA** $=$ **SCB** $=$ **SCC** $= 0$ and **SC** > 0

$$\mathbf{SCA} = \frac{\mathbf{SCREF}^2}{W_\mathrm{f}} \cdot \left(\frac{1}{\mathbf{SC}} - \frac{1}{\mathbf{SC} + W_\mathrm{f}} \right) \tag{3.232}$$

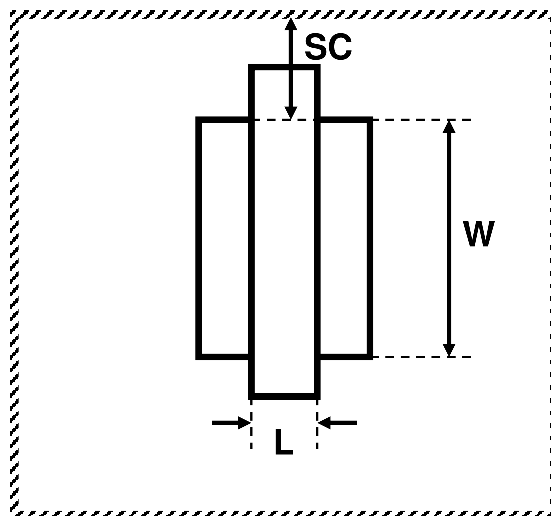

Figure 3.5: A layout of MOS devices for pre-layout simulation using estimated value for **SC**.

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$$\mathbf{SCB} = \frac{1}{W_\mathrm{f} \cdot \mathbf{SCREF}} \cdot \left[\frac{\mathbf{SCREF}}{10} \cdot \mathbf{SC} \cdot \exp\left(-10 \cdot \frac{\mathbf{SC}}{\mathbf{SCREF}}\right) + \frac{\mathbf{SCREF}^2}{100} \cdot \exp\left(-10 \cdot \frac{\mathbf{SC}}{\mathbf{SCREF}}\right) - \frac{\mathbf{SCREF}}{10} \cdot (\mathbf{SC} + W_\mathrm{f}) \cdot \exp\left(-10 \cdot \frac{\mathbf{SC} + W_\mathrm{f}}{\mathbf{SCREF}}\right) - \frac{\mathbf{SCREF}^2}{100} \cdot \exp\left(-10 \cdot \frac{\mathbf{SC} + W_\mathrm{f}}{\mathbf{SCREF}}\right) \right] \tag{3.233}$$

$$\mathbf{SCC} = \frac{1}{W_\mathrm{f} \cdot \mathbf{SCREF}} \cdot \left[\frac{\mathbf{SCREF}}{20} \cdot \mathbf{SC} \cdot \exp\left(-20 \cdot \frac{\mathbf{SC}}{\mathbf{SCREF}}\right) + \frac{\mathbf{SCREF}^2}{400} \cdot \exp\left(-20 \cdot \frac{\mathbf{SC}}{\mathbf{SCREF}}\right) - \frac{\mathbf{SCREF}}{20} \cdot (\mathbf{SC} + W_\mathrm{f}) \cdot \exp\left(-20 \cdot \frac{\mathbf{SC} + W_\mathrm{f}}{\mathbf{SCREF}}\right) - \frac{\mathbf{SCREF}^2}{400} \cdot \exp\left(-20 \cdot \frac{\mathbf{SC} + W_\mathrm{f}}{\mathbf{SCREF}}\right) \right] \tag{3.234}$$

3.6.2 Calculation of parameter modifications

The calculation of K_vthowe and K_uowe is given in Section 3.2 (global model) or 3.3 (binning model).

$$\mathbf{VFB} = \mathbf{VFB}_\mathrm{ref} + K_\mathrm{vthowe} \cdot (\mathbf{SCA} + \mathbf{WEB} \cdot \mathbf{SCB} + \mathbf{WEC} \cdot \mathbf{SCC}) \tag{3.235}$$

$$\mathbf{BETN} = \mathbf{BETN}_\mathrm{ref} \cdot [1 + K_\mathrm{uowe} \cdot (\mathbf{SCA} + \mathbf{WEB} \cdot \mathbf{SCB} + \mathbf{WEC} \cdot \mathbf{SCC})] \tag{3.236}$$

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3.7 Asymmetric junctions

From PSP 102.3 onwards, asymmetric junction can be modeled in PSP. This includes asymmetric source-bulk and drain-bulk junctions, GIDL/GISL, overlap gate currents, overlap capacitances and outer fringe capacitances. The asymmetric junction model can be switched on by means of the parameter **SWJUNASYM**. Note that if **SWJUNASYM** $= 1$, the new parameters for the drain side are used all together. Those whose values are not explicitly specified in the model card are set to their default value, *not* to their counterparts for the source side. In other words, it is not possible to activate the parameters for the drain side on a one-by-one basis. The physical scaling and binning rules to calculate the related local parameters for the drain side are given in Section 3.2 and 3.3.

If **SWJUNASYM** $= 0$, the related parameters for the drain side are ignored. Effectively, the following assignments are applied before evaluation of the calculations described in Section 4.

If **SWJUNASYM** $= 0$:

$$\mathbf{TOXOVD} = \mathbf{TOXOV} \tag{3.237}$$

$$\mathbf{NOVD} = \mathbf{NOV} \tag{3.238}$$

$$\mathbf{AGIDLD} = \mathbf{AGIDL} \tag{3.239}$$

$$\mathbf{BGIDLD} = \mathbf{BGIDL} \tag{3.240}$$

$$\mathbf{STBGIDLD} = \mathbf{STBGIDL} \tag{3.241}$$

$$\mathbf{CGIDLD} = \mathbf{CGIDL} \tag{3.242}$$

$$\mathbf{IGOVD} = \mathbf{IGOV} \tag{3.243}$$

$$\mathbf{CGOVD} = \mathbf{CGOV} \tag{3.244}$$

$$\mathbf{CFRD} = \mathbf{CFR} \tag{3.245}$$

$$\mathbf{RSHD} = \mathbf{RSH} \tag{3.246}$$

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Section 4

PSP Model Equations

4.1 Internal Parameters (including Temperature Scaling)

In this section, bias-independent internal parameters will be calculated, including temperature scaling. These parameters are computed from local parameters. Local parameters are (as usual) denoted by capital characters in bold font, whereas the internal parameters are denoted by symbols in bold font.

Transistor temperature

$$T_{\mathrm{KR}} = T_0 + \mathbf{TR} \tag{4.1}$$

$$T_{\mathrm{KA}} = T_0 + T_{\mathrm{A}} + \mathbf{DTA} \tag{4.2}$$

$$T_{\mathrm{KD}} = T_{\mathrm{KA}} + V_{\mathrm{dt}} \tag{4.3}$$

$$\Delta T = T_{\mathrm{KD}} - T_{\mathrm{KR}} \tag{4.4}$$

$$\Delta T_{\mathrm{A}} = T_{\mathrm{KA}} - T_{\mathrm{KR}} \tag{4.5}$$

$$\boldsymbol{\phi}_{\mathbf{T}} = \frac{k_{\mathrm{B}} \cdot T_{\mathrm{KD}}}{q} \tag{4.6}$$

$$\boldsymbol{\phi}_{\mathbf{T}_{\mathrm{A}}} = \frac{k_{\mathrm{B}} \cdot T_{\mathrm{KA}}}{q} \tag{4.7}$$

Local process parameters

$$\boldsymbol{\phi}^{*}_{\mathbf{T}} = \boldsymbol{\phi}_{\mathbf{T}} \cdot \left(1 + \mathbf{CT} \cdot \frac{T_{\mathrm{KR}}}{T_{\mathrm{KD}}}\right) \tag{4.8}$$

$$\boldsymbol{V}_{\mathbf{FB}} = \mathbf{VFB} + \mathbf{STVFB} \cdot \Delta T + \mathbf{DELVTO} \tag{4.9}$$

$$E_{\mathrm{g}}/q = 1.179 - 9.025 \cdot 10^{-5} \cdot T_{\mathrm{KD}} - 3.05 \cdot 10^{-7} \cdot {T_{\mathrm{KD}}}^2 \tag{4.10}$$

$$r_{\mathrm{T}} = \left(1.045 + 4.5 \cdot 10^{-4} \cdot T_{\mathrm{KD}}\right) \cdot \left(0.523 + 1.4 \cdot 10^{-3} \cdot T_{\mathrm{KD}} - 1.48 \cdot 10^{-6} \cdot {T_{\mathrm{KD}}}^2\right) \tag{4.11}$$

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$$n_{\mathrm{i}} = 2.5 \cdot 10^{25} \cdot {r_{\mathrm{T}}}^{3/4} \cdot (T_{\mathrm{KD}}/300)^{3/2} \cdot \exp\left(-\frac{E_{\mathrm{g}}/q}{2 \cdot \boldsymbol{\phi_{\mathrm{T}}}}\right) \tag{4.12}$$

$$\phi_{\mathrm{B,dc}}^{\mathrm{cl}} = \mathrm{MAX}\left(\mathbf{DPHIB} + 2 \cdot \boldsymbol{\phi_{\mathrm{T}}} \cdot \ln\left[\mathbf{NEFF}/n_{\mathrm{i}}\right],\ 0.05\right) \tag{4.13}$$

$$N_{\mathrm{eff,ac}} = \mathrm{MIN}[\mathrm{MAX}(\mathbf{FACNEFFAC} \cdot \mathbf{NEFF}, 10^{20}), 10^{26}] \tag{4.14}$$

$$\phi_{\mathrm{B,ac}}^{\mathrm{cl}} = \mathrm{MAX}\left(\mathbf{DPHIB} + \mathbf{DELVTAC} + 2 \cdot \boldsymbol{\phi_{\mathrm{T}}} \cdot \ln\left[N_{\mathrm{eff,ac}}/n_{\mathrm{i}}\right],\ 0.05\right) \tag{4.15}$$

$$\epsilon_{\mathrm{ox}} = \mathbf{EPSROX} \cdot \epsilon_0 \tag{4.16}$$

$$C_{\mathrm{ox}} = \epsilon_{\mathrm{ox}}/\mathbf{TOX} \tag{4.17}$$

$$\epsilon_{\mathrm{Si}} = \epsilon_{\mathrm{r,Si}} \cdot \epsilon_0 \tag{4.18}$$

$$\gamma_{0,\mathrm{dc}} = \sqrt{2 \cdot q \cdot \epsilon_{\mathrm{Si}} \cdot \mathbf{NEFF}}/C_{\mathrm{ox}} \tag{4.19}$$

$$\gamma_{0,\mathrm{ac}} = \sqrt{2 \cdot q \cdot \epsilon_{\mathrm{Si}} \cdot N_{\mathrm{eff,ac}}}/C_{\mathrm{ox}} \tag{4.20}$$

$$G_{0,\mathrm{dc}}^{\mathrm{cl}} = \gamma_{0,\mathrm{dc}}/\sqrt{\boldsymbol{\phi_{\mathrm{T}}}} \tag{4.21}$$

$$G_{0,\mathrm{ac}}^{\mathrm{cl}} = \gamma_{0,\mathrm{ac}}/\sqrt{\boldsymbol{\phi_{\mathrm{T}}}} \tag{4.22}$$

Polysilicon depletion parameter

$$\boldsymbol{k_{\mathrm{P}}} = \begin{cases} \text{if } \mathbf{NP} = 0 & \left\{ \boldsymbol{k_{\mathrm{P}}} = 0 \right. \\ \text{if } \mathbf{NP} > 0 & \begin{cases} \mathrm{NP}_1 = \mathrm{MAX}(\mathbf{NP},\ 8 \cdot 10^7/\mathbf{TOX}^2) \\ \mathrm{NP}_2 = \mathrm{MAX}(\mathrm{NP}_1,\ 5 \cdot 10^{24}) \\ \boldsymbol{k_{\mathrm{P}}} = 2 \cdot \boldsymbol{\phi_{\mathrm{T}}} \cdot C_{\mathrm{ox}}^2/(q \cdot \epsilon_{\mathrm{Si}} \cdot \mathrm{NP}_2) \end{cases} \end{cases} \tag{4.23}$$

Quantum-mechanical correction parameters

$$\boldsymbol{q_{\mathrm{lim}}} = 10 \cdot \boldsymbol{\phi_{\mathrm{T}}} \tag{4.24}$$

$$\boldsymbol{q_{\mathrm{q}}} = \begin{cases} 0.4 \cdot \mathbf{QMC} \cdot QM_{\mathrm{N}} \cdot C_{\mathrm{ox}}^{2/3} & \text{for NMOS} \\ 0.4 \cdot \mathbf{QMC} \cdot QM_{\mathrm{P}} \cdot C_{\mathrm{ox}}^{2/3} & \text{for PMOS} \end{cases} \tag{4.25}$$

$$q_{\mathrm{b0,dc}} = \gamma_{0,\mathrm{dc}} \cdot \sqrt{\phi_{\mathrm{B,dc}}^{\mathrm{cl}}} \tag{4.26}$$

$$q_{\mathrm{b0,ac}} = \gamma_{0,\mathrm{ac}} \cdot \sqrt{\phi_{\mathrm{B,ac}}^{\mathrm{cl}}} \tag{4.27}$$

$$\boldsymbol{\phi_{\mathrm{B}}}_{,\mathrm{dc}} = \phi_{\mathrm{B,dc}}^{\mathrm{cl}} + 0.75 \cdot \boldsymbol{q_{\mathrm{q}}} \cdot q_{\mathrm{b0,dc}}^{2/3} \tag{4.28}$$

$$\boldsymbol{\phi_{\mathrm{B}}}_{,\mathrm{ac}} = \phi_{\mathrm{B,ac}}^{\mathrm{cl}} + 0.75 \cdot \boldsymbol{q_{\mathrm{q}}} \cdot q_{\mathrm{b0,ac}}^{2/3} \tag{4.29}$$

$$\boldsymbol{G_{0}}_{,\mathrm{dc}} = G_{0,\mathrm{dc}}^{\mathrm{cl}} \cdot \left(1 + \boldsymbol{q_{\mathrm{q}}} \cdot q_{\mathrm{b0,dc}}^{-1/3}\right) \tag{4.30}$$

$$\boldsymbol{G_{0}}_{,\mathrm{ac}} = G_{0,\mathrm{ac}}^{\mathrm{cl}} \cdot \left(1 + \boldsymbol{q_{\mathrm{q}}} \cdot q_{\mathrm{b0,ac}}^{-1/3}\right) \tag{4.31}$$

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$V_{\rm SB}$-clipping parameters

$$\boldsymbol{\phi}_{\mathbf{X},\mathrm{dc}} = 0.95 \cdot \boldsymbol{\phi}_{\mathbf{B},\mathrm{dc}} \tag{4.32}$$

$$\boldsymbol{\phi}_{\mathbf{X},\mathrm{ac}} = 0.95 \cdot \boldsymbol{\phi}_{\mathbf{B},\mathrm{ac}} \tag{4.33}$$

$$\boldsymbol{a}_{\boldsymbol{\phi},\mathrm{dc}} = 2.5 \cdot 10^{-3} \cdot \boldsymbol{\phi}^2_{\mathbf{B},\mathrm{dc}} \tag{4.34}$$

$$\boldsymbol{a}_{\boldsymbol{\phi},\mathrm{ac}} = 2.5 \cdot 10^{-3} \cdot \boldsymbol{\phi}^2_{\mathbf{B},\mathrm{ac}} \tag{4.35}$$

$$\boldsymbol{b}_{\boldsymbol{\phi},\mathrm{dc}} = 2.5 \cdot 10^{-3} \cdot \boldsymbol{\phi}^2_{\mathbf{B},\mathrm{dc}} \tag{4.36}$$

$$\boldsymbol{b}_{\boldsymbol{\phi},\mathrm{ac}} = 2.5 \cdot 10^{-3} \cdot \boldsymbol{\phi}^2_{\mathbf{B},\mathrm{ac}} \tag{4.37}$$

$$\boldsymbol{\phi}^{\star}_{\mathbf{X},\mathrm{dc}} = 0.5 \cdot \sqrt{\boldsymbol{b}_{\boldsymbol{\phi},\mathrm{dc}}} \tag{4.38}$$

$$\boldsymbol{\phi}^{\star}_{\mathbf{X},\mathrm{ac}} = 0.5 \cdot \sqrt{\boldsymbol{b}_{\boldsymbol{\phi},\mathrm{ac}}} \tag{4.39}$$

$$\boldsymbol{\phi}^{*}_{\mathbf{X},\mathrm{dc}} = \mathrm{MINA}\left(\boldsymbol{\phi}_{\mathbf{X},\mathrm{dc}} - \boldsymbol{\phi}^{\star}_{\mathbf{X},\mathrm{dc}},\, 0,\, \boldsymbol{a}_{\boldsymbol{\phi},\mathrm{dc}}\right) \tag{4.40}$$

$$\boldsymbol{\phi}^{*}_{\mathbf{X},\mathrm{ac}} = \mathrm{MINA}\left(\boldsymbol{\phi}_{\mathbf{X},\mathrm{ac}} - \boldsymbol{\phi}^{\star}_{\mathbf{X},\mathrm{ac}},\, 0,\, \boldsymbol{a}_{\boldsymbol{\phi},\mathrm{ac}}\right) \tag{4.41}$$

NUD parameters

$$\mathbf{u_{s1}} = \sqrt{\mathbf{VSBNUD} + \boldsymbol{\phi}_{\mathbf{B}}} - \sqrt{\boldsymbol{\phi}_{\mathbf{B}}} \tag{4.42}$$

$$\mathbf{u_{s21}} = \sqrt{\mathbf{DVSBNUD} + \boldsymbol{\phi}_{\mathbf{B}}} - \sqrt{\boldsymbol{\phi}_{\mathbf{B}}} - \mathbf{u_{s1}} \tag{4.43}$$

Local process parameters in gate overlap regions

$$\gamma_{\rm ov} = \sqrt{2 \cdot q \cdot \epsilon_{\rm Si} \cdot \mathbf{NOV}} \cdot \mathbf{TOXOV}/\epsilon_{\rm ox} \tag{4.44}$$

$$\gamma_{\rm dov} = \sqrt{2 \cdot q \cdot \epsilon_{\rm Si} \cdot \mathbf{NOVD}} \cdot \mathbf{TOXOVD}/\epsilon_{\rm ox} \tag{4.45}$$

$$\boldsymbol{G}_{\mathbf{ov}} = \gamma_{\rm ov}/\sqrt{\boldsymbol{\phi}_{\mathbf{T}}} \tag{4.46}$$

$$\boldsymbol{G}_{\mathbf{dov}} = \gamma_{\rm dov}/\sqrt{\boldsymbol{\phi}_{\mathbf{T}}} \tag{4.47}$$

$$\boldsymbol{\varepsilon}_{\mathbf{ov}} = 3.1 \cdot \boldsymbol{G}_{\mathbf{ov}} + 8.5 \tag{4.48}$$

$$\boldsymbol{a}_{\mathbf{ov}} = \begin{cases} 64/\boldsymbol{G}_{\mathbf{ov}} & \text{for } 1/\boldsymbol{G}_{\mathbf{ov}} < 0.06 \\ 22/\boldsymbol{G}_{\mathbf{ov}} + 3 & \text{for } 0.06 \le 1/\boldsymbol{G}_{\mathbf{ov}} \le 0.45 \\ -7.2/\boldsymbol{G}_{\mathbf{ov}} + 15.5 & \text{for } 0.45 < 1/\boldsymbol{G}_{\mathbf{ov}} \le 1.6 \\ \boldsymbol{G}_{\mathbf{ov}} & \text{for } 1/\boldsymbol{G}_{\mathbf{ov}} > 1.6 \end{cases} \tag{4.49}$$

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$$\boldsymbol{\delta}_{\mathbf{ov}} = \frac{\varepsilon_{\mathbf{ov}}}{2} + \frac{\boldsymbol{G}_{\mathbf{ov}}^2}{2} - \boldsymbol{G}_{\mathbf{ov}} \cdot \sqrt{\frac{\varepsilon_{\mathbf{ov}}}{2} + \frac{\boldsymbol{G}_{\mathbf{ov}}^2}{4} + \boldsymbol{a}_{\mathbf{ov}}} \tag{4.50}$$

$$\varepsilon_{\mathbf{dov}} = 3.1 \cdot \boldsymbol{G}_{\mathbf{dov}} + 8.5 \tag{4.51}$$

$$\boldsymbol{a}_{\mathbf{dov}} = \begin{cases} 64/\boldsymbol{G}_{\mathbf{dov}} & \text{for } 1/\boldsymbol{G}_{\mathbf{dov}} < 0.06 \\ 22/\boldsymbol{G}_{\mathbf{dov}} + 3 & \text{for } 0.06 \le 1/\boldsymbol{G}_{\mathbf{dov}} \le 0.45 \\ -7.2/\boldsymbol{G}_{\mathbf{dov}} + 15.5 & \text{for } 0.45 < 1/\boldsymbol{G}_{\mathbf{dov}} \le 1.6 \\ \boldsymbol{G}_{\mathbf{dov}} & \text{for } 1/\boldsymbol{G}_{\mathbf{dov}} > 1.6 \end{cases} \tag{4.52}$$

$$\boldsymbol{\delta}_{\mathbf{dov}} = \frac{\varepsilon_{\mathbf{dov}}}{2} + \frac{\boldsymbol{G}_{\mathbf{dov}}^2}{2} - \boldsymbol{G}_{\mathbf{dov}} \cdot \sqrt{\frac{\varepsilon_{\mathbf{dov}}}{2} + \frac{\boldsymbol{G}_{\mathbf{dov}}^2}{4} + \boldsymbol{a}_{\mathbf{dov}}} \tag{4.53}$$

Mobility parameters

$$\boldsymbol{\beta} = \mathbf{FACTUO} \cdot \mathbf{BETN} \cdot C_{\mathrm{ox}} \cdot (T_{\mathrm{KR}}/T_{\mathrm{KD}})^{\mathbf{STBET}} \tag{4.54}$$

$$\boldsymbol{\theta}_{\boldsymbol{\mu}} = \mathbf{THEMU} \cdot (T_{\mathrm{KR}}/T_{\mathrm{KD}})^{\mathbf{STTHEMU}} \tag{4.55}$$

$$\boldsymbol{\mu}_{\mathbf{E}} = \mathbf{MUE} \cdot (T_{\mathrm{KR}}/T_{\mathrm{KD}})^{\mathbf{STMUE}} \tag{4.56}$$

$$\boldsymbol{X}_{\mathbf{cor}} = \mathbf{XCOR} \cdot (T_{\mathrm{KR}}/T_{\mathrm{KD}})^{\mathbf{STXCOR}} \tag{4.57}$$

$$\boldsymbol{C}_{\mathbf{S}} = \mathbf{CS} \cdot (T_{\mathrm{KR}}/T_{\mathrm{KD}})^{\mathbf{STCS}} \tag{4.58}$$

$$\boldsymbol{E}_{\mathbf{eff0}} = 10^{-8} \cdot C_{\mathrm{ox}}/\epsilon_{\mathrm{Si}} \tag{4.59}$$

$$\boldsymbol{\eta}_{\boldsymbol{\mu}} = \begin{cases} 1/2 \cdot \mathbf{FETA} & \text{for NMOS} \\ 1/3 \cdot \mathbf{FETA} & \text{for PMOS} \end{cases} \tag{4.60}$$

$$\boldsymbol{\eta}_{\boldsymbol{\mu},\mathrm{ac}} = \begin{cases} 1/2 & \text{for NMOS} \\ 1/3 & \text{for PMOS} \end{cases} \tag{4.61}$$

Series resistance parameter

$$R_{\mathrm{s}} = \mathbf{RS} \cdot (T_{\mathrm{KR}}/T_{\mathrm{KD}})^{\mathbf{STRS}} \tag{4.62}$$

$$\boldsymbol{\theta}_{\mathbf{R}} = 2 \cdot \boldsymbol{\beta} \cdot R_{\mathrm{s}} \tag{4.63}$$

Velocity saturation parameter

$$\boldsymbol{\theta}_{\mathbf{sat}} = \mathbf{THESAT} \cdot (T_{\mathrm{KR}}/T_{\mathrm{KD}})^{\mathbf{STTHESAT}} \tag{4.64}$$

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Impact-ionization parameter

$$\boldsymbol{a_2} = \mathbf{A2} \cdot (T_{\rm KD}/T_{\rm KR})^{\mathbf{STA2}} \tag{4.65}$$

Gate current parameters

$$\boldsymbol{I_{\rm GINV}} = \mathbf{IGINV} \cdot (T_{\rm KA}/T_{\rm KR})^{\mathbf{STIG}} \tag{4.66}$$

$$\boldsymbol{I_{\rm GOV}} = \mathbf{IGOV} \cdot (T_{\rm KA}/T_{\rm KR})^{\mathbf{STIG}} \tag{4.67}$$

$$\boldsymbol{I_{\rm GOVD}} = \mathbf{IGOVD} \cdot (T_{\rm KA}/T_{\rm KR})^{\mathbf{STIG}} \tag{4.68}$$

$$\boldsymbol{B} = \frac{4}{3} \cdot \frac{\mathbf{TOX}}{\hbar} \cdot \sqrt{2 \cdot q \cdot m_0 \cdot \mathbf{CHIB}} = 6.830909 \cdot 10^9 \cdot \mathbf{TOX} \cdot \sqrt{\mathbf{CHIB}} \tag{4.69}$$

$$\boldsymbol{B_{\rm ov}} = \boldsymbol{B} \cdot \mathbf{TOXOV}/\mathbf{TOX} \tag{4.70}$$

$$\boldsymbol{B_{\rm ovd}} = \boldsymbol{B} \cdot \mathbf{TOXOVD}/\mathbf{TOX} \tag{4.71}$$

$$\boldsymbol{GC_{\rm Q}} = \begin{cases} -0.99 \cdot \dfrac{\mathbf{GC2}}{2 \cdot \mathbf{GC3}} & \text{for } \mathbf{GC3} < 0 \\ 0 & \text{for } \mathbf{GC3} \geq 0 \end{cases} \tag{4.72}$$

$$\boldsymbol{\alpha_{\rm b}} = \frac{E_{\rm g}/q + \boldsymbol{\phi_{\rm B}}}{2} \tag{4.73}$$

$$\boldsymbol{D_{\rm ch}} = \mathbf{GCO} \cdot \boldsymbol{\phi^*_{\rm T}} \tag{4.74}$$

$$\boldsymbol{D_{\rm ov}} = \mathbf{GCO} \cdot \boldsymbol{\phi_{\rm T_A}} \tag{4.75}$$

Gate-induced drain leakage parameters

$$\boldsymbol{A_{\rm GIDL}} = \mathbf{AGIDL} \cdot \left(\frac{2 \cdot 10^{-9}}{\mathbf{TOXOV}}\right)^2 \tag{4.76}$$

$$\boldsymbol{A_{\rm GIDLD}} = \mathbf{AGIDLD} \cdot \left(\frac{2 \cdot 10^{-9}}{\mathbf{TOXOVD}}\right)^2 \tag{4.77}$$

$$\boldsymbol{B_{\rm GIDL}} = \mathbf{BGIDL} \cdot \mathrm{MAX}\left([1 + \mathbf{STBGIDL} \cdot \Delta T_{\rm A}]\,, 0\right) \cdot \left(\frac{\mathbf{TOXOV}}{2 \cdot 10^{-9}}\right) \tag{4.78}$$

$$\boldsymbol{B_{\rm GIDLD}} = \mathbf{BGIDLD} \cdot \mathrm{MAX}\left([1 + \mathbf{STBGIDLD} \cdot \Delta T_{\rm A}]\,, 0\right) \cdot \left(\frac{\mathbf{TOXOVD}}{2 \cdot 10^{-9}}\right) \tag{4.79}$$

Self heating

$$\boldsymbol{R_{\rm TH}} = \mathbf{RTH} \cdot \left(\frac{T_{\rm KA}}{\cdot T_{\rm KR}}\right)^{\mathbf{STRTH}} \tag{4.80}$$

Noise parameter

$$\boldsymbol{N_{\rm T}} = \mathbf{FNT} \cdot 4 \cdot k_{\rm B} \cdot T_{\rm KD} \tag{4.81}$$

Additional internal parameters

$$\boldsymbol{x_1} = 1.25 \tag{4.82}$$

4.2 Current Model

In this section, the current model equations of the PSP-model are given. Use is made of the applied terminal bias values $V_{\rm GS}$, $V_{\rm DS}$ and $V_{\rm SB}$, the local parameters listed in Section 2.5.2 and the internal parameters introduced in Section 4.1. Local parameters are denoted by capital characters in bold font, whereas internal (bias-independent) parameters are denoted by symbols in bold font.

The definitions of the auxiliary functions MINA(.), MAXA(.), $\chi(.)$ and $\sigma_{1,2}(.)$ can be found in Appendix A.

Depending on the value of the parameters **SWNUD** and **SWDELVTAC**, the surface potential (at source- and drain-side of the channel) and associated computations, i.e., Eqs. (4.94)–(4.185), may be evaluated twice: once for the dc-characteristics and a second time for the ac-characteristics of the model. Details are given below.

4.2.1 Conditioning of Terminal Voltages

$$V_{\rm dsx} = \sqrt{{V_{\rm DS}}^2 + 0.01} - 0.1 \tag{4.83}$$

$$\phi_{\rm V,dc} = {\rm MINA}\left(V_{\rm SB},\, V_{\rm SB} + V_{\rm DS},\, \boldsymbol{b}_{\boldsymbol{\phi},\rm dc}\right) + \boldsymbol{\phi}_{\mathbf{X},\rm dc} \tag{4.84}$$

$$\phi_{\rm V,ac} = {\rm MINA}\left(V_{\rm SB},\, V_{\rm SB} + V_{\rm DS},\, \boldsymbol{b}_{\boldsymbol{\phi},\rm ac}\right) + \boldsymbol{\phi}_{\mathbf{X},\rm ac} \tag{4.85}$$

$$V^*_{\rm SB,dc} = V_{\rm SB} - {\rm MINA}\left(\phi_{\rm V},\, 0,\, \boldsymbol{a}_{\boldsymbol{\phi},\rm dc}\right) + \boldsymbol{\phi}^*_{\mathbf{X},\rm dc} \tag{4.86}$$

$$V^*_{\rm SB,ac} = V_{\rm SB} - {\rm MINA}\left(\phi_{\rm V},\, 0,\, \boldsymbol{a}_{\boldsymbol{\phi},\rm ac}\right) + \boldsymbol{\phi}^*_{\mathbf{X},\rm ac} \tag{4.87}$$

Nonuniform doping effect. Eqs. (4.88)–(4.93) are only evaluated when **SWNUD** $\neq 0$ and **GFACNUD** $\neq 1$:

$$V_{\rm mB} = V^*_{\rm SB} + 0.5 \cdot (V_{\rm DS} - V_{\rm dsx}) \tag{4.88}$$

$$u_{\rm s} = \sqrt{V_{\rm mB} + \boldsymbol{\phi}_{\mathbf{B}}} - \sqrt{\boldsymbol{\phi}_{\mathbf{B}}} \tag{4.89}$$

$$p = 2 \cdot \frac{u_{\rm s} - \mathbf{u_{s1}}}{\mathbf{u_{s21}}} - 1 \tag{4.90}$$

$$u_{\rm s,nud} = u_{\rm s} - 0.25 \cdot (1 - \mathbf{GFACNUD}) \cdot \mathbf{u_{s21}} \cdot \left\{p + \sqrt{p^2 + [\ln(2)]^2}\right\} \tag{4.91}$$

$$V_{\rm mB,nud} = \left(u_{\rm s,nud} + 2 \cdot \sqrt{\boldsymbol{\phi}_{\mathbf{B}}}\right) \cdot u_{\rm s,nud} \tag{4.92}$$

$$V^*_{\rm SB,dc} = V_{\rm mB,nud} - 0.5 \cdot (V_{\rm DS} - V_{\rm dsx}) \tag{4.93}$$

The surface potential (at source- and drain-side of the channel) and associated computations, i.e., Eqs. (4.94)–(4.185), are evaluated using $V^*_{\rm SB} = V^*_{\rm SB,dc}$, $\boldsymbol{\phi}_{\mathbf{B}} = \boldsymbol{\phi}_{\mathbf{B},\rm dc}$, and $\boldsymbol{G}_{\mathbf{0}} = \boldsymbol{G}_{\mathbf{0},\rm dc}$.

If **SWNUD** $= 1$ or **SWDELVTAC** $= 1$, Eqs. (4.94)–(4.185) are evaluated a second time using $V^*_{\rm SB} = V^*_{\rm SB,ac}$, $\boldsymbol{\phi}_{\mathbf{B}} = \boldsymbol{\phi}_{\mathbf{B},\rm ac}$, and $\boldsymbol{G}_{\mathbf{0}} = \boldsymbol{G}_{\mathbf{0},\rm ac}$.

$$V^*_{\rm DB} = V_{\rm DS} + V^*_{\rm SB} \tag{4.94}$$

$$V_{\rm sbx} = V^*_{\rm SB} + \frac{V_{\rm DS} - V_{\rm dsx}}{2} \tag{4.95}$$

Drain-induced barrier lowering:

$$\Delta V_{\rm G} = \mathbf{CF} \cdot V_{\rm dsx} \cdot (1 + \mathbf{CFB} \cdot V_{\rm sbx}) \tag{4.96}$$

$$V^*_{\rm GB} = V_{\rm GS} + V^*_{\rm SB} + \Delta V_{\rm G} - \boldsymbol{V}_{\mathbf{FB}} \tag{4.97}$$

$$x_{\rm g} = V^*_{\rm GB}/\boldsymbol{\phi}^*_{\mathbf{T}} \tag{4.98}$$

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4.2.2 Bias-Dependent Body Factor

$$D_{\mathrm{nsub}} = \mathbf{DNSUB} \cdot \mathrm{MAXA}\big(0,\, V_{\mathrm{GS}} + V_{\mathrm{SB}} - \mathbf{VNSUB},\, \mathbf{NSLP}\big) \tag{4.99}$$

$$G = \boldsymbol{G_0} \cdot \sqrt{1 + D_{\mathrm{nsub}}} \tag{4.100}$$

4.2.3 Surface Potential at Source Side and Related Variables

$$\xi = 1 + G/\sqrt{2} \tag{4.101}$$

$$x_{\mathrm{ns}} = \frac{\boldsymbol{\phi_B} + V_{\mathrm{SB}}^*}{\boldsymbol{\phi_T}^*} \tag{4.102}$$

$$\Delta_{\mathrm{ns}} = \exp\left(-x_{\mathrm{ns}}\right) \tag{4.103}$$

$$x_{\mathrm{mrg}} = 10^{-5} \cdot \xi \tag{4.104}$$

$$\text{if } x_{\mathrm{g}} < -x_{\mathrm{mrg}} \begin{cases} y_{\mathrm{g}} = -x_{\mathrm{g}} \\ z = 1.25 \cdot y_{\mathrm{g}}/\xi \\ \eta = \left[z + 10 - \sqrt{(z-6)^2 + 64}\right]/2 \\ a = \left(y_{\mathrm{g}} - \eta\right)^2 + G^2 \cdot (\eta + 1) \\ c = 2 \cdot (y_{\mathrm{g}} - \eta) - G^2 \\ \tau = -\eta + \ln\left(a/G^2\right) \\ y_0 = \sigma_1(a,\, c,\, \tau,\, \eta) \\ \Delta_0 = \exp\left(y_0\right) \\ p = 2 \cdot (y_{\mathrm{g}} - y_0) + G^2 \cdot \left[\Delta_0 - 1 + \Delta_{\mathrm{ns}} \cdot (1 - \chi'(y_0) - 1/\Delta_0)\right] \\ q = \left(y_{\mathrm{g}} - y_0\right)^2 + G^2 \cdot \left[y_0 - \Delta_0 + 1 + \Delta_{\mathrm{ns}} \cdot (1 + \chi(y_0) - 1/\Delta_0 - 2 \cdot y_0)\right] \\ x_{\mathrm{s}} = -y_0 - \dfrac{2 \cdot q}{p + \sqrt{p^2 - 2 \cdot q \cdot \{2 - G^2 \cdot [\Delta_0 + \Delta_{\mathrm{ns}} \cdot (1/\Delta_0 - \chi''(y_0))]\}}} \end{cases} \tag{4.105}$$

$$\text{if } |x_{\mathrm{g}}| \le x_{\mathrm{mrg}} \left\{ \; x_{\mathrm{s}} = \frac{x_{\mathrm{g}}}{\xi} \cdot \left[1 + G \cdot x_{\mathrm{g}} \cdot \frac{1 - \Delta_{\mathrm{ns}}}{\xi^2 \cdot 6 \cdot \sqrt{2}}\right] \right. \tag{4.106}$$

$$\text{if } x_{\mathrm{g}} > x_{\mathrm{mrg}} \quad \begin{cases} \hat{x}_{\mathrm{g1}} = \boldsymbol{x_1} + G \cdot \sqrt{\exp(-\boldsymbol{x_1}) + \boldsymbol{x_1} - 1} \\ \bar{x} = \dfrac{x_{\mathrm{g}}}{\xi} \cdot \left[1 + x_{\mathrm{g}} \cdot (\xi \cdot \boldsymbol{x_1} - \hat{x}_{\mathrm{g1}})/\hat{x}_{\mathrm{g1}}^2\right] \\ x_0 = x_{\mathrm{g}} + G^2/2 - G \cdot \sqrt{x_{\mathrm{g}} + G^2/4 - 1 + \exp(-\bar{x})} \\ b_{\mathrm{x}} = x_{\mathrm{ns}} + 3 \\ \eta = \mathrm{MINA}(x_0,\, b_{\mathrm{x}},\, 5) - \left(b_{\mathrm{x}} - \sqrt{b_{\mathrm{x}}^2 + 5}\right)/2 \\ a = (x_{\mathrm{g}} - \eta)^2 - G^2 \cdot [\exp(-\eta) + \eta - 1 - \Delta_{\mathrm{ns}} \cdot (\eta + 1 + \chi(\eta))] \\ b = 1 - G^2/2 \cdot [\exp(-\eta) - \Delta_{\mathrm{ns}} \cdot \chi''(\eta)] \\ c = 2 \cdot (x_{\mathrm{g}} - \eta) + G^2 \cdot [1 - \exp(-\eta) - \Delta_{\mathrm{ns}} \cdot (1 + \chi'(\eta))] \\ \tau = x_{\mathrm{ns}} - \eta + \ln\left(a/G^2\right) \\ y_0 = \sigma_2(a,\, b,\, c,\, \tau,\, \eta) \\ \Delta_0 = \exp(y_0) \\ p = 2 \cdot (x_{\mathrm{g}} - y_0) + G^2 \cdot [1 - 1/\Delta_0 + \Delta_{\mathrm{ns}} \cdot (\Delta_0 - 1 - \chi'(y_0))] \\ q = (x_{\mathrm{g}} - y_0)^2 - G^2 \cdot [y_0 + 1/\Delta_0 - 1 + \Delta_{\mathrm{ns}} \cdot (\Delta_0 - y_0 - 1 - \chi(y_0))] \\ x_{\mathrm{s}} = y_0 + \dfrac{2 \cdot q}{p + \sqrt{p^2 - 2 \cdot q \cdot \{2 - G^2 \cdot [1/\Delta_0 + \Delta_{\mathrm{ns}} \cdot (\Delta_0 - \chi''(y_0))]\}}} \end{cases} \tag{4.107}$$

Eqs. (4.108)-(4.110) are only calculated for $x_{\mathrm{g}} > 0$.

$$E_{\mathrm{s}} = \exp(-x_{\mathrm{s}}) \tag{4.108}$$

$$D_{\mathrm{s}} = [1/E_{\mathrm{s}} - x_{\mathrm{s}} - 1 - \chi(x_{\mathrm{s}})] \cdot \Delta_{\mathrm{ns}} \tag{4.109}$$

$$P_{\mathrm{s}} = x_{\mathrm{s}} - 1 + E_{\mathrm{s}} \tag{4.110}$$

$$x_{\mathrm{gs}} = \begin{cases} x_{\mathrm{g}} - x_{\mathrm{s}} & \text{for } x_{\mathrm{g}} \le 0 \\ G \cdot \sqrt{D_{\mathrm{s}} + P_{\mathrm{s}}} & \text{for } x_{\mathrm{g}} > 0 \end{cases} \tag{4.111}$$

$$\psi_{\mathrm{ss}} = \boldsymbol{\phi}_{\mathbf{T}}^* \cdot x_{\mathrm{s}} \tag{4.112}$$

4.2.4 Drain Saturation Voltage

Eqs. (4.113)-(4.133) are only calculated for $x_{\mathrm{g}} > 0$.

$$q_{\mathrm{is}} = \frac{G^2 \cdot \boldsymbol{\phi}_{\mathbf{T}}^* \cdot D_{\mathrm{s}}}{x_{\mathrm{gs}} + G \cdot \sqrt{P_{\mathrm{s}}}} \tag{4.113}$$

$$\alpha_{\mathrm{s}} = 1 + \frac{G \cdot (1 - E_{\mathrm{s}})}{2 \cdot \sqrt{P_{\mathrm{s}}}} \tag{4.114}$$

$$q_{\mathrm{bs}} = \boldsymbol{\phi}_{\mathbf{T}}^* \cdot G \cdot \sqrt{P_{\mathrm{s}}} \tag{4.115}$$

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$$\rho_{\mathrm{b}} = \begin{cases} 1 + \mathbf{RSB} \cdot V_{\mathrm{sbx}} & \text{for } \mathbf{RSB} \geq 0 \\ \dfrac{1}{1 - \mathbf{RSB} \cdot V_{\mathrm{sbx}}} & \text{for } \mathbf{RSB} < 0 \end{cases} \tag{4.116}$$

$$\rho_{\mathrm{g,s}} = \begin{cases} \dfrac{1}{1 + \mathbf{RSG} \cdot q_{\mathrm{is}}} & \text{for } \mathbf{RSG} \geq 0 \\ 1 - \mathbf{RSG} \cdot q_{\mathrm{is}} & \text{for } \mathbf{RSG} < 0 \end{cases} \tag{4.117}$$

$$\rho_{\mathrm{s}} = \boldsymbol{\theta}_{\mathbf{R}} \cdot \rho_{\mathrm{b}} \cdot \rho_{\mathrm{g,s}} \cdot q_{\mathrm{is}} \tag{4.118}$$

$$\mu_{\mathrm{x}} = \frac{1 + \boldsymbol{X}_{\mathbf{cor}} \cdot V_{\mathrm{sbx}}}{1 + 0.2 \cdot \boldsymbol{X}_{\mathbf{cor}} \cdot V_{\mathrm{sbx}}} \tag{4.119}$$

$$E_{\mathrm{eff,s}} = \boldsymbol{E}_{\mathbf{eff0}} \cdot \left(q_{\mathrm{bs}} + \boldsymbol{\eta}_{\boldsymbol{\mu}} \cdot q_{\mathrm{is}}\right) \tag{4.120}$$

$$G_{\mathrm{mob,s}} = \frac{1 + \left(\boldsymbol{\mu}_{\mathbf{E}} \cdot E_{\mathrm{eff,s}}\right)^{\boldsymbol{\theta}_{\boldsymbol{\mu}}} + \boldsymbol{C}_{\mathbf{S}} \cdot \left(\dfrac{q_{\mathrm{bs}}}{q_{\mathrm{is}} + q_{\mathrm{bs}}}\right)^2 + \rho_{\mathrm{s}}}{\mu_{\mathrm{x}}} \tag{4.121}$$

$$\xi_{\mathrm{tb}} = \begin{cases} 1 + \mathbf{THESATB} \cdot V_{\mathrm{sbx}} & \text{for } \mathbf{THESATB} \geq 0 \\ \dfrac{1}{1 - \mathbf{THESATB} \cdot V_{\mathrm{sbx}}} & \text{for } \mathbf{THESATB} < 0 \end{cases} \tag{4.122}$$

$$w_{\mathrm{sat,s}} = \frac{100 \cdot q_{\mathrm{is}} \cdot \xi_{\mathrm{tb}}}{100 + q_{\mathrm{is}} \cdot \xi_{\mathrm{tb}}} \tag{4.123}$$

$$\theta^*_{\mathrm{sat,s}} = \begin{cases} \dfrac{\boldsymbol{\theta}_{\mathbf{sat}}}{G_{\mathrm{mob,s}}} \cdot \left(1 + \mathbf{THESATG} \cdot w_{\mathrm{sat,s}}\right) & \text{for } \mathbf{THESATG} \geq 0 \\ \dfrac{\boldsymbol{\theta}_{\mathbf{sat}}}{G_{\mathrm{mob,s}}} \cdot \dfrac{1}{1 - \mathbf{THESATG} \cdot w_{\mathrm{sat,s}}} & \text{for } \mathbf{THESATG} < 0 \end{cases} \tag{4.124}$$

$$\phi_\infty = q_{\mathrm{is}}/\alpha_{\mathrm{s}} + \boldsymbol{\phi}^*_{\mathbf{T}} \tag{4.125}$$

$$y_{\mathrm{sat}} = \begin{cases} \theta^*_{\mathrm{sat,s}} \cdot \phi_\infty/\sqrt{2} & \text{for NMOS} \\ \dfrac{\theta^*_{\mathrm{sat,s}} \cdot \phi_\infty/\sqrt{2}}{\sqrt{1 + \theta^*_{\mathrm{sat,s}} \cdot \phi_\infty/\sqrt{2}}} & \text{for PMOS} \end{cases} \tag{4.126}$$

$$z_{\mathrm{a}} = \frac{2}{1 + \sqrt{1 + 4 \cdot y_{\mathrm{sat}}}} \tag{4.127}$$

$$\phi_0 = \phi_\infty \cdot z_{\mathrm{a}} \cdot \left[1 + 0.86 \cdot z_{\mathrm{a}} \cdot y_{\mathrm{sat}} \cdot \frac{1 - z_{\mathrm{a}}^2 \cdot y_{\mathrm{sat}}}{1 + 4 \cdot z_{\mathrm{a}}^3 \cdot y_{\mathrm{sat}}^2}\right] \tag{4.128}$$

$$a_{\mathrm{sat}} = x_{\mathrm{gs}} + G^2/2 \tag{4.129}$$

$$\phi_2 = \frac{\boldsymbol{\phi}_{\mathbf{T}}^{*} \cdot 0.98 \cdot G^2 \cdot D_{\mathrm{s}}}{a_{\mathrm{sat}} + \sqrt{a_{\mathrm{sat}}^2 - 0.98 \cdot G^2 \cdot D_{\mathrm{s}}}} \tag{4.130}$$

$$\phi_{\mathrm{sat}} = \frac{2 \cdot \phi_0 \cdot \phi_2}{\phi_0 + \phi_2 + \sqrt{(\phi_0 + \phi_2)^2 - 3.96 \cdot \phi_0 \cdot \phi_2}} \tag{4.131}$$

$$V_{\mathrm{dsat}} = \phi_{\mathrm{sat}} - \boldsymbol{\phi}_{\mathbf{T}}^{*} \cdot \ln \left[1 + \frac{\phi_{\mathrm{sat}} \cdot \left(\phi_{\mathrm{sat}} - 2 \cdot a_{\mathrm{sat}} \cdot \boldsymbol{\phi}_{\mathbf{T}}^{*}\right)}{G^2 \cdot D_{\mathrm{s}} \cdot \boldsymbol{\phi}_{\mathbf{T}}^{*\,2}}\right] \tag{4.132}$$

$$V_{\mathrm{dse}} = \frac{V_{\mathrm{DS}}}{\left[1 + (V_{\mathrm{DS}}/V_{\mathrm{dsat}})^{\mathbf{AX}}\right]^{1/\mathbf{AX}}} \tag{4.133}$$

4.2.5 Surface Potential at Drain Side and Related Variables

Eqs. (4.134)-(4.143) are only calculated for $x_{\mathrm{g}} > 0$.

$$x_{\mathrm{nd}} = \frac{\boldsymbol{\phi}_{\mathbf{B}} + V_{\mathrm{SB}}^{*} + V_{\mathrm{dse}}}{\boldsymbol{\phi}_{\mathbf{T}}^{*}} \tag{4.134}$$

$$k_{\mathrm{ds}} = \exp\left(-V_{\mathrm{dse}}/\boldsymbol{\phi}_{\mathbf{T}}^{*}\right) \tag{4.135}$$

$$\Delta_{\mathrm{nd}} = \Delta_{\mathrm{ns}} \cdot k_{\mathrm{ds}} \tag{4.136}$$

$$\text{if } x_{\mathrm{g}} \le x_{\mathrm{mrg}} \left\{ \; x_{\mathrm{d}} = \frac{x_{\mathrm{g}}}{\xi} \cdot \left[1 + G \cdot x_{\mathrm{g}} \cdot \frac{1 - \Delta_{\mathrm{nd}}}{\xi^2 \cdot 6 \cdot \sqrt{2}}\right] \right. \tag{4.137}$$

$$\text{if } x_{\mathrm{g}} > x_{\mathrm{mrg}} \left\{ \begin{array}{l} b_{\mathrm{x}} = x_{\mathrm{nd}} + 3.0 \\ \eta = \mathrm{MINA}(x_0,\, b_{\mathrm{x}},\, 5) - \left(b_{\mathrm{x}} - \sqrt{b_{\mathrm{x}}^2 + 5}\right)/2 \\ a = (x_{\mathrm{g}} - \eta)^2 - G^2 \cdot [\exp(-\eta) + \eta - 1 - \Delta_{\mathrm{nd}} \cdot (\eta + 1 + \chi(\eta))] \\ b = 1 - G^2/2 \cdot [\exp(-\eta) - \Delta_{\mathrm{nd}} \cdot \chi''(\eta)] \\ c = 2 \cdot (x_{\mathrm{g}} - \eta) + G^2 \cdot [1 - \exp(-\eta) - \Delta_{\mathrm{nd}} \cdot (1 + \chi'(\eta))] \\ \tau = x_{\mathrm{nd}} - \eta + \ln\left(a/G^2\right) \\ y_0 = \sigma_2(a,\, b,\, c,\, \tau,\, \eta) \\ \Delta_0 = \exp\left(y_0\right) \\ p = 2 \cdot (x_{\mathrm{g}} - y_0) + G^2 \cdot [1 - 1/\Delta_0 + \Delta_{\mathrm{nd}} \cdot (\Delta_0 - 1 - \chi'(y_0))] \\ q = (x_{\mathrm{g}} - y_0)^2 - G^2 \cdot [y_0 + 1/\Delta_0 - 1 + \Delta_{\mathrm{nd}} \cdot (\Delta_0 - y_0 - 1 - \chi(y_0))] \\ x_{\mathrm{d}} = y_0 + \dfrac{2 \cdot q}{p + \sqrt{p^2 - 2 \cdot q \cdot \{2 - G^2 \cdot [1/\Delta_0 + \Delta_{\mathrm{nd}} \cdot (\Delta_0 - \chi''(y_0))]\}}} \end{array} \right. \tag{4.138}$$

$$x_{\mathrm{ds}} = x_{\mathrm{d}} - x_{\mathrm{s}} \tag{4.139}$$

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$$\text{if } x_{\mathrm{ds}} < 10^{-10} \begin{cases} p = 2 \cdot x_{\mathrm{gs}} + G^2 \cdot [1 - E_{\mathrm{s}} + \Delta_{\mathrm{nd}} \cdot (1/E_{\mathrm{s}} - 1 - \chi'(x_{\mathrm{s}}))] \\ q = G^2 \cdot (1 - k_{\mathrm{ds}}) \cdot D_{\mathrm{s}} \\ \xi = 1 - G^2/2 \cdot [E_{\mathrm{s}} + \Delta_{\mathrm{nd}} \, (1/E_{\mathrm{s}} - \chi''(x_{\mathrm{s}}))] \\ x_{\mathrm{ds}} = \dfrac{2 \cdot q}{p + \sqrt{p^2 - 4 \cdot \xi \cdot q}} \\ x_{\mathrm{d}} = x_{\mathrm{s}} + x_{\mathrm{ds}} \end{cases} \tag{4.140}$$

$$E_{\mathrm{d}} = \exp(-x_{\mathrm{d}}) \tag{4.141}$$

$$D_{\mathrm{d}} = (1/E_{\mathrm{d}} - x_{\mathrm{d}} - 1 - \chi(x_{\mathrm{d}})) \cdot \Delta_{\mathrm{nd}} \tag{4.142}$$

$$\Delta\psi = \boldsymbol{\phi_{\mathrm{T}}^{*}} \cdot x_{\mathrm{ds}} \tag{4.143}$$

$$\psi_{\mathrm{sd}} = \boldsymbol{\phi_{\mathrm{T}}^{*}} \cdot x_{\mathrm{d}} \tag{4.144}$$

4.2.6 Mid-Point Surface Potential and Related Variables

$$\text{if } x_{\mathrm{g}} > 0 \begin{cases} x_{\mathrm{m}} = (x_{\mathrm{s}} + x_{\mathrm{d}})/2 \\ E_{\mathrm{m}} = \sqrt{E_{\mathrm{s}} \cdot E_{\mathrm{d}}} \\ \bar{D} = (D_{\mathrm{s}} + D_{\mathrm{d}})/2 \\ D_{\mathrm{m}} = \bar{D} + x_{\mathrm{ds}}^2/8 \cdot \left(E_{\mathrm{m}} - 2/G^2\right) \\ P_{\mathrm{m}} = x_{\mathrm{m}} - 1 + E_{\mathrm{m}} \\ x_{\mathrm{gm}} = G \cdot \sqrt{D_{\mathrm{m}} + P_{\mathrm{m}}} \end{cases} \tag{4.145}$$

$$\text{if } x_{\mathrm{g}} \le 0 \begin{cases} x_{\mathrm{m}} = x_{\mathrm{s}} \\ x_{\mathrm{gm}} = x_{\mathrm{g}} - x_{\mathrm{s}} \end{cases} \tag{4.146}$$

4.2.7 Polysilicon Depletion

Eqs. (4.147)-(4.161) are only calculated for $\boldsymbol{k_{\mathrm{P}}} > 0$ and $x_{\mathrm{g}} > 0$ (otherwise $\eta_{\mathrm{p}} = 1$):

$$x_{\mathrm{m}}^{(0)} = x_{\mathrm{m}}, \qquad x_{\mathrm{ds}}^{(0)} = x_{\mathrm{ds}}, \qquad D_{\mathrm{m}}^{(0)} = D_{\mathrm{m}}, \qquad E_{\mathrm{m}}^{(0)} = E_{\mathrm{m}}, \tag{4.147}$$

$$d_0 = 1 - E_{\mathrm{m}}^{(0)} + 2 \cdot x_{\mathrm{gm}}/G^2 \tag{4.148}$$

$$\eta_{\mathrm{p}} = 1/\sqrt{1 + \boldsymbol{k_{\mathrm{P}}} \cdot x_{\mathrm{gm}}} \tag{4.149}$$

$$x_{\mathrm{pm}} = \boldsymbol{k_{\mathrm{P}}} \cdot \left[\frac{\eta_{\mathrm{p}} \cdot x_{\mathrm{gm}}}{1 + \eta_{\mathrm{p}}}\right]^2 \cdot \frac{D_{\mathrm{m}}^{(0)}}{D_{\mathrm{m}}^{(0)} + P_{\mathrm{m}}} \tag{4.150}$$

$$p = 2 \cdot (x_{\mathrm{gm}} - x_{\mathrm{pm}}) + G^2 \cdot \left(1 - E_{\mathrm{m}}^{(0)} + D_{\mathrm{m}}^{(0)}\right) \tag{4.151}$$

$$q = x_{\rm pm} \cdot (x_{\rm pm} - 2 \cdot x_{\rm gm}) \tag{4.152}$$

$$\xi_{\rm p} = 1 - G^2/2 \cdot \left(E_{\rm m}^{(0)} + D_{\rm m}^{(0)}\right) \tag{4.153}$$

$$u_{\rm p} = \frac{p \cdot q}{p^2 - \xi_{\rm p} \cdot q} \tag{4.154}$$

$$x_{\rm m} = x_{\rm m}^{(0)} + u_{\rm p} \tag{4.155}$$

$$E_{\rm m} = E_{\rm m}^{(0)} \cdot \exp\left(-u_{\rm p}\right) \tag{4.156}$$

$$D_{\rm m} = D_{\rm m}^{(0)} \cdot \exp\left(u_{\rm p}\right) \tag{4.157}$$

$$P_{\rm m} = x_{\rm m} - 1 + E_{\rm m} \tag{4.158}$$

$$x_{\rm gm} = G \cdot \sqrt{D_{\rm m} + P_{\rm m}} \tag{4.159}$$

$$x_{\rm ds} = x_{\rm ds}^{(0)} \cdot \frac{\exp\left(u_{\rm p}\right) \cdot \left[\bar{D} + d_0\right]}{1 - E_{\rm m} + 2 \cdot x_{\rm gm} \cdot \eta_{\rm p}/G^2 + \exp\left(u_{\rm p}\right) \cdot \bar{D}} \tag{4.160}$$

$$\Delta\psi = \boldsymbol{\phi}_{\mathbf{T}}^{*} \cdot x_{\rm ds} \tag{4.161}$$

4.2.8 Potential Mid-Point Inversion Charge and Related Variables

Eqs. (4.162)-(4.170) are only calculated for $x_{\rm g} > 0$.

$$q_{\rm im} = \frac{G^2 \cdot \boldsymbol{\phi}_{\mathbf{T}}^{*} \cdot D_{\rm m}}{x_{\rm gm} + G \cdot \sqrt{P_{\rm m}}} \tag{4.162}$$

$$\alpha_{\rm m} = \eta_{\rm p} + \frac{G \cdot (1 - E_{\rm m})}{2 \cdot \sqrt{P_{\rm m}}} \tag{4.163}$$

$$q_{\rm im}^{*} = q_{\rm im} + \boldsymbol{\phi}_{\mathbf{T}}^{*} \cdot \alpha_{\rm m} \tag{4.164}$$

$$q_{\rm bm} = \boldsymbol{\phi}_{\mathbf{T}}^{*} \cdot G \cdot \sqrt{P_{\rm m}} \tag{4.165}$$

Series resistance:

$$\rho_{\rm g} = \begin{cases} \dfrac{1}{1 + \mathbf{RSG} \cdot q_{\rm im}} & \text{for } \mathbf{RSG} \geq 0 \\ 1 - \mathbf{RSG} \cdot q_{\rm im} & \text{for } \mathbf{RSG} < 0 \end{cases} \tag{4.166}$$

$$\rho_{\rm s} = \boldsymbol{\theta}_{\mathbf{R}} \cdot \rho_{\rm b} \cdot \rho_{\rm g} \cdot q_{\rm im} \tag{4.167}$$

Mobility reduction:

$$E_{\rm eff} = \boldsymbol{E}_{\mathbf{eff0}} \cdot \left(q_{\rm bm} + \boldsymbol{\eta}_{\boldsymbol{\mu}} \cdot q_{\rm im}\right) \tag{4.168}$$

$$q_{\rm eff1} = q_{\rm bm} + \boldsymbol{\eta}_{\boldsymbol{\mu},ac} \cdot q_{\rm im} \tag{4.169}$$

$$G_{\rm mob} = \frac{1 + \left(\boldsymbol{\mu}_{\mathbf{E}} \cdot E_{\rm eff}\right)^{\boldsymbol{\theta}_{\boldsymbol{\mu}}} + \boldsymbol{C}_{\mathbf{S}} \cdot \left(\frac{q_{\rm bm}}{q_{\rm im} + q_{\rm bm}}\right)^2 + \rho}{\mu_{\rm x}} \tag{4.170}$$

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4.2.9 Drain-Source Channel Current

Eqs. (4.171)-(4.182) are only calculated for $x_\mathrm{g} > 0$:

Channel length modulation:

$$R_1 = q_\mathrm{im}/q_\mathrm{im}^* \tag{4.171}$$

$$R_2 = \boldsymbol{\phi}_\mathbf{T}^* \cdot \alpha_\mathrm{m}/q_\mathrm{im}^* \tag{4.172}$$

$$T_1 = \ln\left(\frac{1+\dfrac{V_\mathrm{DS}-\Delta\psi}{\mathbf{VP}}}{1+\dfrac{V_\mathrm{dse}-\Delta\psi}{\mathbf{VP}}}\right) \tag{4.173}$$

$$T_2 = \ln\left(1+\frac{V_\mathrm{dsx}}{\mathbf{VP}}\right) \tag{4.174}$$

$$\Delta L/L = \mathbf{ALP} \cdot T_1 \tag{4.175}$$

$$G_{\Delta L} = \frac{1}{1+\Delta L/L + (\Delta L/L)^2} \tag{4.176}$$

$$\Delta L_1/L = \left[\mathbf{ALP} + \frac{\mathbf{ALP1}}{q_\mathrm{im}^*} \cdot R_1\right] \cdot T_1 + \mathbf{ALP2} \cdot q_\mathrm{bm} \cdot R_2^2 \cdot T_2 \tag{4.177}$$

$$F_{\Delta L} = \left[1+\Delta L_1/L + (\Delta L_1/L)^2\right] \cdot G_{\Delta L} \tag{4.178}$$

Velocity saturation:

$$w_\mathrm{sat} = \frac{100 \cdot q_\mathrm{im} \cdot \xi_\mathrm{tb}}{100 + q_\mathrm{im} \cdot \xi_\mathrm{tb}} \tag{4.179}$$

$$\theta_\mathrm{sat}^* = \begin{cases} \dfrac{\boldsymbol{\theta}_\mathbf{sat}}{G_\mathrm{mob,s} \cdot G_{\Delta L}} \cdot (1 + \mathbf{THESATG} \cdot w_\mathrm{sat}) & \text{for } \mathbf{THESATG} \geq 0 \\[2ex] \dfrac{\boldsymbol{\theta}_\mathbf{sat}}{G_\mathrm{mob,s} \cdot G_{\Delta L}} \cdot \dfrac{1}{1 - \mathbf{THESATG} \cdot w_\mathrm{sat}} & \text{for } \mathbf{THESATG} < 0 \end{cases} \tag{4.180}$$

$$z_\mathrm{sat} = \begin{cases} \left(\theta_\mathrm{sat}^* \cdot \Delta\psi\right)^2 & \text{for NMOS} \\[2ex] \dfrac{\left(\theta_\mathrm{sat}^* \cdot \Delta\psi\right)^2}{1+\theta_\mathrm{sat}^* \cdot \Delta\psi} & \text{for PMOS} \end{cases} \tag{4.181}$$

$$G_\mathrm{vsat} = \frac{G_\mathrm{mob} \cdot G_{\Delta L}}{2} \cdot \left(1 + \sqrt{1 + 2 \cdot z_\mathrm{sat}}\right) \tag{4.182}$$

Auxiliary Variables for Calculation of Intrinsic Charges and Gate Current. Eqs. (4.183)-(4.185) are only calculated for $x_\mathrm{g} > 0$.

$$V_\mathrm{oxm} = \boldsymbol{\phi}_\mathbf{T}^* \cdot x_\mathrm{gm} \tag{4.183}$$

$$\alpha_\mathrm{m}' = \alpha_\mathrm{m} \cdot \left[1 + \frac{z_\mathrm{sat}}{2} \cdot \left(\frac{G_\mathrm{mob} \cdot G_{\Delta L}}{G_\mathrm{vsat}}\right)^2\right] \tag{4.184}$$

$$H = \frac{G_{\rm mob} \cdot G_{\Delta L}}{G_{\rm vsat}} \cdot \frac{q^*_{\rm im}}{\alpha'_{\rm m}} \tag{4.185}$$

In the remainder of this document, some variables (e.g., $x_{\rm g}$) are labeled 'dc' or 'ac' (e.g., $x_{\rm g,dc}$ or $x_{{\rm g},ac}$). Variables labeled 'dc' result from the *first* evaluation of Eqs. (4.94)–(4.185). For variables labeled 'ac', there are two possibilities. If **SWNUD** $= 1$ or **SWDELVTAC** $= 1$, their values result from the *second* evaluation of Eqs. (4.94)–(4.185). In any other case, their value is equal to their 'dc'-counterpart.
This applies to the following variables: $x_{\rm g}$, $q_{\rm eff1}$, $V_{\rm oxm}$, $q_{\rm im}$, $q^*_{\rm im}$, $\alpha_{\rm m}$, $\Delta\psi$, $G_{\Delta L}$, $F_{\Delta L}$, H, $\eta_{\rm p}$, $G_{\rm vsat}$, $V_{\rm dse}$, $G_{\rm mob}$, $x_{\rm m}$, G, $x_{\rm gm}$, $\theta^*_{\rm sat}$.

Drain-Source channel current:

$$I_{\rm DS} = \begin{cases} 0 & \text{for } x_{\rm g,dc} \le 0 \\ \boldsymbol{\beta} \cdot F_{\Delta L,\rm dc} \cdot \dfrac{q^*_{\rm im,dc}}{G_{\rm vsat,dc}} \cdot \Delta\psi_{\rm dc} & \text{for } x_{\rm g,dc} > 0 \end{cases} \tag{4.186}$$

4.2.10 Impact Ionization or Weak-Avalanche

The equations in this Section are only calculated when **SWIMPACT** $= 1$ and $x_{\rm g} > 0$.

$$a^*_2 = \boldsymbol{a_2} \cdot \left[1 + \mathbf{A4} \cdot \left(\sqrt{V^*_{\rm SB,dc} + \boldsymbol{\phi}_\mathbf{B}} - \sqrt{\boldsymbol{\phi}_\mathbf{B}}\right)\right] \tag{4.187}$$

$$\Delta V_{\rm sat} = V_{\rm DS} - \mathbf{A3} \cdot \Delta\psi_{\rm dc} \tag{4.188}$$

$$M_{\rm avl} = \begin{cases} 0 & \text{for } \Delta V_{\rm sat} \le 0 \\ \mathbf{A1} \cdot \Delta V_{\rm sat} \cdot \exp\left(-\dfrac{a^*_2}{\Delta V_{\rm sat}}\right) & \text{for } \Delta V_{\rm sat} > 0 \end{cases} \tag{4.189}$$

$$I_{\rm avl} = M_{\rm avl} \cdot I_{\rm DS} \tag{4.190}$$

4.2.11 Surface Potential in Gate Overlap Regions

$$x_{\rm sov}\left(x_{\rm g}\right) = \begin{cases} x'_g = \left(x_{\rm g} + \sqrt{x^2_{\rm g} + \boldsymbol{\varepsilon}^2_\mathbf{ov}}\right)\Big/ 2 \\ x_{\rm sov} = -x'_{\rm g} - \boldsymbol{G}^2_\mathbf{ov}/2 + \boldsymbol{G}_\mathbf{ov} \cdot \sqrt{x'_{\rm g} + \boldsymbol{G}^2_\mathbf{ov}/4 + \boldsymbol{a}_\mathbf{ov}} + \boldsymbol{\delta}_\mathbf{ov} \end{cases} \tag{4.191}$$

$$x_{\rm dov}\left(x_{\rm g}\right) = \begin{cases} x'_g = \left(x_{\rm g} + \sqrt{x^2_{\rm g} + \boldsymbol{\varepsilon}^2_\mathbf{dov}}\right)\Big/ 2 \\ x_{\rm dov} = -x'_{\rm g} - \boldsymbol{G}^2_\mathbf{dov}/2 + \boldsymbol{G}_\mathbf{dov} \cdot \sqrt{x'_{\rm g} + \boldsymbol{G}^2_\mathbf{dov}/4 + \boldsymbol{a}_\mathbf{dov}} + \boldsymbol{\delta}_\mathbf{dov} \end{cases} \tag{4.192}$$

$$\psi_{\rm sov} = -\boldsymbol{\phi}_{\mathbf{T}_{\rm A}} \cdot x_{\rm sov}\left(-\frac{V_{\rm GS}}{\boldsymbol{\phi}_{\mathbf{T}_{\rm A}}}\right) \tag{4.193}$$

$$\psi_{\rm dov} = -\boldsymbol{\phi}_{\mathbf{T}_{\rm A}} \cdot x_{\rm dov}\left(-\frac{V_{\rm GS} - V_{\rm DS}}{\boldsymbol{\phi}_{\mathbf{T}_{\rm A}}}\right) \tag{4.194}$$

$$V_{\rm ov_0} = V_{\rm GS} - \psi_{\rm sov} \tag{4.195}$$

$$V_{\rm ov_L} = V_{\rm GS} - V_{\rm DS} - \psi_{\rm dov} \tag{4.196}$$

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4.2.12 Gate Current

The equations in this Section are only calculated when **SWIGATE** $= 1$.

Source/Drain gate overlap current:

$$I_{\rm GSov}(V_{\rm GX},\,\psi_{\rm ov},\,V_{\rm ov}) = \begin{cases} V_{\rm ov}^* = \sqrt{V_{\rm ov}^2 + 10^{-6}} \\ z_{\rm g} = \begin{cases} \mathrm{MINA}\left(\dfrac{V_{\rm ov}^*}{\mathbf{CHIB}},\,\boldsymbol{GC_{\mathrm{Q}}},\,10^{-6}\right) & \text{for } \mathbf{GC3} < 0 \\ \dfrac{V_{\rm ov}^*}{\mathbf{CHIB}} & \text{for } \mathbf{GC3} \geq 0 \end{cases} \\ F_{\rm S1} = \dfrac{3.0\cdot \boldsymbol{\phi_{\mathrm{T_A}}} + \psi_{\rm ov}}{\boldsymbol{\phi_{\mathrm{T_A}}}} \\ F_{\rm S2} = -3.0 - \mathbf{GCO} \\ F_{\rm S3} = 30\cdot V_{\rm GX} \\ F_{\rm Sov} = \mathrm{MXE}\left(F_{\rm S2},\,\mathrm{MNE}\left(F_{\rm S1},\,F_{\rm S3},\,0.9\right),\,0.3\right) \\ I_{\rm Gov} = \boldsymbol{I_{\mathrm{GOV}}}\cdot F_{\rm Sov}\cdot \\ \qquad \exp\left(\boldsymbol{B_{\mathrm{ov}}}\cdot\left[-\dfrac{3}{2} + z_{\rm g}\cdot(\mathbf{GC2} + \mathbf{GC3}\cdot z_{\rm g})\right]\right) \end{cases} \tag{4.197}$$

$$I_{\rm GDov}(V_{\rm GX},\,\psi_{\rm ov},\,V_{\rm ov}) = \begin{cases} V_{\rm ov}^* = \sqrt{V_{\rm ov}^2 + 10^{-6}} \\ z_{\rm g} = \begin{cases} \mathrm{MINA}\left(\dfrac{V_{\rm ov}^*}{\mathbf{CHIB}},\,\boldsymbol{GC_{\mathrm{Q}}},\,10^{-6}\right) & \text{for } \mathbf{GC3} < 0 \\ \dfrac{V_{\rm ov}^*}{\mathbf{CHIB}} & \text{for } \mathbf{GC3} \geq 0 \end{cases} \\ F_{\rm S1} = \dfrac{3.0\cdot \boldsymbol{\phi_{\mathrm{T_A}}} + \psi_{\rm ov}}{\boldsymbol{\phi_{\mathrm{T_A}}}} \\ F_{\rm S2} = -3.0 - \mathbf{GCO} \\ F_{\rm S3} = 30\cdot V_{\rm GX} \\ F_{\rm Sov} = \mathrm{MXE}\left(F_{\rm S2},\,\mathrm{MNE}\left(F_{\rm S1},\,F_{\rm S3},\,0.9\right),\,0.3\right) \\ I_{\rm Gov} = \boldsymbol{I_{\mathrm{GOVD}}}\cdot F_{\rm Sov}\cdot \\ \qquad \exp\left(\boldsymbol{B_{\mathrm{dov}}}\cdot\left[-\dfrac{3}{2} + z_{\rm g}\cdot(\mathbf{GC2} + \mathbf{GC3}\cdot z_{\rm g})\right]\right) \end{cases} \tag{4.198}$$

$$I_{\rm GSov} = I_{\rm GSov}\left(V_{\rm GS},\,\psi_{\rm sov},\,V_{\rm ov_0}\right) \tag{4.199}$$

$$I_{\rm GDov} = I_{\rm GDov}\left(V_{\rm GS} - V_{\rm DS}\,,\,\psi_{\rm dov},\,V_{\rm ov_L}\right) \tag{4.200}$$

Gate-channel current:

$$V_{\rm m} = V_{\rm SB,dc}^* + \boldsymbol{\phi_{\mathrm{T}}^*}\cdot\left[\frac{x_{\rm ds,dc}}{2} - \ln\left(\frac{1+\exp(x_{\rm ds,dc} - V_{\rm dse,dc}/\boldsymbol{\phi_{\mathrm{T}}^*})}{2}\right)\right] \tag{4.201}$$

$$\psi_{\rm t} = \mathrm{MINA}\left(0,\, V_{\rm oxm,dc} + \boldsymbol{D}_{\mathbf{ch}},\, 0.01\right) \tag{4.202}$$

$$V^{*}_{\rm oxm} = \sqrt{V^2_{\rm oxm,dc} + 10^{-6}} \tag{4.203}$$

$$z_{\rm g} = \begin{cases} \mathrm{MINA}\left(\dfrac{V^{*}_{\rm oxm}}{\mathbf{CHIB}},\, \boldsymbol{GC}_{\mathbf{Q}},\, 10^{-6}\right) & \text{for } \mathbf{GC3} < 0 \\[2ex] \dfrac{V^{*}_{\rm oxm}}{\mathbf{CHIB}} & \text{for } \mathbf{GC3} \geq 0 \end{cases} \tag{4.204}$$

$$\Delta_{\rm Si} = \exp\left(x_{\rm m,dc} - \frac{\boldsymbol{\alpha}_{\mathbf{b}} + V_{\rm m} - \psi_{\rm t}}{\boldsymbol{\phi}^{*}_{\mathbf{T}}}\right) \tag{4.205}$$

$$F_{\rm S} = \ln\left[\frac{1 + \Delta_{\rm Si}}{1 + \Delta_{\rm Si}\cdot\exp\left(-\dfrac{V_{\rm GS} + V^{*}_{\rm SB,dc} - V_{\rm m}}{\boldsymbol{\phi}^{*}_{\mathbf{T}}}\right)}\right] \tag{4.206}$$

$$I_{\rm GCO} = \boldsymbol{I}_{\mathbf{GINV}}\cdot F_{\rm S}\cdot\exp\left(\boldsymbol{B}\cdot\left[-3/2 + z_{\rm g}\cdot\left(\mathbf{GC2} + \mathbf{GC3}\cdot z_{\rm g}\right)\right]\right) \tag{4.207}$$

$$\text{if } x_{\rm g,dc} > 0 \begin{cases} u_0 = \mathbf{CHIB}/\left[\boldsymbol{B}\cdot\left(\mathbf{GC2} + 2\cdot\mathbf{GC3}\cdot z_{\rm g}\right)\right] \\ x = \Delta\psi_{\rm dc}/\left(2\cdot u_0\right) \\ b = u_0/H_{\rm dc} \\ B_{\rm g} = b\cdot(1-b)/2 \\ A_{\rm g} = 1/2 - 3\cdot B_{\rm g} \\ p_{\rm gc} = (1-b)\cdot\dfrac{\sinh(x)}{x} + b\cdot\cosh(x) \\ p_{\rm gd} = \dfrac{p_{\rm gc}}{2} - B_{\rm g}\cdot\sinh(x) - A_{\rm g}\cdot\dfrac{\sinh(x)}{x}\cdot\left[\coth(x) - \dfrac{1}{x}\right] \end{cases} \tag{4.208}$$

$$\text{if } x_{\rm g,dc} \leq 0 \begin{cases} p_{\rm gc} = 1 \\ p_{\rm gd} = 1/2 \end{cases} \tag{4.209}$$

$$S_{\rm g} = \frac{1}{2}\cdot\left(1 + \frac{x_{\rm g,dc}}{\sqrt{x^2_{\rm g,dc} + 10^{-6}}}\right) \tag{4.210}$$

$$I_{\rm GC} = I_{\rm GCO}\cdot p_{\rm gc}\cdot S_{\rm g} \tag{4.211}$$

$$I_{\rm GCD} = I_{\rm GCO}\cdot p_{\rm gd}\cdot S_{\rm g} \tag{4.212}$$

$$I_{\rm GCS} = I_{\rm GC} - I_{\rm GCD} \tag{4.213}$$

$$I_{\rm GB} = I_{\rm GCO}\cdot p_{\rm gc}\cdot\left(1 - S_{\rm g}\right) \tag{4.214}$$

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4.2.13 Gate-Induced Drain/Source Leakage Current

The equations in this section are only calculated when **SWGIDL** $= 1$.

$$I_{\rm gisl}(V_{\rm ov}, V) = \begin{cases} V_{\rm tov} = \sqrt{V_{\rm ov}^2 + \mathbf{CGIDL}^2 \cdot V^2 + 10^{-6}} \\ t = V \cdot V_{\rm tov} \cdot V_{\rm ov} \\ I_{\rm gisl} = \begin{cases} -\boldsymbol{A}_{\mathbf{GIDL}} \cdot t \cdot \exp\left(-\dfrac{\boldsymbol{B}_{\mathbf{GIDL}}}{V_{\rm tov}}\right) & \text{for } V_{\rm ov} < 0 \\ 0 & \text{for } V_{\rm ov} \geq 0 \end{cases} \end{cases} \tag{4.215}$$

$$I_{\rm gidl}(V_{\rm ov}, V) = \begin{cases} V_{\rm tov} = \sqrt{V_{\rm ov}^2 + \mathbf{CGIDLD}^2 \cdot V^2 + 10^{-6}} \\ t = V \cdot V_{\rm tov} \cdot V_{\rm ov} \\ I_{\rm gidl} = \begin{cases} -\boldsymbol{A}_{\mathbf{GIDLD}} \cdot t \cdot \exp\left(-\dfrac{\boldsymbol{B}_{\mathbf{GIDLD}}}{V_{\rm tov}}\right) & \text{for } V_{\rm ov} < 0 \\ 0 & \text{for } V_{\rm ov} \geq 0 \end{cases} \end{cases} \tag{4.216}$$

$$I_{\rm gisl} = I_{\rm gisl}(V_{\rm ov_0}, V_{\rm SB}) \tag{4.217}$$

$$I_{\rm gidl} = I_{\rm gidl}(V_{\rm ov_L}, V_{\rm DS} + V_{\rm SB}) \tag{4.218}$$

4.2.14 Total Terminal Currents

$$I_{\rm D} = I_{\rm DS} + I_{\rm avl} - I_{\rm GDov} - I_{\rm GCD} + I_{\rm gidl} \tag{4.219}$$

$$I_{\rm S} = -I_{\rm DS} - I_{\rm GSov} - I_{\rm GCS} + I_{\rm gisl} \tag{4.220}$$

$$I_{\rm G} = I_{\rm GC} + I_{\rm GB} + I_{\rm GDov} + I_{\rm GSov} \tag{4.221}$$

$$I_{\rm B} = -I_{\rm avl} - I_{\rm GB} - I_{\rm gidl} - I_{\rm gisl} \tag{4.222}$$

4.3 Charge Model

In this section, the charge model equations of the PSP-model are given. Use is made of the applied terminal bias values $V_{\rm GS}$, $V_{\rm DS}$ and $V_{\rm SB}$, the local parameters listed in Section 2.5.2 and the internal parameters introduced in Section 4.1. Local parameters are denoted by capital characters in bold font, whereas internal (bias-independent) parameters are denoted by symbols in bold font.

The definitions of the auxiliary functions MINA(.), MAXA(.), $\chi(.)$ and $\sigma_{1,2}(.)$ can be found in Appendix A.

4.3.1 Quantum-Mechanical Corrections

$$q_{\rm eff,ac} = \begin{cases} V_{\rm oxm,ac} & \text{for } x_{\rm g,ac} \leq 0 \\ q_{{\rm eff1},ac} & \text{for } x_{\rm g,ac} > 0 \end{cases} \tag{4.223}$$

$$C_{\rm OX}^{\rm qm} = \begin{cases} \textbf{COX} & \text{for } \boldsymbol{q_{\rm q}} = 0 \\ \dfrac{\textbf{COX}}{1 + \boldsymbol{q_{\rm q}}/({q_{\rm eff,ac}}^2 + {\boldsymbol{q_{\rm lim}}}^2)^{1/6}} & \text{for } \boldsymbol{q_{\rm q}} > 0 \end{cases} \tag{4.224}$$

4.3.2 Intrinsic Charge Model

$$\text{if } x_{\rm g} > 0 \begin{cases} F_{\rm j} = \Delta\psi_{\rm ac}/\left(2 \cdot H_{\rm ac}\right) \\ q_{\Delta L} = (1 - G_{\Delta L,\rm ac}) \cdot (q_{\rm im,ac} - \alpha_{\rm m,ac} \cdot \Delta\psi_{\rm ac}/2) \\ q_{\Delta L}^* = q_{\Delta L,\rm ac} \cdot (1 + G_{\Delta L,\rm ac}) \\ Q_{\rm G}^{(i)} = C_{\rm OX}^{\rm qm} \cdot \left[V_{\rm oxm,ac} + \dfrac{\eta_{\rm p,ac} \cdot \Delta\psi_{\rm ac}}{2} \cdot \left(\dfrac{G_{\Delta L,\rm ac}}{3} \cdot F_{\rm j} + G_{\Delta L,\rm ac} - 1\right)\right] \\ Q_{\rm I}^{(i)} = -C_{\rm OX}^{\rm qm} \cdot \left[G_{\Delta L,\rm ac} \cdot \left(q_{\rm im,ac} + \dfrac{\alpha_{\rm m,ac} \cdot \Delta\psi_{\rm ac}}{6} \cdot F_{\rm j}\right) + q_{\Delta L,\rm ac}\right] \\ Q_{\rm D}^{(i)} = -\dfrac{C_{\rm OX}^{\rm qm}}{2} \cdot \left[G_{\Delta L,\rm ac}^2 \cdot \left(q_{\rm im,ac} + \dfrac{\alpha_{\rm m,ac} \cdot \Delta\psi_{\rm ac}}{6} \cdot \left[\dfrac{F_{\rm j}^2}{5} + F_{\rm j} - 1\right]\right) + q_{\Delta L}^*\right] \end{cases} \tag{4.225}$$

$$\text{if } x_{\rm g} \leq 0 \begin{cases} Q_{\rm G}^{(i)} & = C_{\rm OX}^{\rm qm} \cdot V_{\rm oxm,ac} \\ Q_{\rm I}^{(i)} & = 0 \\ Q_{\rm D}^{(i)} & = 0 \end{cases} \tag{4.226}$$

$$Q_{\rm S}^{(i)} = Q_{\rm I}^{(i)} - Q_{\rm D}^{(i)} \tag{4.227}$$

$$Q_{\rm B}^{(i)} = -Q_{\rm I}^{(i)} - Q_{\rm G}^{(i)} \tag{4.228}$$

4.3.3 Extrinsic Charge Model

The charges of the source and drain overlap regions:

$$Q_{\rm sov} = \textbf{CGOV} \cdot (V_{\rm GS} - \psi_{\rm sov}) \tag{4.229}$$

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$$Q_{\rm dov} = \textbf{CGOVD} \cdot (V_{\rm GS} - V_{\rm DS} - \psi_{\rm dov}) \tag{4.230}$$

The charge of the bulk overlap region

$$Q_{\rm bov} = \textbf{CGBOV} \cdot (V_{\rm GS} + V_{\rm SB}) \tag{4.231}$$

Outer fringe charge:

$$Q_{\rm ofs} = \textbf{CFR} \cdot V_{\rm GS} \tag{4.232}$$

$$Q_{\rm ofd} = \textbf{CFRD} \cdot (V_{\rm GS} - V_{\rm DS}) \tag{4.233}$$

4.3.4 Total Terminal Charges

$$Q_{\rm G} = Q_{\rm G}^{(i)} + Q_{\rm sov} + Q_{\rm dov} + Q_{\rm ofs} + Q_{\rm ofd} + Q_{\rm bov} \tag{4.234}$$

$$Q_{\rm S} = Q_{\rm S}^{(i)} - Q_{\rm sov} - Q_{\rm ofs} \tag{4.235}$$

$$Q_{\rm D} = Q_{\rm D}^{(i)} - Q_{\rm dov} - Q_{\rm ofd} \tag{4.236}$$

$$Q_{\rm B} = Q_{\rm B}^{(i)} - Q_{\rm bov} \tag{4.237}$$

4.4 Noise Model

Eqs. (4.238)-(4.254) are only calculated for $x_\mathrm{g} > 0$. In these equations f_op represents the operation frequency of the transistor and $j = \sqrt{-1}$.

$$N^* = \frac{C_\mathrm{ox}}{q} \cdot \alpha_\mathrm{m,dc} \cdot \boldsymbol{\phi}_\mathbf{T} \tag{4.238}$$

$$N^*_\mathrm{m} = \frac{C_\mathrm{ox}}{q} \cdot q^*_\mathrm{im,dc} \tag{4.239}$$

$$\Delta N = \frac{C_\mathrm{ox}}{q} \cdot \alpha_\mathrm{m,dc} \cdot \Delta\psi_\mathrm{dc} \tag{4.240}$$

$$S_\mathrm{fl} = \frac{q \cdot \boldsymbol{\phi}_\mathbf{T}^2 \cdot \boldsymbol{\beta} \cdot I_\mathrm{DS}}{(f_\mathrm{op})^\mathbf{EF} \cdot C_\mathrm{ox} \cdot G_\mathrm{vsat,dc} \cdot N^*} \cdot \Bigg[(\mathbf{NFA} - \mathbf{NFB} \cdot N^* + \mathbf{NFC} \cdot N^{*\,2}) \cdot \ln\left(\frac{N^*_\mathrm{m} + \Delta N/2}{N^*_\mathrm{m} - \Delta N/2}\right) + \Big(\mathbf{NFB} + \mathbf{NFC} \cdot [N^*_\mathrm{m} - 2 \cdot N^*]\Big) \cdot \Delta N \Bigg] \tag{4.241}$$

$$H_0 = \frac{q^*_\mathrm{im,dc}}{\alpha_\mathrm{m,dc}} \tag{4.242}$$

$$t_1 = \frac{q_\mathrm{im,dc}}{q^*_\mathrm{im,dc}} \tag{4.243}$$

$$t_2 = \left(\frac{\Delta\psi_\mathrm{dc}}{12 \cdot H_0}\right)^2 \tag{4.244}$$

$$R = \frac{H_0}{H} - 1 \tag{4.245}$$

$$l_\mathrm{c} = 1 - 12 \cdot t_2 \cdot R \tag{4.246}$$

$$g_\mathrm{ideal} = \frac{\boldsymbol{\beta} \cdot q^*_\mathrm{im,dc}}{G_\mathrm{vsat,dc}} \cdot F_{\Delta L,\mathrm{dc}} \tag{4.247}$$

$$C_\mathrm{Geff} = \left(\frac{G_\mathrm{vsat,ac}}{G_\mathrm{mob,ac} \cdot G_{\Delta L,\mathrm{ac}}}\right)^2 \cdot C^\mathrm{qm}_\mathrm{OX} \cdot \eta_\mathrm{p,ac} \tag{4.248}$$

$$m_\mathrm{id} = \frac{g_\mathrm{ideal}}{l_\mathrm{c}^2} \cdot [t_1 + 12 \cdot t_2 - 24 \cdot (1 + t_1) \cdot t_2 \cdot R] \tag{4.249}$$

$$S_\mathrm{id} = \boldsymbol{N}_\mathbf{T} \cdot m_\mathrm{id} \tag{4.250}$$

$$m_\mathrm{ig} = \frac{1}{l_\mathrm{c}^2 \cdot g_\mathrm{ideal}} \cdot \left[\frac{t_1}{12} - t_2 \cdot \left(t_1 + \frac{1}{5} - 12 \cdot t_2\right) - \frac{8}{5} \cdot t_2 \cdot (t_1 + 1 - 12 \cdot t_2) \cdot R\right] \tag{4.251}$$

$$S_\mathrm{ig} = \boldsymbol{N}_\mathbf{T} \cdot \frac{(2 \cdot \pi \cdot f_\mathrm{op} \cdot C_\mathrm{Geff})^2 \cdot m_\mathrm{ig}}{1 + (2 \cdot \pi \cdot f_\mathrm{op} \cdot C_\mathrm{Geff} \cdot m_\mathrm{ig})^2} \tag{4.252}$$

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$$m_{\mathrm{igid}} = \frac{\sqrt{t_2}}{l_{\mathrm{c}}^2} \cdot \left[1 - 12 \cdot t_2 - \left(t_1 + \frac{96}{5} \cdot t_2 - 12 \cdot t_1 \cdot t_2\right) \cdot R\right] \tag{4.253}$$

$$S_{\mathrm{igid}} = \boldsymbol{N_{\mathrm{T}}} \cdot \frac{2 \cdot \pi \cdot j \cdot f_{\mathrm{op}} \cdot C_{\mathrm{Geff}} \cdot m_{\mathrm{igid}}}{1 + 2 \cdot \pi \cdot j \cdot f_{\mathrm{op}} \cdot C_{\mathrm{Geff}} \cdot m_{\mathrm{ig}}} \tag{4.254}$$

Gate current shot noise:

$$S_{\mathrm{igs}} = 2 \cdot q \cdot (I_{\mathrm{GCS}} + I_{\mathrm{GSov}}) \tag{4.255}$$

$$S_{\mathrm{igd}} = 2 \cdot q \cdot (I_{\mathrm{GCD}} + I_{\mathrm{GDov}}) \tag{4.256}$$

Avalanche current shot noise:

$$S_{\mathrm{avl}} = 2 \cdot q \cdot (1 + M_{\mathrm{avl}}) \cdot I_{\mathrm{avl}} \tag{4.257}$$

Thermal noise for parasitic resistances (see Fig. 3.2):

$$S_{\mathrm{R_G}} = 4 \cdot k_{\mathrm{B}} \cdot T_{\mathrm{KD}} / R_{\mathrm{gate}} \tag{4.258}$$

$$S_{\mathrm{R_{BULK}}} = 4 \cdot k_{\mathrm{B}} \cdot T_{\mathrm{KD}} / R_{\mathrm{bulk}} \tag{4.259}$$

$$S_{\mathrm{R_{WELL}}} = 4 \cdot k_{\mathrm{B}} \cdot T_{\mathrm{KD}} / R_{\mathrm{well}} \tag{4.260}$$

$$S_{\mathrm{R_{JUNS}}} = 4 \cdot k_{\mathrm{B}} \cdot T_{\mathrm{KD}} / R_{\mathrm{juns}} \tag{4.261}$$

$$S_{\mathrm{R_{JUND}}} = 4 \cdot k_{\mathrm{B}} \cdot T_{\mathrm{KD}} / R_{\mathrm{jund}} \tag{4.262}$$

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4.5 Self heating

Fig. 4.1 shows the simple thermal network that is implemented in PSP. The current that reflects the power dissipation is given by

$$P_{\rm diss} = I_{\rm DS} \cdot V_{\rm DS} + I_{\rm impact} \cdot (V_{\rm DS} + V_{\rm SB}) + \frac{V_{\rm SIS}^2}{R_{\rm source}} + \frac{V_{\rm DID}^2}{R_{\rm drain}}. \tag{4.263}$$

If **RTH** $< 10^{-3}$, $P_{\rm diss} = 0$. This can be used to switch off self heating.

The built-in thermal network of PSP can be bypassed (e.g., to replace it with an externally connected thermal network) by setting **CTH** $= 0$ and assigning a very large value to **RTH**.

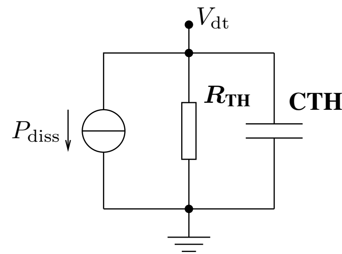

Figure 4.1: Internal thermal network of PSP

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Section 5

Non-quasi-static RF model

5.1 Introduction

For high-frequency modeling and fast transient simulations, a special version of the PSP model is available, which enables the simulation of non-quasi-static (NQS) effects, and includes several parasitic resistances.

5.2 NQS-effects

In the PSP-NQS model, NQS-effects are introduced by applying the one-dimensional current continuity equation ($\partial I/\partial y \propto -\partial\rho/\partial t$) to the channel. A full numerical solution of this equation is too inefficient for compact modeling, therefore an approximate technique is used. The channel is partitioned into $N+1$ sections of equal length by assigning N equidistant *collocation points*. The charge density (per unit channel area) along the channel is then approximated by a cubic spline through these collocation points, assuring that both the charge and its first and second spatial derivatives are continuous along the channel. Within this approximation, the current continuity equation reduces to a system of N coupled first order ordinary differential equations, from which the channel charge at each collocation point can be found:

$$\left\{\begin{array}{rcl} \dfrac{\mathrm{d}Q_1}{\mathrm{d}t} & = & f_1(Q_1,\ldots,Q_N) \\ \vdots & & \vdots \\ \dfrac{\mathrm{d}Q_N}{\mathrm{d}t} & = & f_N(Q_1,\ldots,Q_N) \end{array}\right. \tag{5.1}$$

Here, Q_i is the charge density at the i-th collocation point and f_i are functions, which contain the *complete* PSP-charge model. These equations are implemented by the definition of appropriate subcircuits (see left part of Fig. 5.1) and solved by the circuit simulator. Finally, the four terminal charges are calculated from the channel charges, using the Ward-Dutton partitioning scheme for the source and drain charges.

A full description of the PSP-NQS model is given in Section 5.3. More background information can be found in literature [7, 8].

5.3 NQS Model Equations

In this section, several symbols and notations are used which were defined in Section 4. Moreover, y denotes the (normalized) position along the channel ($y = 0$ is source side, $y = 1$ is drain side), while x denotes the surface potential (normalized to ϕ_T^*) at a certain position.

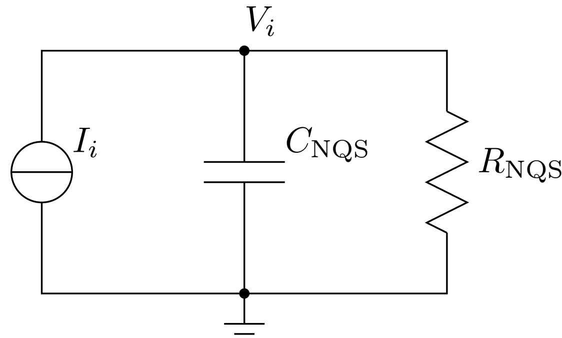

Figure 5.1: The subcircuit used to solve one of the differential equations of Eq. (5.1). The current is set to $I_i = C_{\rm NQS} \cdot f(V_1, \ldots, V_N)$, where the voltage V_i represents the charge density Q_i at the i-th collocation point and is solved by the circuit simulator. N of these circuits are defined and they are coupled through the dependence of I_i on the voltages of the other circuits. The resistance $R_{\rm NQS}$ has a very large value and is present only for convergence purposes. *Right:* The full network of parasitic elements in the PSP-NQS model. The large full dots indicate the five additional internal nodes.

5.3.1 Internal constants

Eqs. (5.2)–(5.7) are independent of bias conditions and time. Consequently, they have to be computed only once.

Note: In PSP only **SWNQS** $= 0, 1, 2, 3, 5, 9$ are allowed!

$$n = \textbf{SWNQS} + 1 \tag{5.2}$$

$$h = 1/n \tag{5.3}$$

The matrix A is a square $(n+1) \times (n+1)$-matrix with elements $A_{i,j}$ $(0 \le i, j \le n)$, which are used in Eq. 5.25. They are computed using the following algorithm (adapted from [9]):

1. Initial values:

$$A_{i,j} = 0 \qquad \text{for } 0 \le i, j \le n \tag{5.4}$$

$$v_i = 0 \qquad \text{for } 0 \le i \le n \tag{5.5}$$

2. First loop:

$$\left.\begin{aligned}
&p = 2 + v_{i-1}/2 \\
&v_i = -1/(2 \cdot p) \\
&A_{i,i-1} = 1/h \\
&A_{i,i} = -2/h \\
&A_{i,i+1} = 1/h \\
&A_{i,j} = \frac{1}{p} \cdot (3 \cdot A_{i,j}/h - A_{i-1,j}/2) \; \Big\} \text{for } j = 0 \ldots n
\end{aligned}\right\} \text{for } i = 1 \ldots (n-1) \tag{5.6}$$

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3. Second loop (back substitution):

$$\left.A_{i,j} = v_i \cdot A_{i+1,j} + A_{i,j} \qquad \text{for } j = 0 \ldots n \right\} \text{for } i = (n-1) \ldots 0 \tag{5.7}$$

5.3.2 Position independent quantities

The following quantities depend on the bias conditions, but are constant along the channel:

$$\text{if } x_{\mathrm{g,ac}} > 0 \begin{cases} y_{\mathrm{m}} = \dfrac{1}{2} \cdot \left(1 + \dfrac{\Delta\psi_{\mathrm{ac}}}{4 \cdot H_{\mathrm{ac}}}\right) \\[2ex] p_{\mathrm{d}} = \dfrac{x_{\mathrm{gm,ac}}}{x_{\mathrm{g,ac}} - x_{\mathrm{m,ac}}} \\[2ex] G_{\mathrm{p}} = G_{\mathrm{ac}}/p_{\mathrm{d}} \end{cases} \tag{5.8}$$

$$\text{if } x_{\mathrm{g,ac}} \leq 0 \begin{cases} y_{\mathrm{m}} = 1/2 \\ p_{\mathrm{d}} = 1 \\ G_{\mathrm{p}} = G_{\mathrm{ac}} \end{cases} \tag{5.9}$$

$$a_{\mathrm{p}} = 1 + G_{\mathrm{p}}/\sqrt{2} \tag{5.10}$$

$$p_{\mathrm{mrg}} = 10^{-5} \cdot a_{\mathrm{p}} \tag{5.11}$$

5.3.3 Position dependent surface potential and charge

Interpolated (quasi-static) surface potential along the channel:

$$\Psi(y) = x_{\mathrm{m,ac}} + \frac{H_{\mathrm{ac}}}{\boldsymbol{\phi}_{\mathbf{T}}^*} \cdot \left(1 - \sqrt{1 - \frac{2 \cdot \Delta\psi_{\mathrm{ac}}}{H_{\mathrm{ac}}} \cdot (y - y_{\mathrm{m}})}\right) \tag{5.12}$$

Normalized bulk-charge and its first two derivatives as functions of surface potential:

$$q_{\mathrm{b}}(x) = -\mathrm{sgn}(x) \cdot G_{\mathrm{p}} \cdot \sqrt{\exp(-x) + x - 1} \tag{5.13}$$

$$q_{\mathrm{b}}'(x) = \frac{G_{\mathrm{p}}^2 \cdot [1 - \exp(-x)]}{2 \cdot q_{\mathrm{b}}(x)} \tag{5.14}$$

$$q_{\mathrm{b}}''(x) = -q_{\mathrm{b}}'(x) - \frac{q_{\mathrm{b}}'(x)^2 - G_{\mathrm{p}}^2/2}{q_{\mathrm{b}}(x)} \tag{5.15}$$

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Surface potential as a function of normalized inversion charge (note that these equations are identical to Eq. (4.191), despite the different notation and physical background):

$$\Pi(x_\mathrm{g}) = \begin{cases} \text{if } x_\mathrm{g} < -p_\mathrm{mrg} & \begin{cases} y_\mathrm{g} = -x_\mathrm{g} \\ z = 1.25 \cdot y_\mathrm{g}/a_\mathrm{p} \\ \eta = \left[z + 10 - \sqrt{(z-6)^2 + 64}\right]/2 \\ a = (y_\mathrm{g} - \eta)^2 + G_\mathrm{p}^2 \cdot (\eta + 1) \\ c = 2 \cdot (y_\mathrm{g} - \eta) - G_\mathrm{p}^2 \\ \tau = -\eta + \ln\left(a/G_\mathrm{p}^2\right) \\ y_0 = \sigma_1(a,\, c,\, \tau,\, \eta) \\ \Delta_0 = \exp(y_0) \\ \xi = 1 - G_\mathrm{p}^2 \cdot \Delta_0/2 \\ p = 2 \cdot (y_\mathrm{g} - y_0) + G_\mathrm{p}^2 \cdot (\Delta_0 - 1) \\ q = (y_\mathrm{g} - y_0)^2 + G_\mathrm{p}^2 \cdot (y_0 - \Delta_0 + 1) \\ \Pi = -y_0 - \dfrac{2 \cdot q}{p + \sqrt{p^2 - 4 \cdot q \cdot \xi}} \end{cases} \\ \text{if } |x_\mathrm{g}| \le p_\mathrm{mrg} & \begin{cases} \Pi = \dfrac{x_\mathrm{g}}{a_\mathrm{p}} \end{cases} \\ \text{if } x_\mathrm{g} > p_\mathrm{mrg} & \begin{cases} \hat{x}_\mathrm{g1} = \boldsymbol{x_1} + G_\mathrm{p} \cdot \sqrt{\exp(-\boldsymbol{x_1}) + \boldsymbol{x_1} - 1} \\ \bar{x} = \dfrac{x_\mathrm{g}}{a_\mathrm{p}} \cdot [1 + x_\mathrm{g} \cdot (\boldsymbol{x_1} \cdot a_\mathrm{p}/\hat{x}_\mathrm{g1} - 1)/\hat{x}_\mathrm{g1}] \\ x_0 = x_\mathrm{g} + G_\mathrm{p}^2/2 - G_\mathrm{p} \cdot \sqrt{x_\mathrm{g} + G_\mathrm{p}^2/4 - 1 + \exp(-\bar{x})} \\ \Delta_0 = \exp(-x_0) \\ \xi = 1 - G_\mathrm{p}^2 \cdot \Delta_0/2 \\ p = 2 \cdot (x_\mathrm{g} - x_0) + G_\mathrm{p}^2 \cdot (1 - \Delta_0) \\ q = (x_\mathrm{g} - x_0)^2 - G_\mathrm{p}^2 \cdot (x_0 + \Delta_0 - 1) \\ \Pi = x_0 + \dfrac{2 \cdot q}{p + \sqrt{p^2 - 4 \cdot q \cdot \xi}} \end{cases} \end{cases} \tag{5.16}$$

$$X(x_\mathrm{g}, q_\mathrm{inv}) = \Pi(x_\mathrm{g} + q_\mathrm{inv}/p_\mathrm{d}) \tag{5.17}$$

Auxiliary functions:

$$q(x) = -p_\mathrm{d} \cdot (x_\mathrm{g} - x) - q_\mathrm{b}(x) \tag{5.18}$$

$$\psi(q, q_{x1}) = \frac{q}{q_{x1}} - 1 \tag{5.19}$$

$$\phi(q, q_{x1}, q_{x2}) = \left(1 - \frac{q \cdot q_{x2}}{q_{x1}^2}\right)/q_{x1} \tag{5.20}$$

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Normalized right-hand-side of continuity equation:

$$f(x_\mathrm{g}, q, q', q'') = \begin{cases} x_\mathrm{z} = X(x_\mathrm{g}, q) \\ q_{x1} = \dfrac{\partial q}{\partial x}(x_\mathrm{z}) = p_\mathrm{d} - q'_\mathrm{b}(x_\mathrm{z}) \\ q_{x2} = \dfrac{\partial^2 q}{\partial x^2}(x_\mathrm{z}) = q''_\mathrm{b}(x_\mathrm{z}) \\ f_0 = \psi(q, q_{x1}) \cdot q'' + \phi(q, q_{x1}, q_{x2}) \cdot q'^2 \\ x_{y1} = \dfrac{\partial x_\mathrm{z}}{\partial y} = q'/q_{x1} \\ z_\mathrm{sat} = \begin{cases} \left(\theta^*_\mathrm{sat,ac} \cdot \boldsymbol{\phi}^*_\mathbf{T} \cdot x_{y1}\right)^2 & \text{for NMOS} \\ \dfrac{\left(\theta^*_\mathrm{sat,ac} \cdot \boldsymbol{\phi}^*_\mathbf{T} \cdot x_{y1}\right)^2}{1 + \theta^*_\mathrm{sat,ac} \cdot \Delta\psi_\mathrm{ac}} & \text{for PMOS} \end{cases} \\ \zeta = \sqrt{1 + 2 \cdot z_\mathrm{sat}} \\ F_\mathrm{vsat} = 2/(1+\zeta) \\ f = F_\mathrm{vsat} \cdot \left[f_0 - F_\mathrm{vsat} \cdot \dfrac{z_\mathrm{sat}}{\zeta} \cdot \psi(q, q_{x1}) \cdot (q'' + x_{y1}^2 \cdot q''_\mathrm{b}(x_\mathrm{z}))\right] \end{cases} \quad (5.21)$$

Normalization constant:

$$T_\mathrm{norm} = \frac{\mathbf{MUNQS} \cdot \boldsymbol{\phi}^*_\mathbf{T} \cdot \boldsymbol{\beta}}{C^\mathrm{qm}_\mathrm{OX}} \cdot G_\mathrm{mob,ac} \cdot G_{\Delta L,\mathrm{ac}} \quad (5.22)$$

5.3.4 Cubic spline interpolation

Using cubic spline interpolation, the spatial derivatives $\frac{\partial q_i}{\partial y}(t)$ and $\frac{\partial^2 q_i}{\partial y^2}(t)$ can be expressed as functions of the $q_i(t)$.

$$q''_0 = 0 \quad (5.23)$$

$$q''_n = 0 \quad (5.24)$$

$$q''_i = \sum_{j=0}^{n} A_{i,j} \cdot q_i \qquad \text{for } 1 \le i \le n-1 \quad (5.25)$$

$$q'_i = \frac{q_{i+1} - q_i}{h} - \frac{h}{6} \cdot (2 \cdot q''_i + q''_{i+1}) \qquad \text{for } 1 \le i \le n-1 \quad (5.26)$$

5.3.5 Continuity equation

Initial value for the q_i ($0 \le i \le n$). These values are used for the DC operating point.

$$x_{i,0} = \Psi(i \cdot h) \quad (5.27)$$

$$q_{i,0} = q(x_{i,0}) \quad (5.28)$$

Note: $x_{0,0} = x_\mathrm{s}$ and $x_{n,0} = x_\mathrm{d}$. Moreover, these values coincide with those in the quasi-static part of PSP.

The core of the NQS-model is the solution of $q(y,t)$ from the charge continuity equation along the channel. By approximating the y-dependence by a cubic spline through a number of collocation points, the problem is reduced to solving the $q_i(t)$ from the following set of coupled differential equations.

$$\boxed{\begin{cases} \dfrac{\partial q_i}{\partial t}(t) + T_\mathrm{norm} \cdot f\left(x_\mathrm{g,ac},\, q_i(t),\, \dfrac{\partial q_i}{\partial y}(t),\, \dfrac{\partial^2 q_i}{\partial y^2}(t)\right) = 0 & \text{for } 1 \le i \le n-1 \\ q_i(0) = q_{i,0} & \end{cases}} \tag{5.29}$$

Note that the boundary points $q_0(t) = q(x_\mathrm{s}) = q_\mathrm{is}$ and $q_n(t) = q(x_\mathrm{d}) = q_\mathrm{id}$ remain fixed to their quasi-static values; they are not solved from the equation above.

The set of differential equations defined above is solved by the circuit simulator via the subcircuits shown in the left part of Fig. 5.1.

5.3.6 Non-quasi-static terminal charges

Once the q_i are known, the NQS terminal charges can be computed:

$$S_0 = \sum_{i=1}^{n-1} q_i \tag{5.30}$$

$$S_2 = \sum_{i=1}^{n-1} q_i'' \tag{5.31}$$

$$q_\mathrm{I}^\mathrm{NQS} = \int_0^1 q(y)\,\mathrm{d}y = h \cdot S_0 + \frac{h}{2} \cdot (u_0 + u_n) - \frac{h^3}{12} \cdot S_2 \tag{5.32}$$

$$U_0 = \sum_{i=1}^{n-1} i \cdot q_i \tag{5.33}$$

$$U_2 = \sum_{i=1}^{n-1} i \cdot q_i'' \tag{5.34}$$

$$q_\mathrm{D}^\mathrm{NQS} = \int_0^1 y \cdot q(y)\,\mathrm{d}y = h^2 \cdot U_0 + \frac{h^2}{6} \cdot [q_0 + (3n-1)u_n] - \frac{h^4}{12} \cdot U_2 \tag{5.35}$$

$$q_\mathrm{S}^\mathrm{NQS} = q_\mathrm{I}^\mathrm{NQS} - q_\mathrm{D}^\mathrm{NQS} \tag{5.36}$$

Currently, only **SWNQS** $= 0, 1, 2, 3, 5, 9$ are allowed. For odd values of **SWNQS** the gate charge is integrated along the channel using "Simpson's rule". If **SWNQS** $= 2$, "Simpson's $3/8$-rule" is used.

- If **SWNQS** is odd (that is, n is even):

$$q_\mathrm{G}^\mathrm{NQS} = p_\mathrm{d} \cdot \left[x_\mathrm{g,ac} - \frac{h}{3} \cdot \left(X(x_\mathrm{g,ac}, q_0) + 4 \cdot \sum_{i=1}^{n/2} X(x_\mathrm{g,ac}, q_{2i-1}) + 2 \cdot \sum_{i=1}^{n/2-1} X(x_\mathrm{g,ac}, q_{2i}) + X(x_\mathrm{g,ac}, q_n)\right)\right] \tag{5.37}$$

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- If **SWNQS** $= 2$ (that is, $n = 3$):

$$q_{\mathrm{G}}^{\mathrm{NQS}} = p_{\mathrm{d}} \cdot \left[x_{\mathrm{g,ac}} - \frac{3 \cdot h}{8} \cdot \left(X(x_{\mathrm{g,ac}}, q_0) + 3 \cdot X(x_{\mathrm{g,ac}}, q_1) + 3 \cdot X(x_{\mathrm{g,ac}}, q_2) + X(x_{\mathrm{g,ac}}, q_3) \right) \right] \quad (5.38)$$

Convert back to conventional units:

$$Q_{\mathrm{S}}^{\mathrm{NQS}} = C_{\mathrm{OX}}^{\mathrm{qm}} \cdot \boldsymbol{\phi}_{\mathbf{T}}^{*} \cdot q_{\mathrm{S}}^{\mathrm{NQS}} \quad (5.39)$$

$$Q_{\mathrm{D}}^{\mathrm{NQS}} = C_{\mathrm{OX}}^{\mathrm{qm}} \cdot \boldsymbol{\phi}_{\mathbf{T}}^{*} \cdot q_{\mathrm{D}}^{\mathrm{NQS}} \quad (5.40)$$

$$Q_{\mathrm{G}}^{\mathrm{NQS}} = C_{\mathrm{OX}}^{\mathrm{qm}} \cdot \boldsymbol{\phi}_{\mathbf{T}}^{*} \cdot q_{\mathrm{G}}^{\mathrm{NQS}} \quad (5.41)$$

$$Q_{\mathrm{B}}^{\mathrm{NQS}} = -(Q_{\mathrm{S}}^{\mathrm{NQS}} + Q_{\mathrm{D}}^{\mathrm{NQS}} + Q_{\mathrm{G}}^{\mathrm{NQS}}) \quad (5.42)$$

Section 6

Embedding

6.1 Model selection

Circuit simulators have different ways for the user to determine which model must be used for simulation. Typically, model selection is either done by *name* or by assigning a value to the parameter **LEVEL**. The method to be used is prescribed by the circuit simulator vendor. If selection is done by name, the value of the parameter **LEVEL** is generally ignored. When Verilog-A code is used, model selection is always done by name.

For the SiMKit and the Verilog-A code provided by the PSP model developers, the method and values to be used are given in the table below. For other implementations, the method/value provided by the circuit simulator vendor is to be used.

From PSP 103.0 onwards, the global, local and binning models are unified. All three models are called by the same *name* or **LEVEL**. Model flavor selection is done by setting parameter **SWGEO**.

Simulator	Model selection by	Global (geom.)	Global (binning)	Local
Spectre	`psp103`	**SWGEO** $= 1$	**SWGEO** $= 2$	**SWGEO** $= 0$
Pstar	**LEVEL** $= 103$			
ADS	`psp103`			
Verilog-A	`PSP103VA`			

6.2 Case of parameters

Throughout this document, all parameter names are printed in uppercase characters. Similarly, in the Verilog-A code provided by the PSP model developers, the parameters are in upper case characters. However, in other PSP implementations a different choice can be made. For example, the parameter names may be in lowercase characters (possibly first character capitalized) if this is conform the conventions of the circuit simulator.

6.3 Embedding PSP in a Circuit Simulator

In CMOS technologies both n- and p-channel MOS transistors are supported. It is convenient to use the same set of equations for both types of transistor instead of two separate models. This is accomplished by mapping a p-channel device with its bias conditions and parameter set onto an equivalent n-channel device with appropriately changed bias conditions (i.e. currents, voltages and charges) and parameters. In this way both types of transistor can be treated internally as an n-channel transistor. Nevertheless, the electrical behavior

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of electrons and holes is not exactly the same (e.g., the mobility and tunneling behavior), and consequently slightly different equations have to be used in case of n- or p-type transistors.

Designers are used to the standard terminology of source, drain, gate and bulk. Therefore, in the context of a circuit simulator it is traditionally possible to address, say, the drain of MOST number 17, even if in reality the corresponding source is at a higher potential (n-channel case). More strongly, most circuit simulators provide for model evaluation values for $V_{\rm DS}$, $V_{\rm GS}$, and $V_{\rm SB}$ based on an a priori assignment of source, drain, and bulk, independent of the actual bias conditions. Since PSP assumes that saturation occurs at the drain side of the MOSFET, the basic model cannot cope with bias conditions that correspond to $V_{\rm DS} < 0$. Again a transformation of the bias conditions is necessary. In this case, the transformation corresponds to internally reassigning source and drain, applying the standard electrical model, and then reassigning the currents and charges to the original terminals. In PSP care has been taken to preserve symmetry with respect to drain and source at $V_{\rm DS} = 0$. In other words, no singularities will occur in the higher-order derivatives at $V_{\rm DS} = 0$.

In detail, for correct embedding of PSP into a circuit simulator, the following procedure—illustrated in Fig. 6.1—is followed. It is assumed that the simulator provides the nodal potentials $V_{\rm D}^e$, $V_{\rm G}^e$, $V_{\rm S}^e$ and $V_{\rm B}^e$ based on an a priori assignment of drain, gate, source and bulk.

Step 1 The voltages $V'_{\rm DS}$, $V'_{\rm GS}$, and $V'_{\rm SB}$ are calculated from the nodal potentials provided by the circuit simulator. In the same step, the value of the parameter **TYPE** is used to deal with the polarity of the device. From here onwards, all transistors can be treated as n-channel devices.

Step 2 Depending on the sign of $V'_{\rm DS}$, 'source-drain interchange' is performed. At this level, the voltages comply to all the requirements for input quantities of PSP.

Step 3 All the internal output quantities (i.e. channel current, weak-avalanche current, gate current, nodal charges, and noise-power spectral densities) are evaluated using the standard PSP equations (Section 4) and the internal voltages.

Step 4 The internal output quantities are corrected for a possible source-drain interchange.

Step 5 External output are corrected for a possible p-channel transformation and **MULT** is applied. The quantities of the intrinsic MOSFET and the junctions are combined.

In general, separate parameter sets are used for n- and p-channel transistors, which are distinguished by the value of **TYPE**. As a consequence, the changes in the parameter values necessary for a p-channel type transistor are normally already included in the parameter sets on file. The changes should therefore not be included in the simulator.

6.3.1 Selection of device type

In the SiMKit-based and built-in version of PSP in certain circuit simulators, the selection of device type (nmos or pmos) is done using a different parameter, or using different parameter values. The correct values for some circuit simulators are given in the table below.

Simulator	Parameter	Value NMOS	value PMOS
Spectre	`type`	n	p
Pstar	`type`	1	-1
ADS	`gender`	1	0
Verilog-A	`TYPE`	1	-1

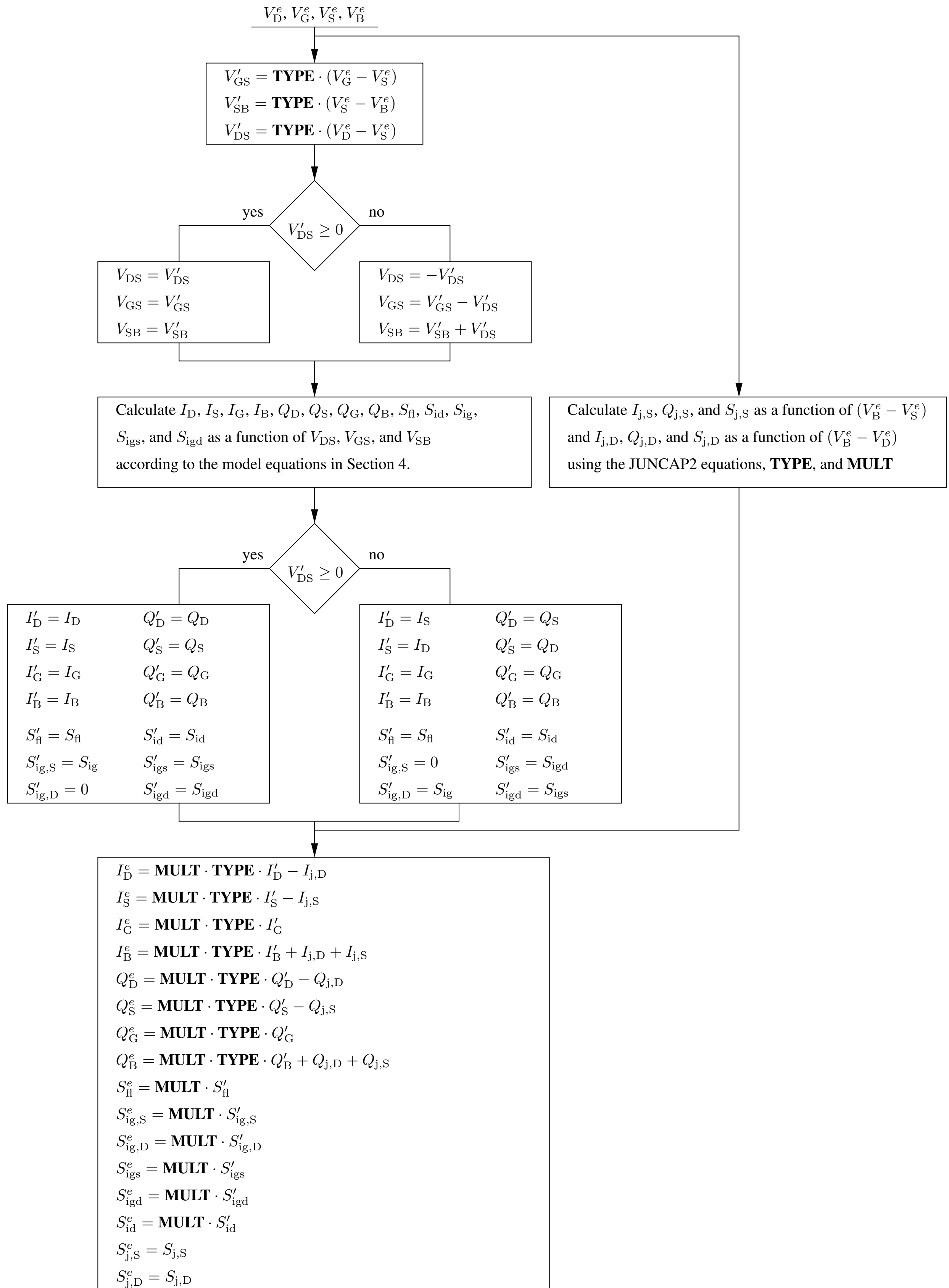

Figure 6.1: Schematic overview of source-drain interchange and handling of **TYPE** and **MULT**. Note that **TYPE** and **MULT** are included in the JUNCAP2 model equations.

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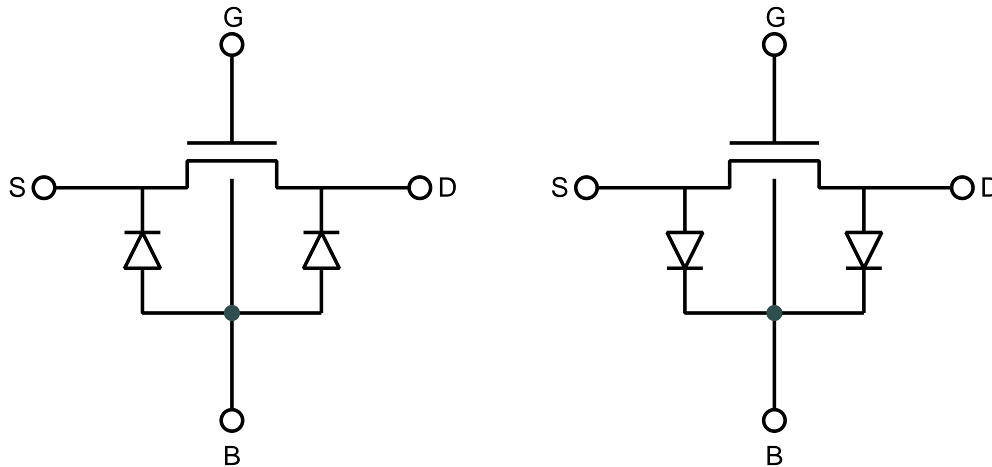

Figure 6.2: Topology of the PSP model. *Left:* n-channel MOSFET; *Right:* p-channel MOSFET. In PSP, the correct diode polarity is automatically chosen via the **TYPE**-parameter.

6.4 Integration of JUNCAP2 in PSP

Introduction

The JUNCAP2 model 200.3 is an integral part of PSP 102.2. In addition, it is available as a stand-alone model. A complete description of the JUNCAP2-model (including all model equations) can be found in the documentation of JUNCAP2's stand alone version [10]. In this section, only the integration of JUNCAP2 in PSP is described.

Topology

In a MOS transistor, there are two junctions: one between source and bulk, and one between drain and bulk. In case of an n-channel MOSFET, the junction anode corresponds to the MOSFET bulk terminal, and the junction cathodes correspond to the source and the drain. In case of a p-channel MOSFET, it is the other way around: now the junction cathode corresponds to the MOSFET bulk terminal, and the junction anodes correspond to the source and the drain. The connections are schematically given in Fig. 6.2. In PSP, this change of junction terminal connections in case of a p-MOSFET is handled automatically via the **TYPE** parameter.

In most cases, the MOSFET is operated in such a way that the junctions are either biased in the reverse mode of operation or not biased at all. In some applications, however, the source-bulk junction has a small forward bias. This is also the case in partially depleted SOI (PDSOI).

As indicated in Fig. 6.1, the interchange of source and drain for $V_{\rm DS} < 0$ (as explained above for the intrinsic MOS model) does *not* apply to the junctions. For example, **ABDRAIN** always refers to junction between the bulk and the terminal known as 'drain' to the simulator, independent of the sign of $V_{\rm DS}$.

Global and local model level

As explained in the introduction, the PSP model has a local and a global level. The JUNCAP2 model is a geometrically scaled model, i.e. it is valid for a range of junction geometries (as described by the geometrical parameters **AB**, **LS**, and **LG**). It has turned out that it is very unnatural to create a local parameter set for JUNCAP2, valid for one particular junction geometry: such a parameter set would have as many parameters as the global parameter set, and would be of no use. (Note that, in contrast, the local model for the intrinsic MOSFET is very useful in, e.g., parameter extraction; this is not the case for JUNCAP2.)

Therefore, the JUNCAP2 model is connected in exactly the same way to both the local and global model levels of PSP. That means that the resulting PSP local model is valid for a MOSFET with one particular channel width

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and length, but with arbitrary junction geometry.

Parameters

Both junctions in the MOSFET are modeled with the same set of JUNCAP2 parameters. In the PSP model, the geometrical parameters **AB**, **LS**, and **LG** need to be specified for both source and drain. They will be denoted as **ABSOURCE**, **LSSOURCE**, and **LGSOURCE** for the source junction, and **ABDRAIN**, **LSDRAIN**, and **LGDRAIN** for the drain junction. For compatibility with BSIM instance parameters, there is also an option to use **AS**, **AD**, **PS**, and **PD**. The complete list of instance parameters (PSP and JUNCAP2) can be found in Sections 2.5.1.

The parameter **MULT** is merged with the parameter **MULT** of the intrinsic MOSFET model. In other words, both intrinsic currents, charges, and noise as well as junction currents, charges and noise are multiplied by one single parameter **MULT**. Beside **MULT**, also the parameters **DTA** and **TYPE** are shared by the intrinsic MOSFET model and the junction model. For clarity, we mention here that the reference temperatures of the intrinsic MOSFET model and junction model are *not* merged; they each have their own value and name (**TR** and **TRJ**, respectively). The currents, charges and spectral noise densities of the source and drain junctions are labeled $I_{\mathrm{j,S}}$, $Q_{\mathrm{j,S}}$, $S_{\mathrm{j,S}}$, $I_{\mathrm{j,D}}$, $Q_{\mathrm{j,D}}$, and $S_{\mathrm{j,D}}$ in Fig. 6.1.

6.5 Verilog-A versus C

As mentioned in Section 1.3, two implementations of the PSP-model are distributed: in Verilog-A language and in C-language (as part of the SiMKit). The C-version is automatically generated from the Verilog-A version by a software package called ADMS [1]. This procedure guarantees that the two implementations contain identical model equations.

Nevertheless, there are a few minor differences between the two, which are due to certain limitations of either the Verilog-A language or the circuit simulators supported in the SiMKit-framework. These differences are described below.

6.5.1 Implementation of GMIN

In both implementations, there is an additional term in Eqs. (4.219) and (4.220), resulting in

$$I_{\mathrm{D}} = I_{\mathrm{DS}} + I_{\mathrm{avl}} - I_{\mathrm{GDov}} - I_{\mathrm{GCD}} + I_{\mathrm{gidl}} + G_{\mathrm{min}} \cdot V_{\mathrm{DS}} \tag{6.1}$$

and

$$I_{\mathrm{S}} = -I_{\mathrm{DS}} - I_{\mathrm{GSov}} - I_{\mathrm{GCS}} + I_{\mathrm{gisl}} - G_{\mathrm{min}} \cdot V_{\mathrm{DS}}. \tag{6.2}$$

In the SiMKit, G_{min} is a variable which is accessible by the circuit simulator. This allows the circuit simulator to improve the convergence properties of a circuit by making use of so-called 'G_{min}-stepping'.

In the Verilog-A version of PSP, G_{min} is set to a fixed value $G_{\mathrm{min}} = 1 \cdot 10^{-15}$ S.[1]

6.5.2 Implementation of parasitic resistances

From PSP 102.2 and PSP 103.0 onwards, a network of parasitic resistors has been inserted around the intrinsic MOSFET. If the user sets one or more of these resistance values to zero, the associated internal node(s) could be shorted to one of its neighbors, reducing the size of the matrix in the circuit simulator. This phenomenon is called 'node collapse' and is supported by most major circuit simulators.

[1] If supported by the circuit simulator, Verilog-A version 2.2 allows the value of G_{min} to be accessed by the circuit simulator. Once this feature is generally available in Verilog-A compilers, it will be included in PSP as well.

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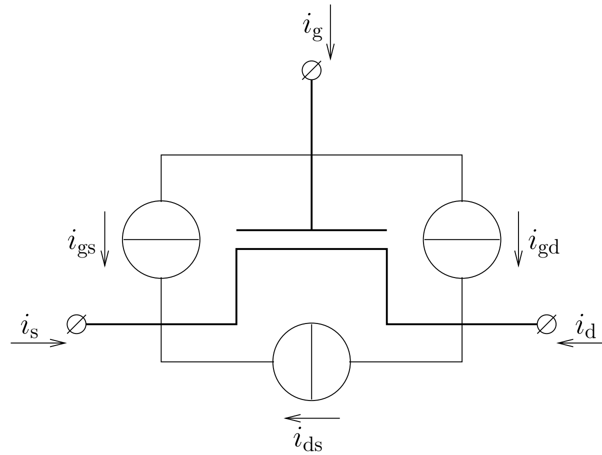

Figure 6.3: Definition of noise currents.

Flexible topology (and thus node collapse) is presently supported by most Verilog-A compilers. As a result, node collapse is functional in the official PSP Verilog-A in the majority of today's circuit simulators.

From SiMKit 3.0 onwards, the SiMKit architecture allows for flexible topologies and therefore supports node collapse in PSP. This functionality is therefore available in circuit simulations with that can work with SiMKit. Besides, many circuit simulators that have a native implementation of PSP support node collapse.

6.5.3 Implementation of the noise-equations

Definition of noise model

Eqs. (4.250), (4.252), and (4.254) describe the noise power spectral density of the thermal noise. In this section, the relationship between the quantities $S_{\rm id}$, $S_{\rm ig}$, and $S_{\rm igid}$ (as calculated in these equations) and noise sources in the model is defined.

Fig. 6.3 shows a schematic representation of a noiseless transistor (model) and three noise sources. The small-signal noise currents of these noise current sources are indicated by $i_{\rm ds}$, $i_{\rm gs}$, and $i_{\rm gd}$. The two noise sources connected to G are fully correlated. Moreover, each of them is partly correlated with the noise source between S and D. More precisely, the noise powers and correlations associated with these sources are given by

$$\begin{aligned}
\langle i_{\rm ds} \cdot i_{\rm ds}^* \rangle &= S_{\rm id} \\
\langle i_{\rm gd} \cdot i_{\rm ds}^* \rangle &= S_{\rm igid}/2 \\
\langle i_{\rm gs} \cdot i_{\rm ds}^* \rangle &= S_{\rm igid}/2 \\
\langle i_{\rm gd} \cdot i_{\rm gd}^* \rangle &= S_{\rm ig}/4 \\
\langle i_{\rm gs} \cdot i_{\rm gd}^* \rangle &= S_{\rm ig}/4 \\
\langle i_{\rm gs} \cdot i_{\rm gs}^* \rangle &= S_{\rm ig}/4
\end{aligned} \tag{6.3}$$

The non-listed elements follow from the fact that this is a complex correlation matrix and therefore self-adjoint. This defines the noise model of PSP.

For completeness, we will give the noise correlation matrix associated with the *terminal* currents $i_{\rm d}$, $i_{\rm g}$ and $i_{\rm s}$, because it is closer related to the numbers that are obtained in a circuit simulation. Because $i_{\rm d} = i_{\rm ds} - i_{\rm gs}$,

$i_{\rm g} = i_{\rm gs} + i_{\rm gd}$ and $i_{\rm s} = i_{\rm gs} - i_{\rm ds}$, we find by straightforward substitution and some basic arithmetic

$$\begin{aligned} \langle i_{\rm d} \cdot i_{\rm d}^* \rangle &= S_{\rm id} + S_{\rm ig}/4 - {\rm Re}(S_{\rm igid}) \\ \langle i_{\rm g} \cdot i_{\rm d}^* \rangle &= S_{\rm igid} - S_{\rm ig}/2 \\ \langle i_{\rm s} \cdot i_{\rm d}^* \rangle &= -S_{\rm id} + S_{\rm ig}/4 - {\rm Im}(S_{\rm igid}) \\ \langle i_{\rm g} \cdot i_{\rm g}^* \rangle &= S_{\rm ig} \\ \langle i_{\rm s} \cdot i_{\rm g}^* \rangle &= -S_{\rm igid}^* - S_{\rm ig}/2 \\ \langle i_{\rm s} \cdot i_{\rm s}^* \rangle &= S_{\rm id} + S_{\rm ig}/4 + {\rm Re}(S_{\rm igid}) \end{aligned} \tag{6.4}$$

Verilog-A

In Verilog-A it is not possible to define noise sources that are frequency dependent (except for $1/f$-noise), nor is it possible to directly define correlations between noise sources. Instead, the desired model must be created by using controlled sources and the frequency transfer of passive elements.[2]

The goal is to create the three noise sources shown in Fig. 6.3 with the noise powers (including frequency dependence and correlation) as described by Eq. (6.3).

To simplify notation, we rewrite Eqs. (4.252) and (4.254) as

$$S_{\rm ig} = \frac{\boldsymbol{N_{\rm T}}}{m_{\rm ig}} \cdot |T|^2 \tag{6.5}$$

and

$$S_{\rm igid} = \frac{\boldsymbol{N_{\rm T}}}{m_{\rm ig}} \cdot m_{\rm igid} \cdot T, \tag{6.6}$$

where

$$T = \frac{j \cdot \omega \cdot \tau}{1 + j \cdot \omega \cdot \tau}, \tag{6.7}$$

$\tau = m_{\rm ig} \cdot C_{\rm Geff}$ and ω is the operating frequency.

Correlation between noise sources in verilog-A can be created by making linear combinations of independent sources. Therefore, we start with two *independent* white noise sources with current noise spectral densities S_1 and S_2 and noise currents i_1 and i_2. If we set

$$i_{\rm gs} = i_{\rm gd} = \frac{1}{2} \cdot \alpha_1 \cdot i_1 \tag{6.8}$$

$$i_{\rm ds} = \beta_1 \cdot i_1 + \beta_2 \cdot i_2, \tag{6.9}$$

where α_1, β_1, and β_2 are certain (complex) coefficients, we get

$$\begin{aligned} S_{\rm ig} &= 4 \cdot \langle i_{\rm gd} \cdot i_{\rm gd}^* \rangle = |\alpha_1|^2 \cdot \langle i_1 \cdot i_1^* \rangle \\ &= |\alpha_1|^2 \cdot S_1 \end{aligned} \tag{6.10}$$

$$\begin{aligned} S_{\rm id} &= \langle i_{\rm ds} \cdot i_{\rm ds}^* \rangle = |\beta_1|^2 \cdot \langle i_1 \cdot i_1^* \rangle + \beta_1 \cdot \beta_2^* \cdot \langle i_1 \cdot i_2^* \rangle + |\beta_2|^2 \cdot \langle i_2 \cdot i_2^* \rangle \\ &= |\beta_1|^2 \cdot S_1 + |\beta_2|^2 \cdot S_2 \end{aligned} \tag{6.11}$$

$$\begin{aligned} S_{\rm igid} &= 2 \cdot \langle i_{\rm gd} \cdot i_{\rm ds}^* \rangle = \alpha_1 \cdot \beta_1^* \cdot \langle i_1 \cdot i_1^* \rangle + \alpha_1 \cdot \beta_2^* \cdot \langle i_1 \cdot i_2^* \rangle \\ &= \alpha_1 \cdot \beta_1^* \cdot S_1. \end{aligned} \tag{6.12}$$

Here we used that the noise currents i_1 and i_2 are independent, such that $\langle i_1 \cdot i_2^* \rangle = 0$. We need to choose proper values for the coefficients α_1, β_1 and β_2, as well as S_1 and S_2, such that $S_{\rm ig}$, $S_{\rm id}$, and $S_{\rm igid}$ get the correct value.

[2] Although this appears to be a limitation, it is in fact very helpful to ensure that the resulting noise model is consistent with time-domain simulations.

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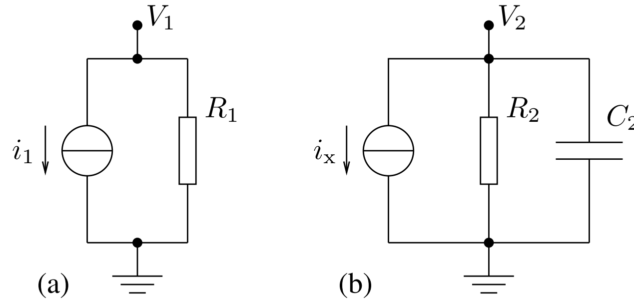

Figure 6.4: The two subcircuits used in PSP's Verilog-A implementation to model the correct frequency dependence of induced gate noise and its correlation with the channel thermal noise.

There is some freedom in choosing the numbers; the values that are used in the verilog-A implementation of PSP are

$$\alpha_1 = T \tag{6.13}$$
$$\beta_1 = m_{\text{igid}} \tag{6.14}$$
$$\beta_2 = 1 \tag{6.15}$$
$$S_1 = \boldsymbol{N_\text{T}}/m_{\text{ig}} \tag{6.16}$$
$$S_2 = \boldsymbol{N_\text{T}} \cdot (1 - C_{\text{igid}}^2) \cdot m_{\text{id}}, \tag{6.17}$$

where

$$C_{\text{igid}} = \frac{m_{\text{igid}}}{\sqrt{m_{\text{ig}} \cdot m_{\text{id}}}}, \tag{6.18}$$

and m_{id}, m_{ig}, and m_{igid} are given by Eqs. (4.249), (4.251), and (4.253), respectively.

To achieve this, we make use of the subcircuits depicted in Fig. 6.4. The first subcircuit (a) contains a parallel connection of a white noise source with current small-signal noise current i_1 and a resistor R_1. The voltage over the elements is denoted by V_1. The second subcircuit (b) contains a voltage-controlled current source with current i_x, a resistor R_2, and a capacitor C_2. The nodal voltage is denoted by V_2.

The parameters of these components are given by

$$S_1 = \langle i_1 \cdot i_1^* \rangle = S_{\text{ig}}^0 \cdot s_\text{f}^2 \tag{6.19}$$
$$R_1 = 1\,\Omega \tag{6.20}$$
$$i_\text{x} = -V_1/s_\text{f} \tag{6.21}$$
$$R_2 = m_{\text{ig}} \tag{6.22}$$
$$C_2 = C_{\text{Geff}} \tag{6.23}$$

where the values of C_{Geff} is given by Eqs. (4.248) and

$$S_{\text{ig}}^0 = \frac{\boldsymbol{N_\text{T}}}{m_{\text{ig}}}. \tag{6.24}$$

Moreover, we introduce a scaling factor $s_\text{f} = \omega_0 \cdot m_{\text{ig}} \cdot C_{\text{Geff}}$ with $\omega_0 = 1$ MHz. Note that the value of s_f and ω_0 do not affect the final result, but help to give the noise power of V_1 a reasonable value.

Choosing the elements in this way, creates a frequency dependent current i_C through the capacitor C_2 given by

$$i_C = T \cdot i_\text{x}. \tag{6.25}$$

The two noise sources connected to the gate in Fig. 6.3 are now realized as two current-controlled current sources with

$$i_{\mathrm{gd}} = i_{\mathrm{gs}} = \frac{1}{2} \cdot i_C. \tag{6.26}$$

The third source in Fig. 6.3 (between source and drain) is realized by putting two elements in parallel:

- A voltage controlled current source with value $(m_{\mathrm{igid}}/s_{\mathrm{f}}) \cdot V_1$ and
- A white noise source with current power spectral density $S_2 = \boldsymbol{N_{\mathrm{T}}} \cdot (1 - C_{\mathrm{igid}}^2) \cdot m_{\mathrm{id}}$.

To complete the model, we remark that from Fig. 6.3 it is clear that source-drain interchange only affects the sign of i_{ds}.

In summary, the relevant portion of the verilog-A implementation is given by (mult-scaling and labels are not included for clarity):

```
electrical NOI;
electrical NOI2;

branch (NOI) NOII;
branch (NOI) NOIR;
branch (NOI) NOIC;

// subcircuit (a)
I(NOI2)   <+  V(NOI2);
I(NOI2)   <+  white_noise(sqig * sqig * sf * sf);

// subcircuit (b)
I(NOII)   <+  -V(NOI2) / sf;
I(NOIR)   <+  V(NOIR) / mig;
I(NOIC)   <+  ddt(CGeff * V(NOIC));

// noise sources ids, igs, and igd
I(DI,SI)  <+  white_noise(sqid * sqid * (1.0 - c_igid * c_igid));
I(DI,SI)  <+  sigVds * migid * V(NOI2) / sf;
I(GP,SI)  <+  ddt(0.5 * CGeff * V(NOIC));
I(GP,DI)  <+  ddt(0.5 * CGeff * V(NOIC));
```

It is straightforward to verify that this implementation of PSP's noise model in Verilog-A naturally yields the desired correlations and frequency dependence. However, it requires two additional internal nodes.

SiMKit C-code

Contrary to the limitation of Verilog-A language, most circuit simulators are able to directly deal with correlated and frequency dependent noise—without the use of additional internal nodes. In order to minimize the simulation time of the model, C-implementations should therefore avoid the use of such internal nodes whenever possible.

In SiMKit, the frequency dependence and correlation of the noise sources indicated in Fig. 6.3 are implemented directly according to Eq. (6.3). The result is therefore equivalent to the verilog-A implementation.

In summary, even though the SiMKit-implementation of the noise model in PSP is different from that in verilog-A (as it does not make use of additional internal nodes) the result of noise noise simulations will be identical.

6.5.4 Clip warnings

From SiMKit 3.7 onwards, it is possible to set the level of clip-warning information through the value of the parameter **PARAMCHK**. This functionality is available for most SiMKit models. It is *not* available in the verilog-A version of PSP.

If the value of **PARAMCHK** is

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< 0 All clip warnings are suppressed.

≥ 0 (default) Clip warnings for instance parameters.

≥ 1 Clip warnings for model parameters.

≥ 2 Clip warnings for internally computed local parameters during model initialization.

≥ 3 Clip warnings for internally computed local parameters during model evaluation.

This works in an accumulative manner: if a higher value of **PARAMCHK** is used, the warnings associated with lower levels are still included. Note that the highest level is of interest only for self heating models, where electrical parameters may change dependent on temperature. Also note that the default value (0) results in less clip warnings than in earlier versions of the model.

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Section 7

Parameter extraction

The parameter extraction strategy for PSP consists of four main steps:

1. Measurements
2. Extraction of local parameters at room temperature
3. Extraction of temperature scaling parameters
4. Extraction of geometry scaling (global) parameters

The above steps will be briefly described in the following sections. Note that the description of the extraction procedure is not ‘complete’ in the sense that only the most important parameters are discussed and in cases at hand it may be advantageous (or even necessary) to use an adapted procedure.

Throughout this section, bias and current conditions are given for an n-channel transistor only; for a p-channel transistor, all voltages and currents should be multiplied by -1.

As explained in the introduction, the hierarchical setup of PSP (local and global level) allows for the two-step parameter extraction procedure described in this section; this is the recommended method of operation. Nevertheless, it is possible to skip the first steps and start extracting global parameters directly. This procedure is not described here, but the directions below may still be useful.

7.1 Measurements

The parameter extraction routine consists of six different DC-measurements (two of which are optional) and two capacitance measurements.[1] Measurement V and VI are only used for extraction of gate-current, avalanche, and GIDL/GISL parameters.

- **Measurement I** (“idvg”): $I_{\rm D}$ vs. $V_{\rm GS}$
  $V_{\rm GS} = 0 \ldots V_{\rm sup}$ (with steps of maximum 50 mV).
  $V_{\rm DS} = 25$ or 50 mV
  $V_{\rm BS} = 0 \ldots -V_{\rm sup}$ (3 or more values)

- **Measurement II** (“idvgh”): $I_{\rm D}$ vs. $V_{\rm GS}$
  $V_{\rm GS} = 0 \ldots V_{\rm sup}$ (with steps of maximum 50 mV).
  $V_{\rm DS} = V_{\rm sup}$
  $V_{\rm BS} = 0 \ldots -V_{\rm sup}$ (3 or more values)

[1] The bias conditions to be used for the measurements are dependent on the supply voltage of the process. Of course it is advisable to restrict the range of voltages to this supply voltage $V_{\rm sup}$. Otherwise physical effects atypical for normal transistor operation—and therefore less well described by PSP—may dominate the characteristics.

- **Measurement III** (“idvd”): $I_{\rm D}$ vs. $V_{\rm DS}$
  $V_{\rm GS} = 0 \ldots V_{\rm sup}$ (3 or more values)
  $V_{\rm DS} = 0 \ldots V_{\rm sup}$ (with steps of maximum 50 mV).
  $V_{\rm BS} = 0$ V

- **Measurement IV** (“idvdh”, optional):$I_{\rm D}$ vs. $V_{\rm DS}$
  $V_{\rm GS} = 0 \ldots V_{\rm sup}$ (3 or more values)
  $V_{\rm DS} = 0 \ldots V_{\rm sup}$ (with steps of maximum 50 mV).
  $V_{\rm BS} = -V_{\rm sup}$

- **Measurement V** (“igvg”): $I_{\rm G}$ and $I_{\rm B}$ vs. $V_{\rm GS}$
  $V_{\rm GS} = -V_{\rm sup} \ldots V_{\rm sup}$ (with steps of maximum 50 mV).
  $V_{\rm DS} = 0 \ldots V_{\rm sup}$ (3 or more values)
  $V_{\rm BS} = 0$ V

- **Measurement VI** (“igvgh”, optional): $I_{\rm G}$ and $I_{\rm B}$ vs. $V_{\rm GS}$
  $V_{\rm GS} = -V_{\rm sup} \ldots V_{\rm sup}$ (with steps of maximum 50 mV).
  $V_{\rm DS} = 0 \ldots V_{\rm sup}$ (3 or more values)
  $V_{\rm BS} = -V_{\rm sup}$

- **Measurement VII** (“cggvg”): $C_{\rm GG}$ vs. $V_{\rm GS}$
  $V_{\rm GS} = -V_{\rm sup} \ldots V_{\rm sup}$ (with steps of maximum 50 mV).
  $V_{\rm DS} = 0$ V
  $V_{\rm BS} = 0$ V

- **Measurement VIII** (“ccgvg”): $C_{\rm CG}$ vs. $V_{\rm GS}$
  $V_{\rm GS} = -V_{\rm sup} \ldots V_{\rm sup}$ (with steps of maximum 50 mV).
  $V_{\rm DS} = 0$ V
  $V_{\rm BS} = 0$ V

For the extraction procedure, the transconductance $g_{\rm m}$ (for Measurement I and II) and the output conductance $g_{\rm DS}$ (for Measurement III and IV) are obtained by numerical differentiation of the measured I-V-curves. Furthermore, $I_{\rm min}$ is the smallest current which can reliably measured by the system (noise limit) and $I_{\rm T}$ is defined as 10% of the largest measured value of $|I_{\rm D}|$ in Measurement I. The latter will be used to make a rough distinction between the subthreshold and superthreshold region.

The channel-to-gate capacitance $C_{\rm CG}$ in Measurement VIII is the summation of the drain-to-gate capacitance $C_{\rm DG}$ and the source-to-gate capacitance $C_{\rm SG}$ (i.e., source and drain are short-circuited); it is needed to extract overlap capacitance parameters.

The local parameter extraction measurements I through VI have to be performed at room temperature for every device. In addition, capacitance measurements VII and VIII need to be performed for at least a long/wide and a short/wide (i.e., $L = L_{\rm min}$) transistor (at room temperature). Furthermore, for the extraction of temperature scaling parameters measurements I, III, and V have to be performed at different temperatures (at least two extra, typically $-40\,^\circ$C and $125\,^\circ$C) for at least a long wide and a short wide transistor.

7.2 Extraction of local parameters at room temperature

General remarks

The simultaneous determination of *all* local parameters for a specific device is not advisable, because the value of some parameters can be wrong due to correlation and suboptimization. Therefore it is more practical to

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split the parameters into several small groups, where each parameter group can be determined using specific measurements. In this section, such a procedure will be outlined.

The extraction of local parameters is performed for every device. In order to ensure that the temperature scaling relations do not affect the behavior at room temperature, the reference temperature **TR** should be set equal to room temperature.

Before starting the parameter extraction procedure, one should make sure that **SWIGATE**, **SWIMPACT**, **SWGIDL**, **SWJUNCAP**, and **TYPE** are set to the desired value. Moreover, **QMC** should be set to 1, in order to include quantum mechanical corrections in the simulations.

It is not the case that all local parameters are extracted for every device. Several parameters are only extracted for one or a few devices, while they are kept fixed for all other devices. Moreover, a number of parameters can generally be kept fixed at their default values and need only occasionally be used for fine-tuning in the optimization procedure. Details are given later in this section.

As a special case, it is generally not necessary to extract values for **AX**. In stead, they can be calculated from Eq. (3.63), using **AXO** ~ 18 and **AXL** ~ 0.25. It may be necessary to tune the latter value such that the value of **AX** is between 2 and 3 for the shortest channel in the technology under study.

It is recommended to start the extraction procedure with the long(est) wide(st) device, then the shortest device with the same width, followed by all remaining devices of the same width in order of decreasing length. Then the next widest-channel devices are extracted, where the various lengths are handled in the same order. In this way, one works ones way down to the narrowest channel devices.

AC-parameters

Some parameters (such as **TOX** and **NP**) that do affect the DC-behavior of a MOSFET can only be extracted accurately from C-V-measurements.[2] This should be done before the actual parameter extraction from DC-measurements is started. In Tables 7.1 and 7.2 the extraction procedure for the AC-parameters is given.

Table 7.1: AC-parameter extraction procedure for a long channel MOSFET.

Step	Optimized parameters	Fitted on	Abs./Rel.	Conditions
1	**VFB**,**NEFF**, **DPHIB**, **NP**, **COX**	VII: C_{GG}	Relative	–
2	Repeat Step 1			

Table 7.2: AC-parameter extraction procedure for a short channel MOSFET. The values of **VFB** and **NP** are taken from the long-channel case.

Step	Optimized parameters	Fitted on	Abs./Rel.	Conditions
1	**NEFF**, **DPHIB**, **COX**	VII: C_{GG}	Relative	–
2	**CGOV**, **NOV**	VIII: C_{CG}	Relative	$V_{\mathrm{GS}} < 0$
3	Repeat Steps 1 and 2			

Starting from the default parameter set and setting **TOX** to a reasonable value (as known from technology), **VFB**, **NEFF**, **DPHIB**, **COX**, and **NP** can be extracted from C_{GG} in Measurement VII for a long, wide device.

Next, **NOV** and **CGOV** can be extracted from C_{CG} in Measurement VIII for a short, wide device (see also Table 7.1), where **VFB** and **NP** are taken from the long channel case. In general, one can assume **TOXOV** $=$ **TOX**.

The value of **TOX** can be determined from **COX** $= \epsilon_{\mathrm{ox}} \cdot L \cdot W /$**TOX**. If the device is sufficiently long and wide, drawn length and width can be used in this formula. Even better, if Measurement VII is available for a

[2] Although parameter **NOV** *can* be determined from overlap gate current, it is nonetheless more accurately determined from Measurement VIII.

few short/wide devices of different lengths, one can extract **TOX** and ΔL from a series of extracted values of **COX** vs. L_{draw}.

Some remarks:

- If C-V-measurements are not available, one could revert to values known from the fabrication process. Note that **TOX** and **TOXOV** are *physical* oxide thicknesses; poly-depletion and quantum-mechanical effects are taken care of by the model. If the gate dielectric is not pure SiO_2, one should manually compensate for the deviating dielectric constant.
- In general, **VFB** and **NP** can be assumed independent of channel length and width (so, the long/wide-channel values can be used for all other devices as well). Only if no satisfactory fits are obtained, one could allow for a length dependence (for **NP**) or length *and* width dependence (for **VFB**). Then, one should proceed by extracting **VFB** and/or **NP** from capacitance measurements for various channel geometries, fit Eq. (3.12) / Eq. (3.32) to the result and use interpolated values in the DC parameter extraction procedure.
- The value of parameter **TOX** profoundly influences both the DC- and AC-behavior of the PSP-model and thus the values of many other parameters. It is therefore very important that this parameter is determined (as described above) and *fixed* before the rest of the extraction procedure is started.

If desired (e.g., for RF-characterization), parameters for several parasitic capacitances (gate-bulk overlap, fringe capacitance, etc.) can be extracted as well (**CGBOV** and **CFR**). However, this requires additional capacitance measurements.

The obtained values of **VFB**, **TOX**, **TOXOV**, **NP**, and **NOV** can now be used in the DC-parameter extraction procedure. The above values of **NEFF** and **DPHIB** can be disregarded; they will be determined more accurately from the DC-measurements.

In devices with strong lateral non-uniform doping, the threshold voltage in AC-measurements may deviate significantly from that in DC-measurements. If that is the case, values for **NEFF** and **DPHIB** obtained from DC-measurements may not be satisfactory to describe AC-measurements. Then, one has the option to set **SWDELVTAC** $= 1$, **DELVTAC** $=$ **DPHIB**$_{\mathrm{ac}}$ $-$ **DPHIB**$_{\mathrm{dc}}$, and **FACNEFFAC** $=$ **NEFF**$_{\mathrm{ac}}/$**NEFF**$_{\mathrm{dc}}$ to get a good description of both the DC and the AC measurements.

DC-parameters

Before the optimization is started a reasonably good starting value has to be determined, both for the parameters to be extracted and for the parameters which remain constant. For most parameters to be extracted for a *long* channel device, the default values from local parameters in Section 2.5.2 can be taken as initial values. Exceptions are given in Table 7.3. Starting from these values, the optimization procedure following the scheme below is performed. This method yields a proper set of parameters after the repetition indicated as the final step in the scheme. Experiments with transistors of several processes show that repeating those steps more than once is generally not necessary.

For an accurate extraction of parameter values, the parameter set for a long-channel transistor has to be determined first. In the long-channel case most of the mobility related parameters (i.e. **MUE** and **THEMU**) and the gate tunneling parameters (**GCO**, **GC2**, and **GC3**) are determined and subsequently fixed for the shorter-channel devices.

In Table 7.4 the complete DC extraction procedure for long-channel transistors is given. The magnitude of the simulated I_{D} and the overall shape of the simulated I_{D}-V_{GS}-curve is roughly set in Step 1. Next the parameters **NEFF**, **DPHIB**, and **CT**—which are important for the subthreshold behavior—are optimized in Step 2, neglecting short-channel effects such as drain-induced barrier-lowering (DIBL). After that, the mobility parameters are optimized in Step 3, neglecting the influence of series-resistance. In Step 4 a preliminary value of the velocity saturation parameter is obtained, and subsequently the conductance parameters **ALP**, **ALP1**, **ALP2**, and **VP** are determined in Step 5. A more accurate value of **THESAT** can now be obtained using Step 6. The gate current parameters are determined in Steps 7 and 8, where it should be noted that **GCO** should only be extracted if the influence of gate-to-bulk tunneling is visible in the measurements. This is usually the

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Table 7.3: Initial values for local parameter extraction for a *long*-channel device. For parameters which are not listed in this table, the default value (as given in Section 2.5.2) can be used as initial value.

Parameter	Initial value
BETN	$0.03 \cdot W/L$
RS	0
THESAT	0.1
AX	12
A1	0

Table 7.4: DC-parameter extraction procedure for a long-channel MOSFET. The parameters **VFB**, **TOX**, **TOXOV**, **NP**, and **NOV** must be taken from C-V-measurements. The optimization is either performed on the absolute or relative deviation between model and measurements, as shown in the table.

Step	Optimized parameters	Fitted on	Abs./Rel.	Conditions
1	**NEFF**, **BETN**, **MUE**, **THEMU**[a]	I: $I_{\rm D}$	Absolute	–
2	**NEFF**, **DPHIB**, **CT**, **GFACNUD**	I: $I_{\rm D}$	Relative	$I_{\rm min} < I_{\rm D} < I_{\rm T}$
3	**MUE**, **THEMU**[a], **CS**, **XCOR**, **BETN**	I: $I_{\rm D}$, $g_{\rm m}$	Absolute	–
4	**THESAT**	III: $I_{\rm D}$	Absolute	–
5	**ALP**, **ALP1**, **ALP2**, **VP**[a], (**AX**)	III: $g_{\rm DS}$	Relative	–
6	**THESAT**	II: $I_{\rm D}$	Absolute	–
7	**IGINV**, **GC2**[a], **GC3**[a]	V: $I_{\rm G}$	Relative	$I_{\rm G} > I_{\rm min}$
8	**IGOV**, (**GCO**[a])	V: $I_{\rm G}$	Relative	$V_{\rm GS} < 0$ V, $I_{\rm G} < -I_{\rm min}$
9	**A1**, **A2**[a], **A3**	V: $I_{\rm B}$	Relative	$V_{\rm GS} > 0$ V, $I_{\rm B} < -I_{\rm min}$
10	**A4**	VI: $I_{\rm B}$	Relative	$V_{\rm GS} > 0$ V, $I_{\rm B} < -I_{\rm min}$
11	**AGIDL**, **BGIDL**[a]	V: $I_{\rm B}$	Relative	$V_{\rm GS} < 0$ V, $I_{\rm B} < -I_{\rm min}$
12	**CGIDL**[a]	VI: $I_{\rm B}$	Relative	$V_{\rm GS} < 0$ V, $I_{\rm B} < -I_{\rm min}$
13	Repeat Steps 2 – 12			

[a]Only extracted for the *widest* long channel device and fixed for all other geometries.

case if $V_{\rm sup} \gtrsim |\mathbf{VFB}|$. This is followed by the weak-avalanche parameters in Step 9 and (optionally) 10, and finally, the gate-induced leakage current parameters are optimized in Step 11 and (optionally) 12.

After completion of the extraction for the long-channel device, it is recommended to first extract parameters for the shortest-channel device (of the same width). The mobility-reduction parameters (**MUE**, **THEMU**) and the gate tunneling probability factors (**GCO**, **GC2**, **GC3**) found from the corresponding long-channel device should be used. The extraction procedure as given in Table 7.5 should be used.

Once the value for **RS** has been found from the shortest device, it should be copied into the long-channel parameter set and steps 2–3 (Table 7.4) should be repeated, possibly leading to some readjustment of **MUE** and **THEMU**. If necessary, this procedure must be repeated. Similarly—once the value of **THESATG** and **THESATB** have been determined from the shortest widest channel device—steps 4, 5, and 6 of the long-channel extraction procedure (Table 7.4) must be repeated to obtain updated values for **THESAT**, **ALP**, **ALP1**, and **ALP2**.

If consistent parametersets have been found for the longest and shortest channel device, the extraction procedure

Table 7.5: DC-parameter extraction procedure for a short-channel MOSFET. Parameters **MUE**, **THEMU**, **VP**, **GCO**, **GC2**, **GC3**, **A2**, **A4**, **BGIDL**, and **CGIDL** are taken from the corresponding long-channel case. The optimization is either performed on the absolute or relative deviation between model and measurements, as indicated in the table.

Step	Optimized parameters	Fitted on	Abs./Rel.	Conditions
1	**NEFF**, **DPHIB**, **BETN**, **RS**[a]	I: I_D	Absolute	–
2	**NEFF**, **DPHIB**, **CT**, **GFACNUD**, **VSBNUD**[b], **DVSBNUD**[b]	I: I_D	Relative	$I_\mathrm{min} < I_\mathrm{D} < I_\mathrm{T}$
3	**BETN**, **RS**[a], **XCOR**	I: I_D, g_m	Absolute	–
4	**THESAT**	III: I_D	Absolute	–
5	**ALP**, **ALP1**, **ALP2**, **CF**, (**AX**)	III: g_DS	Relative	–
6	**CFB**[b]	IV: g_DS	Relative	–
7	**THESAT**, **THESATG**[b], **THESATB**[b]	II: I_D, g_m	Absolute	–
8	**IGINV**, **IGOV**	V: I_G	Relative	$\lvert I_\mathrm{G}\rvert > I_\mathrm{min}$
9	**A1**, **A3**	V: I_B	Relative	$V_\mathrm{GS} > 0$ V, $I_\mathrm{B} < -I_\mathrm{min}$
10	**AGIDL**	V: I_B	Relative	$V_\mathrm{GS} < 0$ V, $I_\mathrm{B} < -I_\mathrm{min}$
11	Repeat Steps 2 – 10			

[a] Only extracted for the *shortest* channel of each width and fixed for all other geometries.
[b] Only extracted for the *shortest widest* device and fixed for all other geometries.

as given in Table 7.5 can be executed for all intermediate channel lengths. The extracted parameter values of the next-longer device can be used as initial values.

Finally, the parameters **GFACNUD**, **VSBNUD**, and **DVSBNUD** should only be used if the description of the body effect is not satisfactory otherwise. For this, the NUD-model must be invoked by setting **SWNUD** $= 1$.

7.3 Extraction of Temperature Scaling Parameters

For a specific device, the temperature scaling parameters can be extracted after determination of the local parameters at room temperature. In order to do so, measurements I, II and IV need to be performed at various temperature values (at least two values different from room temperature, typically $-40\,°\mathrm{C}$ and $125\,°\mathrm{C}$), at least for a long wide device and a short wide device. If the reference temperature **TR** has been chosen equal to room temperature (as recommended in Section 7.2), the modeled behavior at room temperature is insensitive to the value of the temperature scaling parameters. As a first-order estimate of the temperature scaling parameter values, the default values as given by local parameters in Section 2.5.2 can be used. Again the parameter extraction scheme is slightly different for the long-channel and for the short-channel case.

For an accurate extraction, the temperature scaling parameters for a long-wide-channel device have to be determined first. In the long-wide-channel case the carrier mobility parameters can be determined, and they are subsequently fixed for all other devices. In Table 7.6 the appropriate extraction procedure is given. In Step 1 the subthreshold temperature dependence is optimized, followed by the optimization of mobility reduction parameters in Step 2. Next the temperature dependence of velocity saturation is optimized in Step 3. In the subsequent steps, parameters for the temperature dependence of the gate current, the impact ionization current and gate-induced drain leakage are determined. The determined values of the mobility reduction temperature scaling parameters (i.e., **STMUE**, **STTHEMU**, **STCS**, and **STXCOR**) are copied to all other devices and kept fixed during the remainder of the temperature-scaling parameter extraction procedure. Step 1 and 2 could then be performed on one or more long narrow devices as well (for **STVFB**, **STBETN**, and **STTHESAT** only).

Next the extraction procedure as given in Table 7.7 is carried out for several short devices of different widths. Preferably, the extraction is done first for a short narrow device, such that the determined value of **STRS** can

Table 7.6: Temperature scaling parameter extraction procedure for a long wide channel MOSFET. This scheme only makes sense if measurements have been performed at one or (preferably) more temperatures which differ from room temperature.

Step	Optimized parameters	Fitted on	Abs./Rel.	Conditions
1	**STVFB**[a]	I: $I_{\rm D}$	Relative	$I_{\rm D} < I_{\rm T}$
2	**STBETN**[a], **STMUE**, **STTHEMU**, **STCS**, **STXCOR**	I: $I_{\rm D}$	Absolute	–
3	**STTHESAT**[a]	II: $I_{\rm D}$	Absolute	–
4	**STIG**	V: $I_{\rm G}$	Relative	$\lvert I_{\rm G}\rvert > I_{\rm min}$
5	**STA2**	V: $I_{\rm B}$	Relative	$V_{\rm GS} > 0$ V, $I_{\rm B} < -I_{\rm min}$
6	**STBGIDL**	V: $I_{\rm B}$	Relative	$V_{\rm GS} < 0$ V, $I_{\rm B} < -I_{\rm min}$

[a] Also extracted for one or more long *narrow* devices.

Table 7.7: Temperature scaling parameter extraction procedure for short-channel MOSFETs (both wide and narrow). This scheme only makes sense if measurements have been performed at one or (preferably) more temperatures which differ from room temperature.

Step	Optimized parameters	Fitted on	Abs./Rel.	Conditions
1	**STVFB**	I: $I_{\rm D}$	Relative	$V_{\rm GS} < V_{\rm T}$
2	**STBETN**, **STRS**[a]	I: $I_{\rm D}$	Absolute	$V_{\rm GS} > V_{\rm T}$
3	**STTHESAT**	II: $I_{\rm D}$	Absolute	–

[a] Only extracted for a short *narrow* device and fixed for all other geometries.

be used during the extraction of the wider devices.

7.4 Extraction of Geometry Scaling Parameters

The aim of the complete extraction procedure is the determination of the geometry scaling parameters (global parameters), i.e., a single set of parameters (see Section 2.5.2) which gives a good description of the MOSFET-behavior over the full geometry range of a CMOS technology.

Determination of ΔL and ΔW

An extremely important part of the geometry scaling extraction scheme is an accurate determination of ΔL and ΔW, see Eqs. (3.6) and (3.7).[3] Since it affects the DC-, the AC- as well as the noise model and, moreover, it can heavily influence the quality of the resulting global parameter set, it is very important that this step is carried out with care.

Traditionally, ΔW can be determined from the extrapolated zero-crossing in **BETN** versus mask width W. In a similar way ΔL can be determined from $1/$**BETN** versus mask length L. For modern MOS devices with pocket implants, however, it has been found that the above ΔL extraction method is no longer valid [11, 12]. Another, more accurate method is to measure the gate-to-bulk capacitance $C_{\rm GB}$ in accumulation for different channel lengths [12, 13]. In this case the extrapolated zero-crossing in the $C_{\rm GB}$ versus mask length L curve will

[3] Note that $\Delta L_{\rm PS}$ and $\Delta W_{\rm OD}$ are expected to be known from the fabrication process. So, in fact, only **LAP** and **WOT** are extracted from the electrical measurements.

give ΔL. Similarly, the extracted values for **COX** (from the procedure in Table 7.1 and 7.2) vs. mask length L may be used for this purpose. Unfortunately for CMOS technologies in which gate current is non-negligible, capacitance measurements may be hampered by gate current [14]. In this case gate current parameter **IGINV** plotted as a function of channel length L may be used to extract ΔL [14]. If possible, ΔL extraction from C-V-measurements is the preferred method.

Finally, **LOV** can be obtained from (a series of) extracted values of **CGOV** from one or more short devices.

From local to global

First of all, the global parameters **TYPE**, **QMC**, and the 'switch'-parameters should be set to the appropriate value. Next, parameters for which no geometrical scaling rules exist must be taken directly from the local set (this applies to **TR**, **TOXO**, **VNSUBO**, **NSLPO**, **DNSUBO**, **TOXOVO**, **NOVO**, **CFBO**, **STMUEO**, **THEMUO**, **STTHEMUO**, **STCSO**, **STXCORO**, **FETAO**, **STRSO**, **RSBO**, **RSGO**, **THESATBO**, **THESATGO**, **VPO**, **A2O**, **STA2O**, **GCOO**, **STIGO**, **GC2O**, **GC3O**, **CHIBO**, **BGIDLO**, **STBGIDLO**, **CGIDLO**, and **DTA**). Generally, these parameters have been left at their default values or they have been extracted for one device only and subsequently fixed for all other devices. The parameters **LVARO**, **LVARL**, **LVARW**, **WVARO**, **WVARL**, and **WVARW** should be known from technology.

Once the values of ΔL and ΔW are firmly established (as described above), **LAP** and **WOT** can be set and the actual extraction procedure of the geometry scaling parameters can be started. It consists of several *independent* sub-steps (which can be carried out in random order), one for each geometry dependent local parameter.

To illustrate such a sub-step, the local parameter **CT** is taken as an example. The relevant geometry scaling equation from Section 3.2 is Eq. (3.33), from which it can be seen that **CTO**, **CTL**, **CTLEXP**, and **CTW** are the global parameters which determine the value of **CT** as a function of L and W. First, the extracted **CT** of each device in a length-series of measured (preferably wide) devices are considered as a function of L. In this context **CTO**, **CTL**, and **CTLEXP** are optimized such that the fit of Eq. (3.33) to the extracted **CT**-values is as good as possible, while keeping **CTW** fixed at 0. Then **CTW** is determined by considering the extracted **CT**-values from a length-series of measured narrow devices. Finally, the four global parameters may be fine-tuned by optimizing all four parameters to all extracted **CT**-values simultaneously. The default values given in Section 2.5.2 are good initial values for the optimization procedure.

All other parameters can be extracted in a similar manner. The local parameters **BETN** and **NEFF** have quite complicated scaling rules, particularly due to the non-uniform doping profiles employed in modern CMOS technologies. Therefore, a few additional guidelines are in place.

- The optimization procedure for **BETN** is facilitated if not **BETN**, but $\mathbf{BETN}_{\mathrm{sq}} \stackrel{\mathrm{def}}{=} \mathbf{BETN} \cdot L_{\mathrm{E}}/W_{\mathrm{E}}$ is considered.
- Starting from the default values, first **UO**, **FBET1**, **LP1**, **FBET2**, and **LP2** should be determined from a length-series of wide devices. Then **BETW1**, **BETW2**, and **WBET** should be determined from a width-series of long devices. Finally, **FBET1W** and **LP1W** can be found by considering some short narrow devices.
- Starting from the default values, first extract **FOL1**, **FOL2**, **NSUBO**, **NPCK**, and **LPCK** from a length-series of wide devices. Here, **NSUBO** determines the long-channel value of **NEFF**. Moreover, **NPCK** and **LPCK** determine the increase of **NEFF** for shorter channels (reverse short channel effect), while **FOL1** and **FOL2** are used to describe the decrease of **NEFF** for very short channels (short channel effect).
- Then **NSUBW** and **WSEG** can be determined form a width-series of long devices. Finally, **NPCKW**, **LPCKW** and **WEGP** are determined from a width-series of short devices.
- Especially for **BETN** and **NEFF** it is advisable—after completing the procedure described above—to fine tune the global parameters found by considering all extracted values of **BETN** (or **NEFF**) simultaneously.

Note that in many cases it may not be necessary to use the full flexibility of PSP's parameter scaling, e.g., for many technologies **NP** and **VFB** may be considered as independent of geometry. If such a geometry-

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independence is anticipated, the corresponding local parameter should be fixed during local parameter extraction. Only if the resulting global parameter set is not satisfactory, the parameter should be allowed to vary during a subsequent optimization round.

Fine tuning

Once the complete set of global parameters is found, the global model should give an accurate description of the measured I-V-curves and capacitance measurements. Either for fine tuning or to facilitate the extraction of global parameters for which the geometry scaling of the corresponding extracted local parameters is not well-behaved, there are two more things that can be done.

- Local parameters for which the fitting of global parameters was completed satisfactorily could be replaced by the values calculated from the geometrical scaling rules and fixed. Then one could redo (parts of) the local parameter extraction procedure for the remaining local parameters, making them less sensitive for cross-correlations.
- Small groups of global parameters may be fitted directly to the measurements of a well-chosen series of devices, using the global model.

7.5 Summary – Geometrical scaling

Summarizing, for the determination of a full parameter set, the following procedure is recommended.

1. Determine local parameter sets (**VFB**, **NEFF**, . . .) for all measured devices, as explained in Section 7.2 and 7.3.
2. Find ΔL and ΔW.
3. Determine the global parameters by fitting the appropriate geometry scaling rules to the extracted local parameters.
4. Finally, the resulting global can be fine-tuned, by fitting the result of the scaling rules and current equations to the measured currents of all devices simultaneously.

7.6 Extraction of Binning Parameters

In this section, expressions will be given for the parameters in the binning scaling rules, **POYYY**, **PLYYY**, **PWYYY**, and **PLWYYY**, as given in Section 3.3. These coefficients will be expressed in terms of parameter values at the corners of bin (see Fig. 7.1). These expressions can be easily found by substituting the parameter values at the bin corners into the binning scaling rules and inverting the resulting four equations. Note once more that this results in a *separate parameter set for each bin*.

In the expression below, the value of parameter **YYY** at bin corner (L_i, W_j) is denoted by Y_{ij} ($i = 1, 2$, $j = 1, 2$). Moreover, $\Delta L = L_2 - L_1$, $\Delta W = W_2 - W_1$, $A = 1/(\Delta L \cdot \Delta W)$.

1. Coefficients for type I scaling

$$\textbf{POYYY} = A \cdot (L_1 \cdot W_1 \cdot Y_{11} - L_1 \cdot W_2 \cdot Y_{12} - L_2 \cdot W_1 \cdot Y_{21} + L_2 \cdot W_2 \cdot Y_{22}) \tag{7.1}$$

$$\textbf{PLYYY} = A \cdot \frac{L_1 \cdot L_2}{L_{\text{EN}}} \cdot (-W_1 \cdot Y_{11} + W_2 \cdot Y_{12} + W_1 \cdot Y_{21} - W_2 \cdot Y_{22}) \tag{7.2}$$

$$\textbf{PWYYY} = A \cdot \frac{W_1 \cdot W_2}{W_{\text{EN}}} \cdot (-L_1 \cdot Y_{11} + L_1 \cdot Y_{12} + L_2 \cdot Y_{21} - L_2 \cdot Y_{22}) \tag{7.3}$$

$$\textbf{PLWYYY} = A \cdot \frac{L_1 \cdot L_2 \cdot W_1 \cdot W_2}{L_{\text{EN}} \cdot W_{\text{EN}}} \cdot (Y_{11} - Y_{12} - Y_{21} + Y_{22}) \tag{7.4}$$

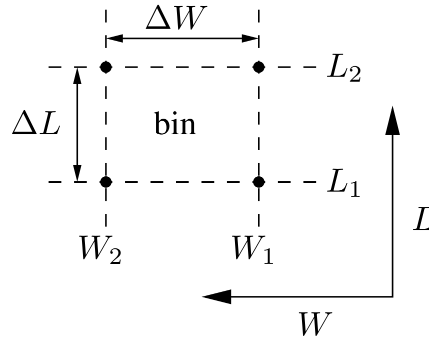

Figure 7.1: Schematic view of a bin, showing the coordinates of the four corners. Note that L_1, L_2, W_1, and W_2 denote the *effective* length and width (L_E and W_E) at the bin corners.

2. Coefficients for type II scaling

$$\textbf{POYYY} = A \cdot (L_2 \cdot W_2 \cdot Y_{11} - L_2 \cdot W_1 \cdot Y_{12} - L_1 \cdot W_2 \cdot Y_{21} + L_1 \cdot W_1 \cdot Y_{22}) \tag{7.5}$$

$$\textbf{PLYYY} = A \cdot L_\mathrm{EN} \cdot (-W_2 \cdot Y_{11} + W_1 \cdot Y_{12} + W_2 \cdot Y_{21} - W_1 \cdot Y_{22}) \tag{7.6}$$

$$\textbf{PWYYY} = A \cdot W_\mathrm{EN} \cdot (-L_2 \cdot Y_{11} + L_2 \cdot Y_{12} + L_1 \cdot Y_{21} - L_1 \cdot Y_{22}) \tag{7.7}$$

$$\textbf{PLWYYY} = A \cdot L_\mathrm{EN} \cdot W_\mathrm{EN} \cdot (Y_{11} - Y_{12} - Y_{21} + Y_{22}) \tag{7.8}$$

3. Coefficients for type III scaling

$$\textbf{POYYY} = A \cdot (-L_1 \cdot W_2 \cdot Y_{11} + L_1 \cdot W_1 \cdot Y_{12} + L_2 \cdot W_2 \cdot Y_{21} - L_2 \cdot W_1 \cdot Y_{22}) \tag{7.9}$$

$$\textbf{PLYYY} = A \cdot \frac{L_1 \cdot L_2}{L_\mathrm{EN}} \cdot (W_2 \cdot Y_{11} - W_1 \cdot Y_{12} - W_2 \cdot Y_{21} + W_1 \cdot Y_{22}) \tag{7.10}$$

$$\textbf{PWYYY} = A \cdot W_\mathrm{EN} \cdot (L_1 \cdot Y_{11} - L_1 \cdot Y_{12} - L_2 \cdot Y_{21} + L_2 \cdot Y_{22}) \tag{7.11}$$

$$\textbf{PLWYYY} = A \cdot \frac{L_1 \cdot L_2 \cdot W_\mathrm{EN}}{L_\mathrm{EN}} \cdot (-Y_{11} + Y_{12} + Y_{21} - Y_{22}) \tag{7.12}$$

Note: For L_1, L_2, W_1, and W_2 in the formulas above one must take the *effective* length and width (L_E and W_E) as defined in Section 3.2.

7.6.1 Binning of BETN

From PSP 103.0 onwards, the binning rule of **BETN** is changed to better match its typical scaling behavior.

- Extract the parameters **POBETN**, **PLBETN**, **PWBETN**, and **PLWBETN** for type I binning by applying Eq. (7.1)-(7.4) to $(L_\mathrm{E}/W_\mathrm{E}) \cdot$ **BETN** (i.e., not to **BETN** itself).

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Section 8

DC Operating Point Output

The DC operating point output facility gives information on the state of a device at its operation point. Beside terminal currents and voltages, the magnitudes of linearized internal elements are given. In some cases meaningful quantities can be derived which are then also given (e.g., f_{T}). The objective of the DC operating point facility is twofold:

- Calculate small-signal equivalent circuit element values
- Open a window on the internal bias conditions of the device and its basic capabilities.

All accessible quantities are described in the table below. The symbols in the 'value' column are defined in Section 4. Besides, the following notation is used: $P_{\mathrm{D}} = 1 + \boldsymbol{k_p} \cdot G/4$, where $\boldsymbol{k_p}$ is defined in Eq. (4.23).

Important note: For *all* operating point output the signs are such as if the device is an NMOS. Moreover, whenever there is a reference to the 'drain', this is always the terminal which is acting as drain for the actual bias conditions. This is even true for variables such as **vds** (which is therefore always nonnegative) and the junction-related variables. The output variable **sdint** shows whether or not this 'drain' is the same as the terminal which was named 'drain' in the simulator.

No.	Name	Unit	Value	Description
0	**ctype**	–	1 for NMOS, -1 for PMOS	Flag for channel-type
1	**sdint**	–	1 if $V'_{\mathrm{DS}} \geq 0, \ -1$ otherwise	Flag for source-drain interchange
			Current components	
2	**ise**	A	$I_{\mathrm{S}} - I_{\mathrm{JS}}$	Total source current
3	**ige**	A	I_{G}	Total gate current
4	**ide**	A	$I_{\mathrm{D}} - I_{\mathrm{JD}}$	Total drain current
5	**ibe**	A	$I_{\mathrm{B}} + I_{\mathrm{JS}} + I_{\mathrm{JD}}$	Total bulk current
6	**ids**	A	I_{DS}	Drain current, excl. avalanche and tunnel currents
7	**idb**	A	$I_{\mathrm{avl}} + I_{\mathrm{gidl}} - I_{\mathrm{JD}}$	Drain-to-bulk current
8	**isb**	A	$I_{\mathrm{gisl}} - I_{\mathrm{JS}}$	Source-to-bulk current
9	**igs**	A	$I_{\mathrm{GCS}} + I_{\mathrm{GSov}}$	Gate-source tunneling current
10	**igd**	A	$I_{\mathrm{GCD}} + I_{\mathrm{GDov}}$	Gate-drain tunneling current
11	**igb**	A	I_{GB}	Gate-bulk tunneling current
12	**igcs**	A	I_{GCS}	Gate-channel tunneling current (source component)

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No.	Name	Unit	Value	Description
13	**igcd**	A	I_{GCD}	Gate-channel tunneling current (drain component)
14	**iavl**	A	I_{avl}	Substrate current due to weak-avalanche
15	**igisl**	A	I_{gisl}	Gate-induced source leakage current
16	**igidl**	A	I_{gidl}	Gate-induced drain leakage current
			Junction currents	
17	**ijs**	A	I_{JS}	Total source junction current
18	**ijsbot**	A	$I_{\mathrm{JS,bot}}$	Source junction current, bottom component
19	**ijsgat**	A	$I_{\mathrm{JS,gat}}$	Source junction current, gate-edge component
20	**ijssti**	A	$I_{\mathrm{JS,sti}}$	Source junction current, STI-edge component
21	**ijd**	A	I_{JD}	Total drain junction current
22	**ijdbot**	A	$I_{\mathrm{JD,bot}}$	Drain junction current, bottom component
23	**ijdgat**	A	$I_{\mathrm{JD,gat}}$	Drain junction current, gate-edge component
24	**ijdsti**	A	$I_{\mathrm{JD,sti}}$	Drain junction current, STI-edge component
			Voltages	
25	**vds**	V	V_{DS}	Drain-source voltage
26	**vgs**	V	V_{GS}	Gate-source voltage
27	**vsb**	V	V_{SB}	Source-bulk voltage
28	**vto**	V	$\mathbf{VFB} + P_{\mathrm{D}} \cdot (\boldsymbol{\phi_{\mathrm{B}}} + 2 \cdot \boldsymbol{\phi^{*}_{\mathrm{T}}}) + G \cdot \sqrt{\boldsymbol{\phi^{*}_{\mathrm{T}}} \cdot (\boldsymbol{\phi_{\mathrm{B}}} + 2 \cdot \boldsymbol{\phi^{*}_{\mathrm{T}}})}$	Zero-bias threshold voltage
29	**vts**	V	$\mathbf{VFB} + P_{\mathrm{D}} \cdot (V_{\mathrm{SB}}^{\mathrm{nud}} + \boldsymbol{\phi_{\mathrm{B}}} + 2 \cdot \boldsymbol{\phi^{*}_{\mathrm{T}}}) - V_{\mathrm{SB}}^{\mathrm{nud}} + G \cdot \sqrt{\boldsymbol{\phi^{*}_{\mathrm{T}}} \cdot (V_{\mathrm{SB}}^{\mathrm{nud}} + \boldsymbol{\phi_{\mathrm{B}}} + 2 \cdot \boldsymbol{\phi^{*}_{\mathrm{T}}})}$	Threshold voltage including back-bias effects
30	**vth**	V	$\mathbf{vts} - \Delta V_{\mathrm{G}}$	Threshold voltage including back-bias and drain-bias effects
31	**vgt**	V	$\mathbf{vgs} - \mathbf{vth}$	Effective gate drive voltage including drain- and back-bias effects
32	**vdss**	V	V_{dsat}	Drain saturation voltage at actual bias
33	**vsat**	V	$V_{\mathrm{DS}} - V_{\mathrm{dsat}}$	Saturation limit
			(Trans-)conductances	
34	**gm**	A/V	$\partial \mathbf{ide} / \partial V_{\mathrm{GS}}$	Transconductance
35	**gmb**	A/V	$-\partial \mathbf{ide} / \partial V_{\mathrm{SB}}$	Substrate-transconductance
36	**gds**	A/V	$\partial \mathbf{ide} / \partial V_{\mathrm{DS}}$	Output conductance
37	**gjs**	A/V	$-\partial \mathbf{ijs} / \partial V_{\mathrm{SB}}$	Source junction conductance

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No.	Name	Unit	Value	Description
38	**gjd**	A/V	$-(\partial\mathbf{ijd}/\partial V_{\rm DS}+\partial\mathbf{ijd}/\partial V_{\rm SB})$	Drain junction conductance
			Capacitances	
39	**cdd**	F	$\partial Q_{\rm D}^{(i)}/\partial V_{\rm DS}$	Drain capacitance
40	**cdg**	F	$-\partial Q_{\rm D}^{(i)}/\partial V_{\rm GS}$	Drain-gate capacitance
41	**cds**	F	$\mathbf{cdd}-\mathbf{cdg}-\mathbf{cdb}$	Drain-source capacitance
42	**cdb**	F	$\partial Q_{\rm D}^{(i)}/\partial V_{\rm SB}$	Drain-bulk capacitance
43	**cgd**	F	$-\partial Q_{\rm G}^{(i)}/\partial V_{\rm DS}$	Gate-drain capacitance
44	**cgg**	F	$\partial Q_{\rm G}^{(i)}/\partial V_{\rm GS}$	Gate capacitance
45	**cgs**	F	$\mathbf{cgg}-\mathbf{cgd}-\mathbf{cgb}$	Gate-source capacitance
46	**cgb**	F	$\partial Q_{\rm G}^{(i)}/\partial V_{\rm SB}$	Gate-bulk capacitance
47	**csd**	F	$-\partial Q_{\rm S}^{(i)}/\partial V_{\rm DS}$	Source-drain capacitance
48	**csg**	F	$-\partial Q_{\rm S}^{(i)}/\partial V_{\rm GS}$	Source-gate capacitance
49	**css**	F	$\mathbf{csg}+\mathbf{csd}+\mathbf{csb}$	Source capacitance
50	**csb**	F	$\partial Q_{\rm S}^{(i)}/\partial V_{\rm SB}$	Source-bulk capacitance
51	**cbd**	F	$-\partial Q_{\rm B}^{(i)}/\partial V_{\rm DS}$	Bulk-drain capacitance
52	**cbg**	F	$-\partial Q_{\rm B}^{(i)}/\partial V_{\rm GS}$	Bulk-gate capacitance
53	**cbs**	F	$\mathbf{cbb}-\mathbf{cbd}-\mathbf{cbg}$	Bulk-source capacitance
54	**cbb**	F	$-\partial Q_{\rm B}^{(i)}/\partial V_{\rm SB}$	Bulk capacitance
55	**cgsol**	F	$\partial(Q_{\rm sov}+Q_{\rm ofs})/\partial V_{\rm GS}$	Total gate-source overlap capacitance
56	**cgdol**	F	$\partial(Q_{\rm dov}+Q_{\rm ofd})/\partial V_{\rm DS}$	Total gate-drain overlap capacitance
			Junction capacitances	
57	**cjs**	F	$C_{\rm JS}$	Total source junction capacitance
58	**cjsbot**	F	$C_{\rm JS,bot}$	Source junction capacitance, bottom component
59	**cjsgat**	F	$C_{\rm JS,gat}$	Source junction capacitance, gate-edge component
60	**cjssti**	F	$C_{\rm JS,sti}$	Source junction capacitance, STI-edge component
61	**cjd**	F	$C_{\rm JD}$	Total drain junction capacitance
62	**cjdbot**	F	$C_{\rm JD,bot}$	Drain junction capacitance, bottom component
63	**cjdgat**	F	$C_{\rm JD,gat}$	Drain junction capacitance, gate-edge component
64	**cjdsti**	F	$C_{\rm JD,sti}$	Drain junction capacitance, STI-edge component
			Miscellaneous	
65	**weff**	m	$W_{\rm E}$	Effective channel width for geometrical models
66	**leff**	m	$L_{\rm E}$	Effective channel length for geometrical models
67	**u**	-	$\mathbf{gm}/\mathbf{gds}$	Transistor gain

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No.	Name	Unit	Value	Description
68	**rout**	Ω	$1/\mathbf{gds}$	Small-signal output resistance
69	**vearly**	V	$\lvert\mathbf{ide}\rvert/\mathbf{gds}$	Equivalent Early voltage
70	**beff**	A/V^2	$2 \cdot \lvert\mathbf{ide}\rvert/\mathbf{vgt}^2$	Gain factor
71	**fug**	Hz	$\mathbf{gm}/[2 \cdot \pi \cdot (\mathbf{cgg} + \mathbf{cgsol} + \mathbf{cgdol})]$	Unity gain frequency at actual bias
72	**rg**	Ω	**RG**	Gate resistance
			Noise	
73	**sfl**	A^2/Hz	$S_{\mathrm{fl}}(1\ \mathrm{Hz})$	Flicker noise current spectral density at 1 Hz
74	**sqrtsff**	V/$\sqrt{\mathrm{Hz}}$	$\sqrt{S_{\mathrm{fl}}(1\ \mathrm{kHz})}/\mathbf{gm}$	Input-referred RMS white noise voltage spectral density at 1 kHz
75	**sqrtsfw**	V/$\sqrt{\mathrm{Hz}}$	$\sqrt{S_{\mathrm{id}}}/\mathbf{gm}$	Input-referred RMS white noise voltage spectral density
76	**sid**	A^2/Hz	S_{id}	Channel thermal noise current spectral density
77	**sig**	A^2/Hz	$S_{\mathrm{ig}}(1\ \mathrm{kHz})$	Induced gate noise current spectral density at 1 kHz
78	**cigid**	–	$\dfrac{m_{\mathrm{igid}}}{\sqrt{m_{\mathrm{ig}} \cdot m_{\mathrm{id}}}}$	Imaginary part of correlation coefficient between S_{ig} and S_{id}
79	**fknee**	Hz	$1\mathrm{Hz} \cdot S_{\mathrm{fl}}(1\mathrm{Hz})/S_{\mathrm{id}}$	Cross-over frequency above which white noise is dominant
80	**sigs**	A^2/Hz	S_{igs}	Gate-source current noise spectral density
81	**sigd**	A^2/Hz	S_{igd}	Gate-drain current noise spectral density
82	**siavl**	A^2/Hz	S_{avl}	Impact ionization current noise spectral density
83	**ssi**	A^2/Hz	$S_{\mathrm{S,I}}$	Total source junction current noise spectral density
84	**sdi**	A^2/Hz	$S_{\mathrm{D,I}}$	Total drain junction current noise spectral density
			Self heating	
85	**tk**	K	T_{KD}	Device temperature
86	**pdiss**	W	P_{diss}	Power dissipation
87	**dtsh**	K	$T_{\mathrm{KD}} - T_{\mathrm{KA}}$	Temperature rise due to self heating

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From PSP 103.0 onwards, the values of local parameters are provided in the operating point output. They are listed in the table below.

No.	Name	Unit	Description
			Process Parameters
0	**lp_vfb**	V	Local parameter **VFB** after T-scaling and clipping
1	**lp_stvfb**	V/K	Local parameter **STVFB** after clipping
2	**lp_tox**	m	Local parameter **TOX** after clipping
3	**lp_epsrox**	–	Local parameter **EPSROX** after clipping
4	**lp_neff**	m^{-3}	Local parameter **NEFF** after clipping
5	**lp_facneffac**	–	Local parameter **FACNEFFAC** after clipping
6	**lp_gfacnud**	–	Local parameter **GFACNUD** after clipping
7	**lp_vsbnud**	V	Local parameter **VSBNUD** after clipping
8	**lp_dvsbnud**	V	Local parameter **DVSBNUD** after clipping
9	**lp_vnsub**	V	Local parameter **VNSUB** after clipping
10	**lp_nslp**	V	Local parameter **NSLP** after clipping
11	**lp_dnsub**	V^{-1}	Local parameter **DNSUB** after clipping
12	**lp_dphib**	V	Local parameter **DPHIB** after clipping
13	**lp_delvtac**	V	Local parameter **DELVTAC** after clipping
14	**lp_np**	m^{-3}	Local parameter **NP** after clipping
15	**lp_ct**	–	Local parameter **CT** after clipping
16	**lp_toxov**	m	Local parameter **TOXOV** after clipping
17	**lp_toxovd**	m	Local parameter **TOXOVD** after clipping
18	**lp_nov**	m^{-3}	Local parameter **NOV** after clipping
19	**lp_novd**	m^{-3}	Local parameter **NOVD** after clipping
			DIBL Parameters
20	**lp_cf**	–	Local parameter **CF** after clipping
21	**lp_cfb**	V^{-1}	Local parameter **CFB** after clipping
			Mobility Parameters
22	**lp_betn**	m^2/V/s	Local parameter **BETN** after T-scaling and clipping
23	**lp_stbet**	–	Local parameter **STBET** after clipping
24	**lp_mue**	m/V	Local parameter **MUE** after T-scaling and clipping
25	**lp_stmue**	–	Local parameter **STMUE** after clipping
26	**lp_themu**	–	Local parameter **THEMU** after T-scaling and clipping
27	**lp_stthemu**	–	Local parameter **STTHEMU** after clipping
28	**lp_cs**	–	Local parameter **CS** after T-scaling and clipping
29	**lp_stcs**	–	Local parameter **STCS** after clipping
30	**lp_xcor**	V^{-1}	Local parameter **XCOR** after T-scaling and clipping
31	**lp_stxcor**	–	Local parameter **STXCOR** after clipping
32	**lp_feta**	–	Local parameter **FETA** after clipping
			Series Resistance Parameters
33	**lp_rs**	Ω	Local parameter **RS** after T-scaling and clipping
34	**lp_strs**	–	Local parameter **STRS** after clipping

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No.	Name	Unit	Description
35	**lp_rsb**	V^{-1}	Local parameter **RSB** after clipping
36	**lp_rsg**	V^{-1}	Local parameter **RSG** after clipping
		Velocity Saturation Parameters	
37	**lp_thesat**	V^{-1}	Local parameter **THESAT** after T-scaling and clipping
38	**lp_stthesat**	–	Local parameter **STTHESAT** after clipping
39	**lp_thesatb**	V^{-1}	Local parameter **THESATB** after clipping
40	**lp_thesatg**	V^{-1}	Local parameter **THESATG** after clipping
		Saturation Voltage Parameters	
41	**lp_ax**	–	Local parameter **AX** after clipping
		Channel Length Modulation (CLM) Parameters	
42	**lp_alp**	–	Local parameter **ALP** after clipping
43	**lp_alp1**	V	Local parameter **ALP1** after clipping
44	**lp_alp2**	V^{-1}	Local parameter **ALP2** after clipping
45	**lp_vp**	V	Local parameter **VP** after clipping
		Impact Ionization (II) Parameters	
46	**lp_a1**	–	Local parameter **A1** after clipping
47	**lp_a2**	V	Local parameter **A2** after T-scaling and clipping
48	**lp_sta2**	–	Local parameter **STA2** after clipping
49	**lp_a3**	–	Local parameter **A3** after clipping
50	**lp_a4**	$1/\sqrt{V}$	Local parameter **A4** after clipping
		Gate Current Parameters	
51	**lp_gco**	–	Local parameter **GCO** after clipping
52	**lp_iginv**	A	Local parameter **IGINV** after T-scaling and clipping
53	**lp_igov**	A	Local parameter **IGOV** after T-scaling and clipping
54	**lp_igovd**	A	Local parameter **IGOVD** after T-scaling and clipping
55	**lp_stig**	–	Local parameter **STIG** after clipping
56	**lp_gc2**	–	Local parameter **GC2** after clipping
57	**lp_gc3**	–	Local parameter **GC3** after clipping
58	**lp_chib**	V	Local parameter **CHIB** after clipping
		Gate-Induced Drain Leakage Parameters	
59	**lp_agidl**	A/V^3	Local parameter **AGIDL** after clipping
60	**lp_agidld**	A/V^3	Local parameter **AGIDLD** after clipping
61	**lp_bgidl**	V	Local parameter **BGIDL** after T-scaling and clipping
62	**lp_bgidld**	V	Local parameter **BGIDLD** after T-scaling and clipping
63	**lp_stbgidl**	V/K	Local parameter **STBGIDL** after clipping
64	**lp_stbgidld**	V/K	Local parameter **STBGIDLD** after clipping
65	**lp_cgidl**	–	Local parameter **CGIDL** after clipping
66	**lp_cgidld**	–	Local parameter **CGIDLD** after clipping

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No.	Name	Unit	Description
			Charge Model Parameters
67	**lp_cox**	F	Local parameter **COX** after clipping
68	**lp_cgov**	F	Local parameter **CGOV** after clipping
69	**lp_cgovd**	F	Local parameter **CGOVD** after clipping
70	**lp_cgbov**	F	Local parameter **CGBOV** after clipping
71	**lp_cfr**	F	Local parameter **CFR** after clipping
72	**lp_cfrd**	F	Local parameter **CFRD** after clipping
			Noise Model Parameters
73	**lp_fnt**	–	Local parameter **FNT** after clipping
74	**lp_nfa**	$1/V/m^4$	Local parameter **NFA** after clipping
75	**lp_nfb**	$1/V/m^2$	Local parameter **NFB** after clipping
76	**lp_nfc**	V^{-1}	Local parameter **NFC** after clipping
77	**lp_ef**	–	Local parameter **EF** after clipping
			Parasitic Resistance Parameters
78	**lp_rg**	Ω	Local parameter **RG** after clipping
79	**lp_rse**	Ω	Local parameter **RSE** after clipping
80	**lp_rde**	Ω	Local parameter **RDE** after clipping
81	**lp_rbulk**	Ω	Local parameter **RBULK** after clipping
82	**lp_rwell**	Ω	Local parameter **RWELL** after clipping
83	**lp_rjuns**	Ω	Local parameter **RJUNS** after clipping
84	**lp_rjund**	Ω	Local parameter **RJUND** after clipping
			Self Heating Parameters
85	**lp_rth**	K/W	Local parameter **RTH** after T-scaling and clipping
86	**lp_cth**	J/K	Local parameter **CTH** after clipping
87	**lp_strth**	–	Local parameter **STRTH** after clipping
			Junction Parameters
88	**cjosbot**	F	Bottom component of total zero-bias source junction capacitance at device temperature
89	**cjossti**	F	STI-edge component of total zero-bias source junction capacitance at device temperature
90	**cjosgat**	F	Gate-edge component of total zero-bias source junction capacitance at device temperature
91	**vbisbot**	V	Built-in voltage of source-side bottom junction at device temperature
92	**vbissti**	V	Built-in voltage of source-side STI-edge junction at device temperature
93	**vbisgat**	V	Built-in voltage of source-side gate-edge junction at device temperature
94	**idsatsbot**	A	Total source-side bottom junction saturation current
95	**idsatssti**	A	Total source-side STI-edge junction saturation current
96	**idsatsgat**	A	Total source-side gate-edge junction saturation current

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No.	Name	Unit	Description
97	**cjosbotd**	F	Bottom component of total zero-bias drain junction capacitance at device temperature
98	**cjosstid**	F	STI-edge component of total zero-bias drain junction capacitance at device temperature
99	**cjosgatd**	F	Gate-edge component of total zero-bias drain junction capacitance at device temperature
100	**vbisbotd**	V	Built-in voltage of drain-side bottom junction at device temperature
101	**vbisstid**	V	Built-in voltage of drain-side STI-edge junction at device temperature
102	**vbisgatd**	V	Built-in voltage of drain-side gate-edge junction at device temperature
103	**idsatsbotd**	A	Total drain-side bottom junction saturation current
104	**idsatsstid**	A	Total drain-side STI-edge junction saturation current
105	**idsatsgatd**	A	Total drain-side gate-edge junction saturation current
			NQS Parameters
106	**lp_munqs**	–	Local parameter **MUNQS** after clipping

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Appendix A

Auxiliary Equations

In this Appendix, some auxiliary functions which are used in the model equations are defined.

The MINA-smoothing function:

$$\text{MINA}\,(x,\,y,\,a) = \frac{1}{2}\cdot\left[x + y - \sqrt{(x-y)^2 + a}\right] \tag{A.1}$$

The MAXA-smoothing function:

$$\text{MAXA}\,(x,\,y,\,a) = \frac{1}{2}\cdot\left[x + y + \sqrt{(x-y)^2 + a}\right] \tag{A.2}$$

The MNE- and MXE-smoothing functions:

$$\text{MNE}\,(x,\,y,\,\varepsilon) = \frac{2}{A}\left[x + y - \sqrt{(x+y)^2 - A\cdot xy}\right] \tag{A.3}$$

$$\text{MXE}\,(x,\,y,\,\varepsilon) = \frac{2}{A}\left[x + y + \sqrt{(x+y)^2 - A\cdot xy}\right] \tag{A.4}$$

$$A = 4 - \varepsilon; \qquad \varepsilon \in (0, 1) \tag{A.5}$$

The functions $\chi(y)$, its derivatives, σ_1, and σ_2, which are used in the explicit approximation of surface potential:

$$\chi(y) = \frac{y^2}{2 + y^2} \tag{A.6}$$

$$\chi'(y) = \frac{4y}{(2 + y^2)^2} \tag{A.7}$$

$$\chi''(y) = \frac{8 - 12y^2}{(2 + y^2)^3} \tag{A.8}$$

$$\nu = a + c \tag{A.9}$$

$$\mu_1 = \frac{v^2}{\tau} + \frac{c^2}{2} - a \tag{A.10}$$

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$$\sigma_1\,(a,\,c,\,\tau,\,\eta) = \frac{a\cdot\nu}{\mu_1 + (c^2/3 - a)\cdot c\cdot\nu/\mu_1} + \eta \tag{A.11}$$

$$\mu_2 = \frac{v^2}{\tau} + \frac{c^2}{2} - a\cdot b \tag{A.12}$$

$$\sigma_2\,(a,\,b,\,c,\,\tau,\,\eta) = \frac{a\cdot\nu}{\mu_2 + (c^2/3 - a\cdot b)\cdot c\cdot\nu/\mu_2} + \eta \tag{A.13}$$

Appendix B

Layout parameter calculation

In post-layout simulations, various PSP instance parameters should be supplied either manually or by a layout extraction tool. In this appendix, it is shown how these parameters should be calculated.

Note: These equations are *not* part of the PSP model.

B.1 Stress parameters

B.1.1 Layout effects for irregular shapes

For irregular shapes the following effective values for **SA** and **SB** are to be used (see Fig B.1).

$$\frac{1}{\mathbf{SA}_{\text{eff}} + 0.5 \cdot L} = \sum_{i=1}^{n} \frac{\mathbf{SW}_i}{W} \cdot \frac{1}{\mathbf{SA}_i + 0.5 \cdot L} \tag{B.1}$$

$$\frac{1}{\mathbf{SB}_{\text{eff}} + 0.5 \cdot L} = \sum_{i=1}^{n} \frac{\mathbf{SW}_i}{W} \cdot \frac{1}{\mathbf{SB}_i + 0.5 \cdot L} \tag{B.2}$$

B.2 Well proximity effect parameters

The values of the instance parameters **SCA**, **SCB** and **SCC** can be calculated from layout parameters using the equations below.

$$f_{\text{A}}(u) = \frac{\mathbf{SCREF}^2}{u^2} \tag{B.3}$$

$$f_{\text{B}}(u) = \frac{u}{\mathbf{SCREF}} \cdot \exp\left(-10 \cdot \frac{u}{\mathbf{SCREF}}\right) \tag{B.4}$$

$$f_{\text{C}}(u) = \frac{u}{\mathbf{SCREF}} \cdot \exp\left(-20 \cdot \frac{u}{\mathbf{SCREF}}\right) \tag{B.5}$$

$$A_{\text{corner}} = \sum_{i=m+1}^{m+k} \left(\frac{L}{2} \cdot \int_{\text{SCX}_i + \text{SCY}_i}^{\text{SCX}_i + \text{SCY}_i + W} f_{\text{A}}(u)\,\mathrm{d}u \right) + \sum_{i=n+1}^{n+k} \left(\frac{W}{2} \cdot \int_{\text{SCX}_i + \text{SCY}_i}^{\text{SCX}_i + \text{SCY}_i + L} f_{\text{A}}(u)\,\mathrm{d}u \right) \tag{B.6}$$

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$$B_{\mathrm{corner}} = \sum_{i=m+1}^{m+k} \left(\frac{L}{2} \cdot \int_{\mathrm{SCX}_i+\mathrm{SCY}_i}^{\mathrm{SCX}_i+\mathrm{SCY}_i+W} f_{\mathrm{B}}(u)\,\mathrm{d}u \right) + \sum_{i=n+1}^{n+k} \left(\frac{W}{2} \cdot \int_{\mathrm{SCX}_i+\mathrm{SCY}_i}^{\mathrm{SCX}_i+\mathrm{SCY}_i+L} f_{\mathrm{B}}(u)\,\mathrm{d}u \right) \quad \text{(B.7)}$$

$$C_{\mathrm{corner}} = \sum_{i=m+1}^{m+k} \left(\frac{L}{2} \cdot \int_{\mathrm{SCX}_i+\mathrm{SCY}_i}^{\mathrm{SCX}_i+\mathrm{SCY}_i+W} f_{\mathrm{C}}(u)\,\mathrm{d}u \right) + \sum_{i=n+1}^{n+k} \left(\frac{W}{2} \cdot \int_{\mathrm{SCX}_i+\mathrm{SCY}_i}^{\mathrm{SCX}_i+\mathrm{SCY}_i+L} f_{\mathrm{C}}(u)\,\mathrm{d}u \right) \quad \text{(B.8)}$$

$$\mathbf{SCA} = \frac{1}{W \cdot L} \cdot \left[\sum_{i=1}^{n} \left(W_i \cdot \int_{\mathrm{SC}_i}^{\mathrm{SC}_i+L} f_{\mathrm{A}}(u)\,\mathrm{d}u \right) + \sum_{i=n+1}^{n+m} \left(L_i \cdot \int_{\mathrm{SC}_i}^{\mathrm{SC}_i+W} f_{\mathrm{A}}(u)\,\mathrm{d}u \right) + A_{\mathrm{corner}} \right] \quad \text{(B.9)}$$

$$\mathbf{SCB} = \frac{1}{W \cdot L} \cdot \left[\sum_{i=1}^{n} \left(W_i \cdot \int_{\mathrm{SC}_i}^{\mathrm{SC}_i+L} f_{\mathrm{B}}(u)\,\mathrm{d}u \right) + \sum_{i=n+1}^{n+m} \left(L_i \cdot \int_{\mathrm{SC}_i}^{\mathrm{SC}_i+W} f_{\mathrm{B}}(u)\,\mathrm{d}u \right) + B_{\mathrm{corner}} \right] \quad \text{(B.10)}$$

$$\mathbf{SCC} = \frac{1}{W \cdot L} \cdot \left[\sum_{i=1}^{n} \left(W_i \cdot \int_{\mathrm{SC}_i}^{\mathrm{SC}_i+L} f_{\mathrm{C}}(u)\,\mathrm{d}u \right) + \sum_{i=n+1}^{n+m} \left(L_i \cdot \int_{\mathrm{SC}_i}^{\mathrm{SC}_i+W} f_{\mathrm{C}}(u)\,\mathrm{d}u \right) + C_{\mathrm{corner}} \right] \quad \text{(B.11)}$$

Here, m and n are the number of projections of the well edge along the length and width of the devices, respectively. Moreover, k is the number of corners selected to account for the ‘corner’ effects.

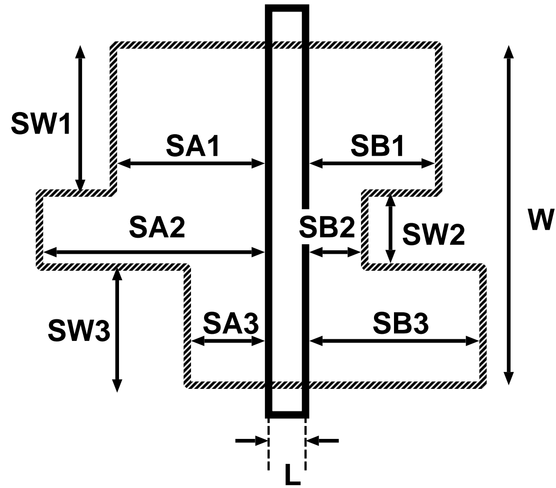

Figure B.1: A typical layout of MOS devices with more instance parameters ($\mathbf{SW}_i$, $\mathbf{SA}_i$ and $\mathbf{SB}_i$) in addition to the traditional L and W.

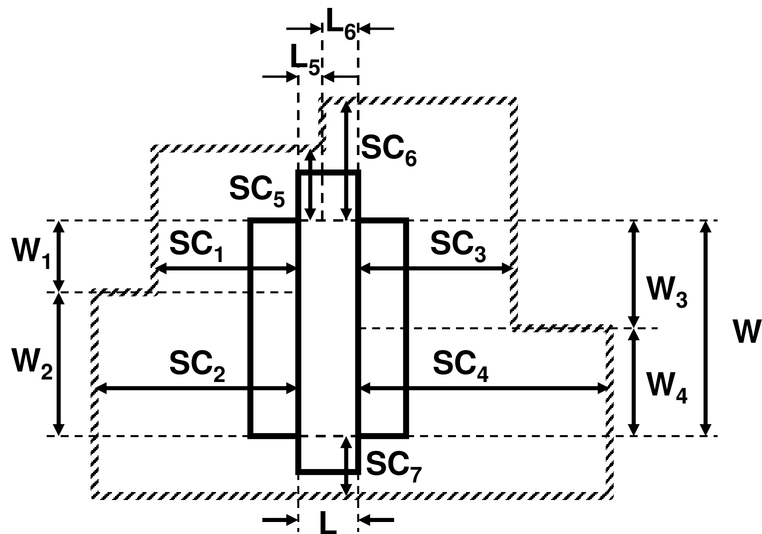

Figure B.2: A typical layout of MOS devices with **WPE** instance parameters

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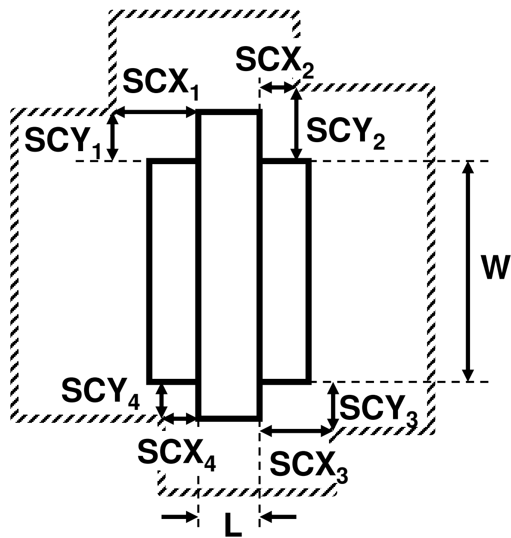

Figure B.3: A layout of MOS devices for corner terms calculation

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